

8. Luminescence Mechanisms

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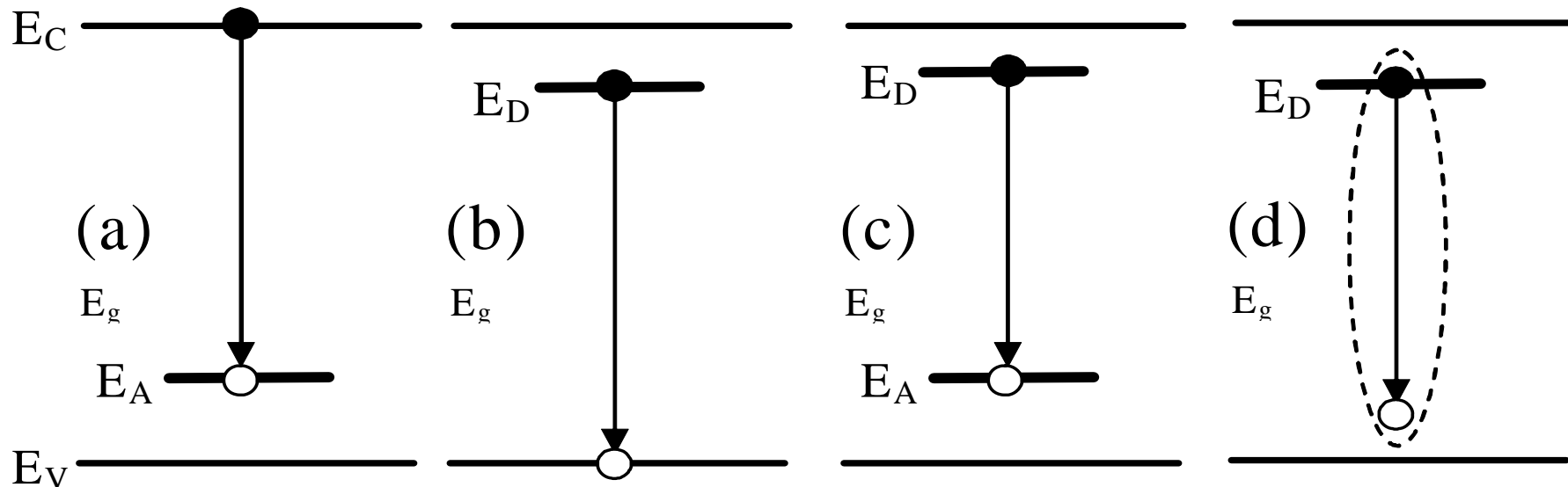
8.15 Afterglow

8.1 Luminescence - Definition

Luminescence is a process that corresponds to emission of electromagnetic radiation beyond thermal equilibrium.

Inorganic materials: Radiative recombination involving impurity levels:

- (a) Conduction-band–acceptor-state transition**
- (b) Donor-state–valence-band transition**
- (c) Donor-acceptor recombination**
- (d) Bound-exciton recombination**



Thus: Luminescence requires localisation of absorbed energy by discrete states!

8.1 Luminescence - Definition

Thermal and non-thermal radiators

Thermal radiators emit a radiation spectrum that equals black body radiation at a corresponding temperature

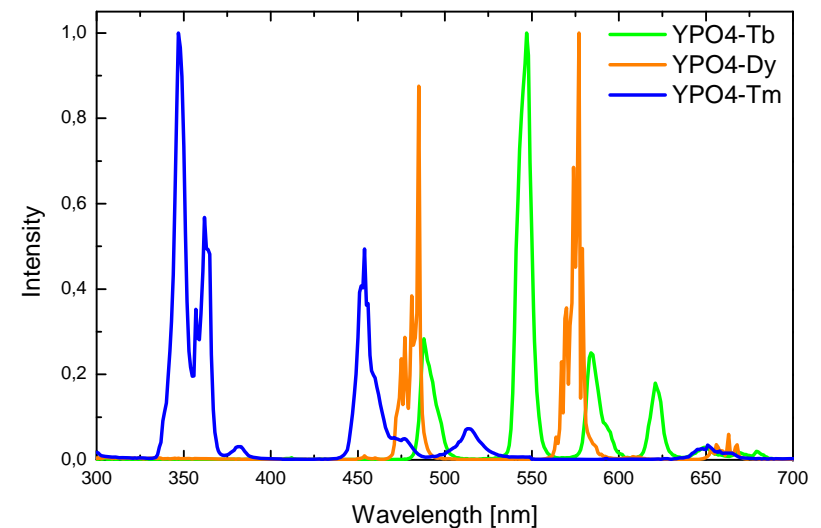
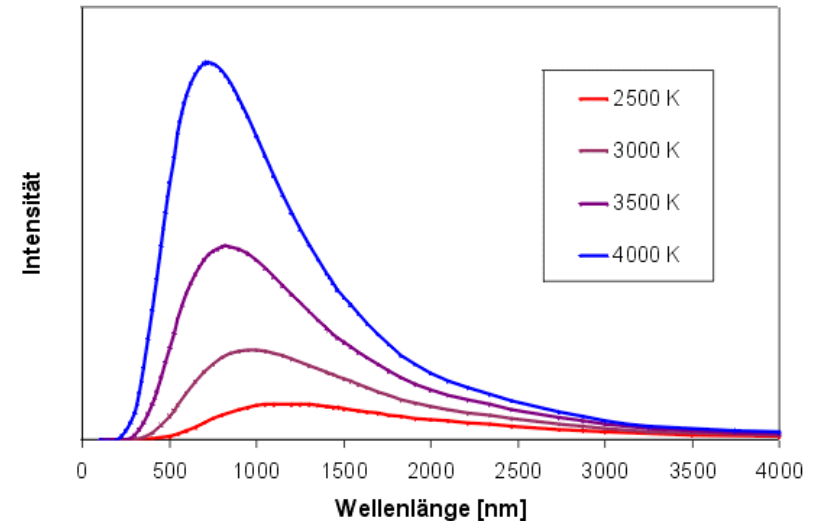
→ **Planck radiation**

Examples: Cosmic background radiation, cosmic objects, halogen- and incandescent lamps

Non-thermal radiators emit a radiation spectrum originating from electronic transitions between discrete electronic energy levels

→ **Luminescence**

Examples: Luminescent materials, LEDs, Lasers



8.1 Luminescence – Materials

Inorganic luminescent materials = Host lattice + defects + dopants

Host lattice

Y_2O_3 , $\text{Y}_3\text{Al}_5\text{O}_{12}$, ZnS , CaAlSiN_3 , $\text{Sr}_2\text{Si}_5\text{N}_8$, ...

- Selection in accordance to requirements defined by the application area:
Excitation energy, absorption strength, chemical environment, temperature

Dopants

Cr^{3+} , Mn^{4+} , Sb^{3+} , Pb^{2+} , $\text{Eu}^{2+/3+}$, Ce^{3+} , ...

- Selection and concentration depend on host lattice and application area:
Solubility, mobility, oxidation state stability, CT state location

Defects

V_K , V_A , F, interstitials, ...

cause:

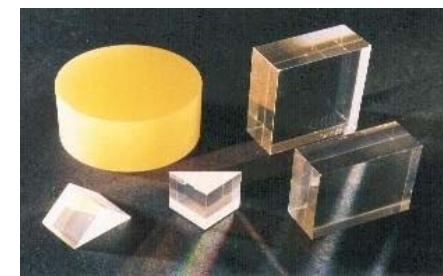
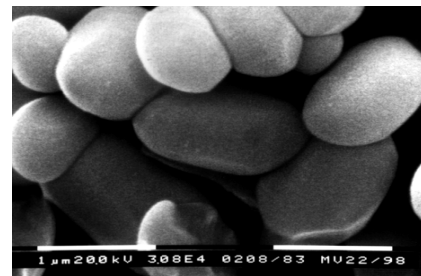
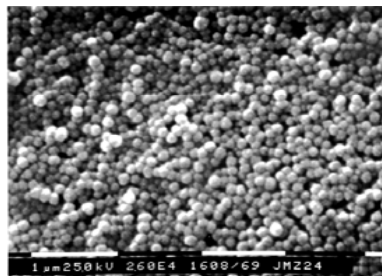
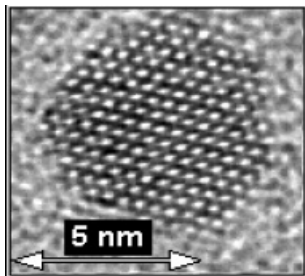
- Afterglow and charge storage
- Concentration and thermal quenching
- Reduction of stability and colour point shift

8.1 Luminescence – Materials

Inorganic luminescent materials - Morphology

- **Nanoscale particles** **Molecular imaging, precursors**
- **μ -sized particles** **Lamps, LEDs, CRTs, PDPs, EL Displays, x-ray converter films**
- **Large single crystals** **Scintillators, Lasers**
- **Ceramics** **LEDs, scintillators, LEDs**
- **Glasses** **Detectors, Lasers**

1 nm 10 nm 100 nm 1 μ m 10 μ m 100 μ m 1 mm 10 mm



8.1 Luminescence – Materials

Inorganic luminescent materials – Requirements for high efficiency

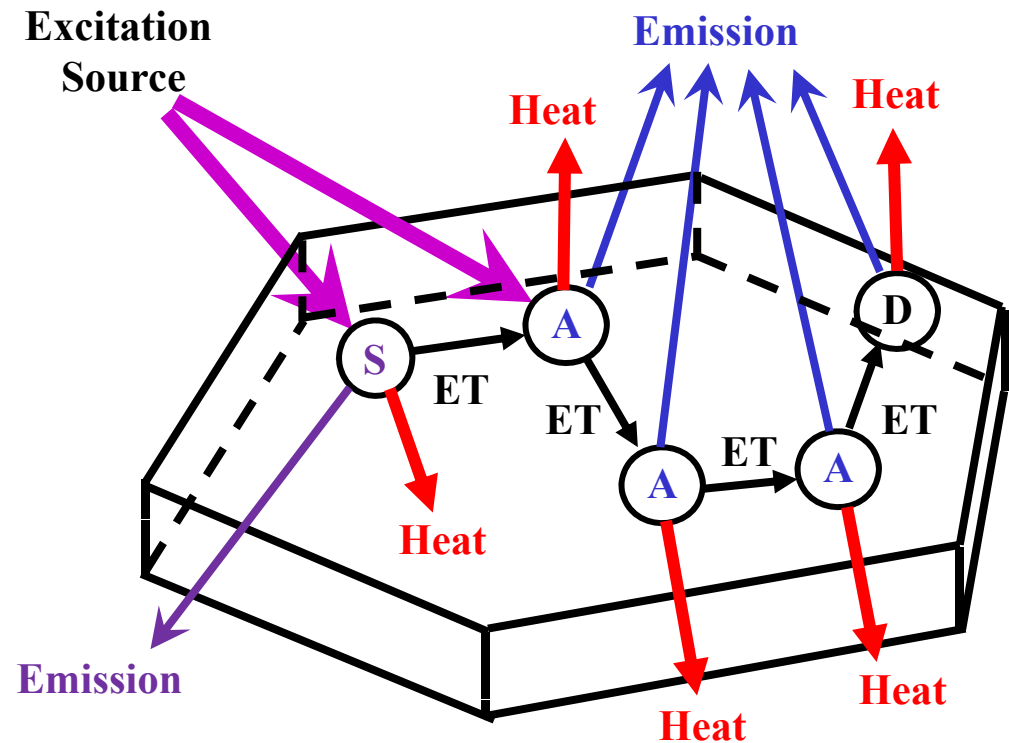
- Strong absorption
- Highly crystalline particles, low defect density
- High purity (99,99% or higher)
- Homogeneous distribution of activator and sensitizer ions
- Low phonon frequencies

Absorption process related to

Optical centres (impurities)

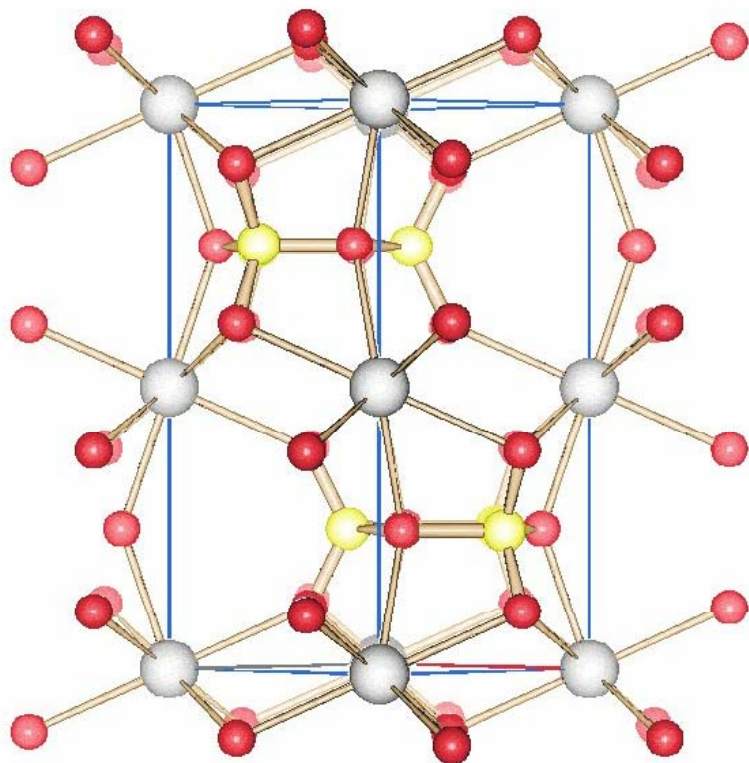
- activators (A)
- sensitizers (S)
- defects (D)
- host lattice (band edge)

Energy transfer often occurs prior to emission process!



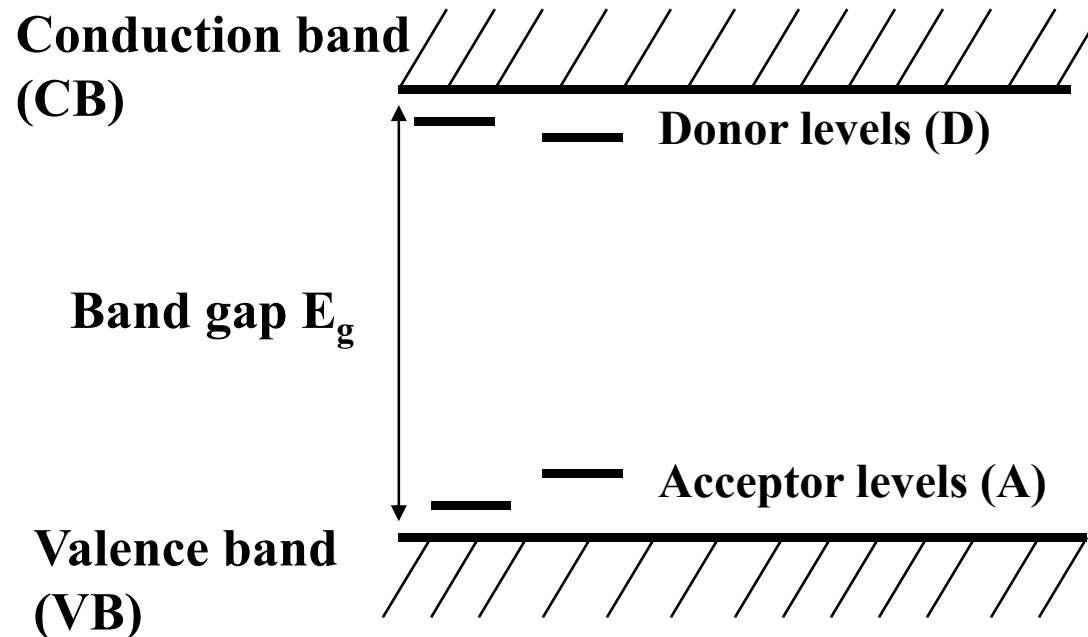
8.1 Luminescence – Materials

Inorganic luminescent materials – The role of the host lattice



YBO₃ (Vaterite)

Band gap $E_g = 6.5$ eV



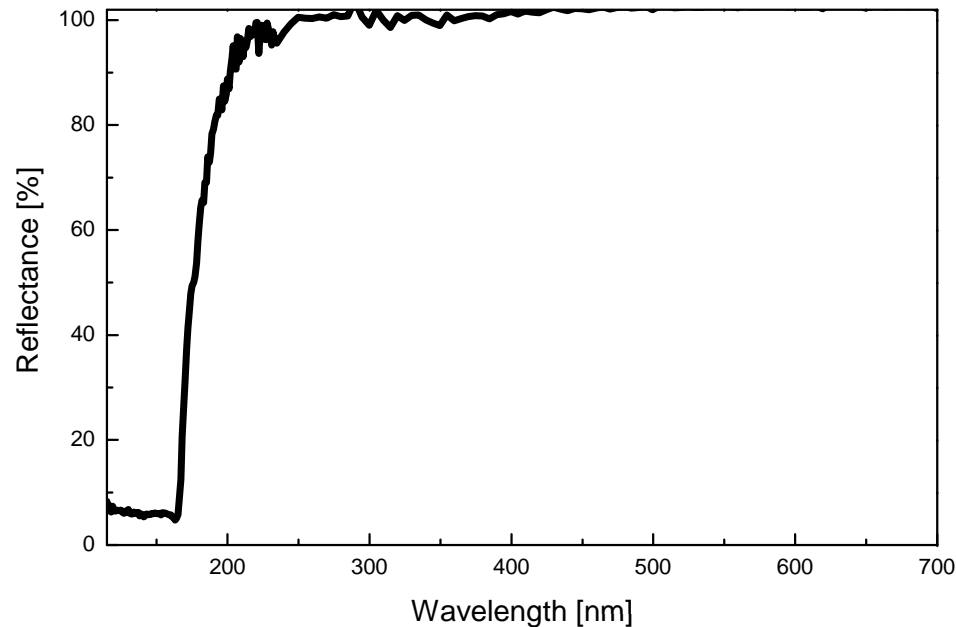
Absorption via

- Host lattice
→ Charge-Transfer or VB to CB
- Defects (colour centers)
→ Donor and acceptor levels

8.1 Luminescence – Materials

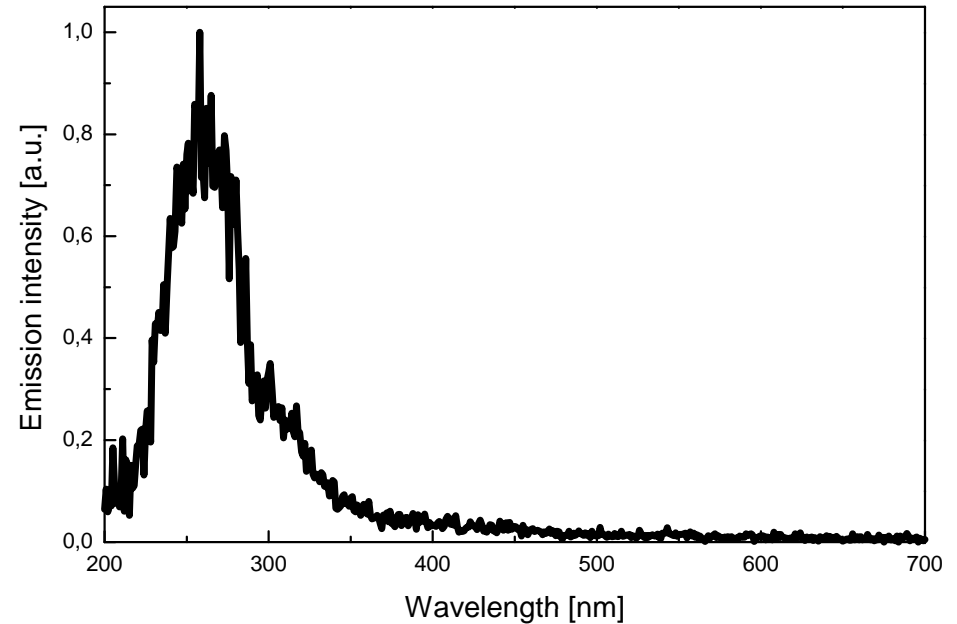
Inorganic luminescent materials – The role of the host lattice

Reflection spectrum of YBO_3



Band gap absorption at 170 nm

Emission spectrum of YBO_3 upon 160 nm excitation

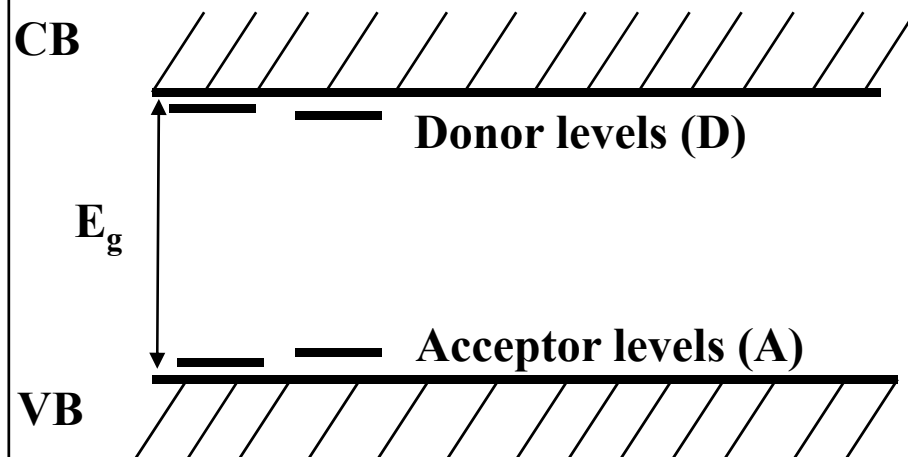


Exciton luminescence at 260 nm

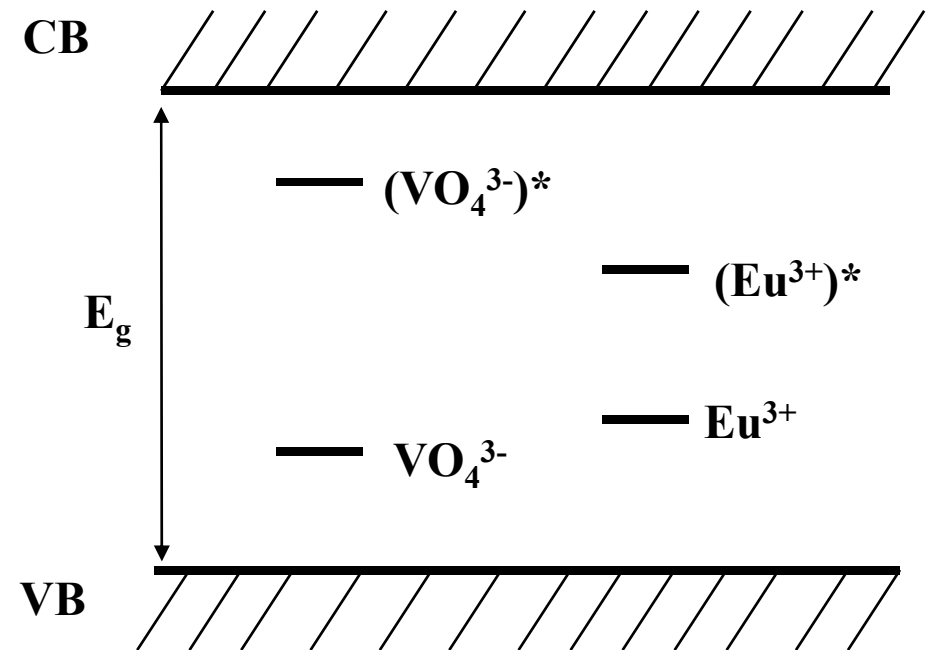
8.1 Luminescence – Materials

Inorganic luminescent materials – The role of the dopants

YVO_4 (tetragonal), $E_g = 4.2 \text{ eV}$



$\text{YPO}_4:\text{V},\text{Eu}$ (tetragonal), $E_g = 8.2 \text{ eV}$

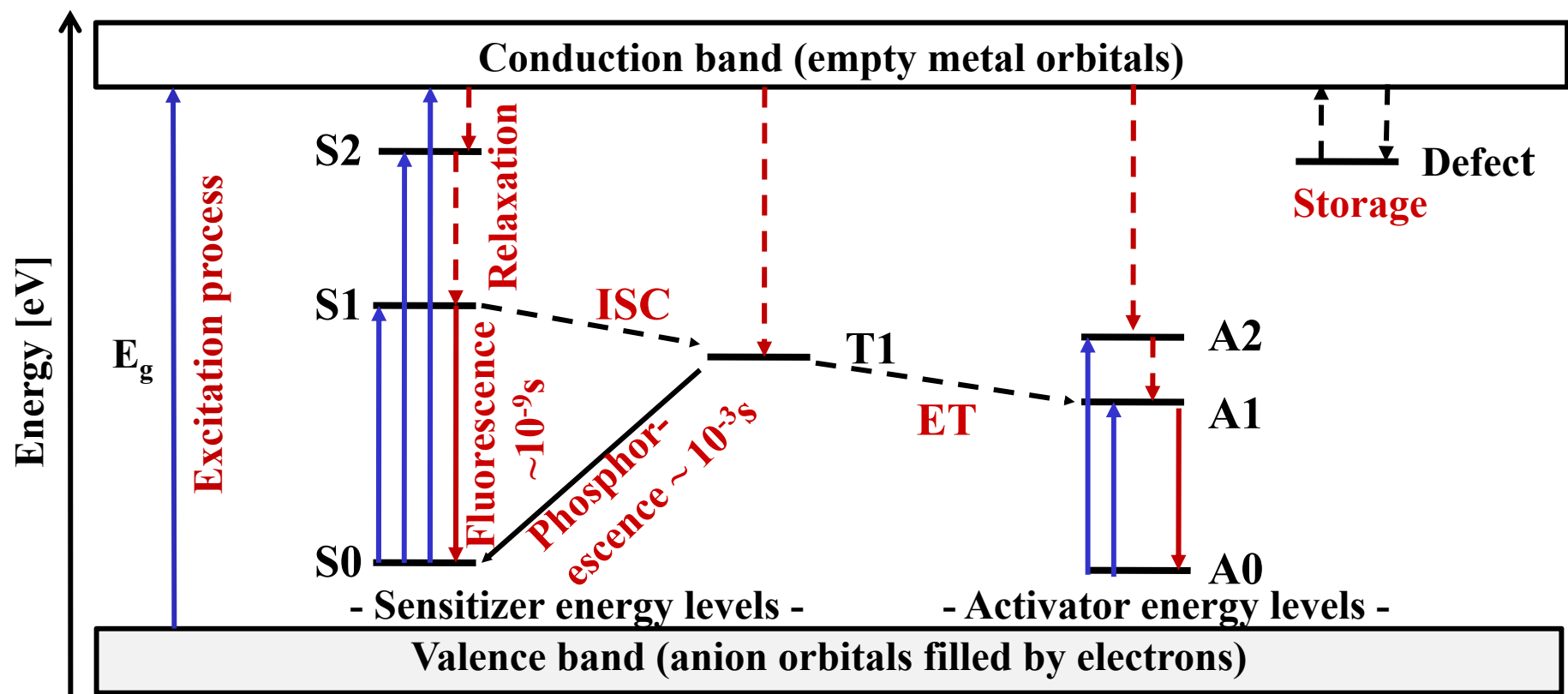


Absorption via

- Host lattice → Charge-Transfer or VB to CB
- Defects (colour centers) → Donor and acceptor levels
- Dopants (impurities) → Activators and sensitizers

8.1 Luminescence - Processes

The overall picture



S0, S1, S2, T1, A0, A1 = Energy levels of the activators and sensitizers

ISC = Intersystem Crossing “spin-forbidden singulett-triplett transition”

ET = Energy transfer

8.1 Luminescence - Processes

Electronic Ground States of Atoms and Ions (Dopants)

The electronic energy levels are defined by the spin and orbital momentum of the electrons and by the coupling of these to the total spin and total (orbital) momentum

Atom/Ion	Electron configuration	Spectroscopic term $^{2S+1}L_J$
Li^0	$1s^2 2s^1$	$^2S_{1/2}$
Li^+	$1s^2$	1S_0
Na^0	$[\text{Ne}]3s^1$	$^2S_{1/2}$
Ti^{3+}	$[\text{Ar}]3d^1$	$^2D_{3/2}$
$\text{Cr}^{3+}/\text{Mn}^{4+}$	$[\text{Ar}]3d^3$	$^4F_{3/2}$
$\text{Mn}^{2+}/\text{Fe}^{3+}$	$[\text{Ar}]3d^5$	$^6S_{5/2}$
$\text{Zn}^{2+}/\text{Cu}^+$	$[\text{Ar}]3d^{10}$	1S_0
Ce^{3+}	$[\text{Xe}]4f^1$	$^2F_{5/2}$
Eu^{3+}	$[\text{Xe}]4f^6$	7F_0
$\text{Eu}^{2+}/\text{Gd}^{3+}/\text{Tb}^{4+}$	$[\text{Xe}]4f^7$	$^8S_{7/2}$
Tb^{3+}	$[\text{Xe}]4f^8$	7F_6
Lu^{3+}	$[\text{Xe}]4f^{14}$	1S_0

8.1 Luminescence - Processes

Selection rules for electric dipole radiation (transitions)

Overall requirement: Conservation of momentum of the system “atom/ion + photon”

1. Spin selection rule $\Delta S = 0$
2. Angular momentum (single electron) $\Delta l = \pm 1$
3. Angular momentum (multi electron)
 $\Delta J = 0, \pm 1$ (but not $J = 0 \rightarrow J = 0$)
 $\Delta L = 0, \pm 1$ (but not $L = 0 \rightarrow L = 0$)
4. Laporte selection rule
 $g \rightarrow u$ or $u \rightarrow g$
not $g \rightarrow g$ or $u \rightarrow u$

Examples:	Ce^{3+}	$[\text{Xe}]4f^1 ({}^2F_{5/2}) \rightarrow [\text{Xe}]5d^1 ({}^2D_{3/2})$	\Rightarrow allowed	\sim ns
	Eu^{3+}	$[\text{Xe}]4f^6 ({}^7F_0) \rightarrow [\text{Xe}]4f^6 ({}^5D_0)$	\Rightarrow forbidden	\sim ms

8.1 Luminescence - Processes

Type	Excitation by	Example
Scintillation	High energy particles γ -rays	high-energy physics PET detectors
X-ray luminescence	X-rays	X-ray amplifier, CT
Cathode luminescence	Electrons (high voltage)	CRTs, oscilloscopes
Photo luminescence	UV/Vis photons	Fluorescent lamps
Electro luminescence	Electrical field (low voltage)	LEDs, EL displays
Chemo luminescence	Chemical reaction	Emergency signals
Bio luminescence	Biochemical reaction	Jelly fish, glow worms
Thermo luminescence	Heat	Afterglow phosphors
Sono luminescence	Ultra sound	-
Mechano luminescence	Mechanical energy	Peeling scotch tape

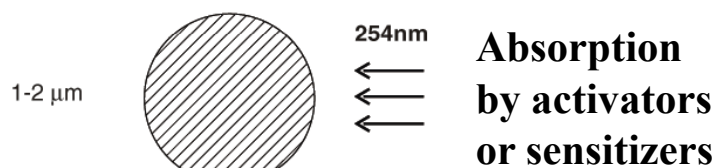
Nature 455 (2008) 1089, blue + UV + x-ray!

8.2 Absorption

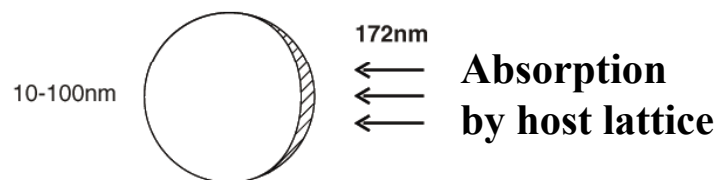
Penetration depth of photons and electrons

Photons (Lambert-Beer law)

Penetration depth



$h \cdot \nu < E_g$ (host lattice)



$h \cdot \nu > E_g$ (host lattice)

Electrons (Feldman equation: R in [\AA])

$$R = 250 \frac{A}{\rho Z^{n/2}} U^n \text{ with } n = \frac{1,2}{1 - 0,29 \log_{10} Z}$$

For 5.7 keV electrons	Density [g/cm ³]	R [\AA]	R [nm]
SiO ₂	2.20	6171	617.8
Al ₂ O ₃	3.97	3476	347.6
Mg ₃ (PO ₄) ₂	2.56	5345	534.4
ZnS	4.04	4248	424.8
MgO	3.59	3799	379.8
MgF ₂	3.15	4464	446.4
MgS	2.68	5603	560.4

Simplified $R \sim 0.046 \cdot U^{5/3} / \rho$ [μm]

For a material with $r = 5.0 \text{ g/cm}^3$ (Y₂O₃)

10 kV electrons R ~ 400 nm

2 kV electrons R ~ 30 nm

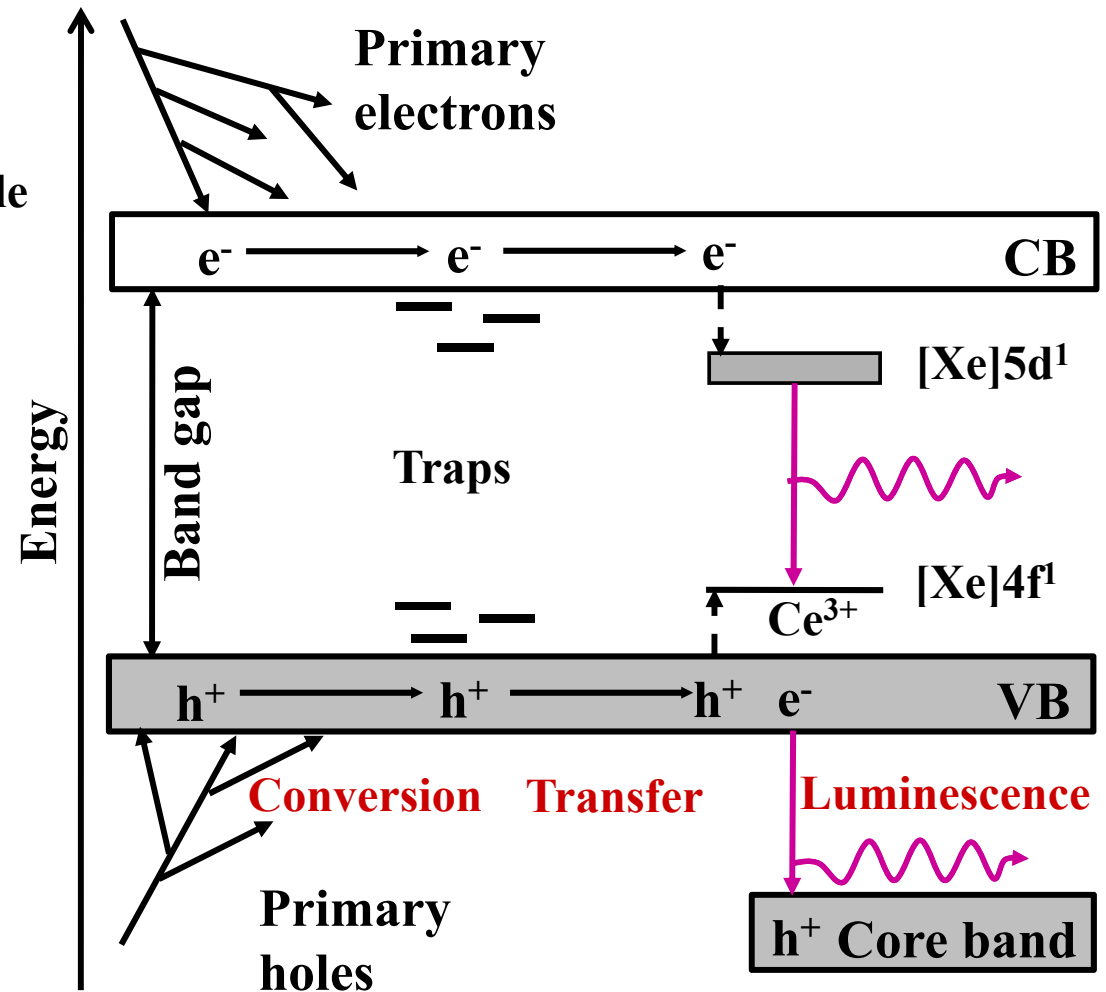
8.3 Excitation Mechanisms

High energy particles, γ - ray, x-ray and high voltage electron excitation

1. Excitation of highly energetic core states
2. Thermalization of electron-hole pairs with band gap energy
3. Energy transfer to activator ions or centers
4. (Center) Luminescence

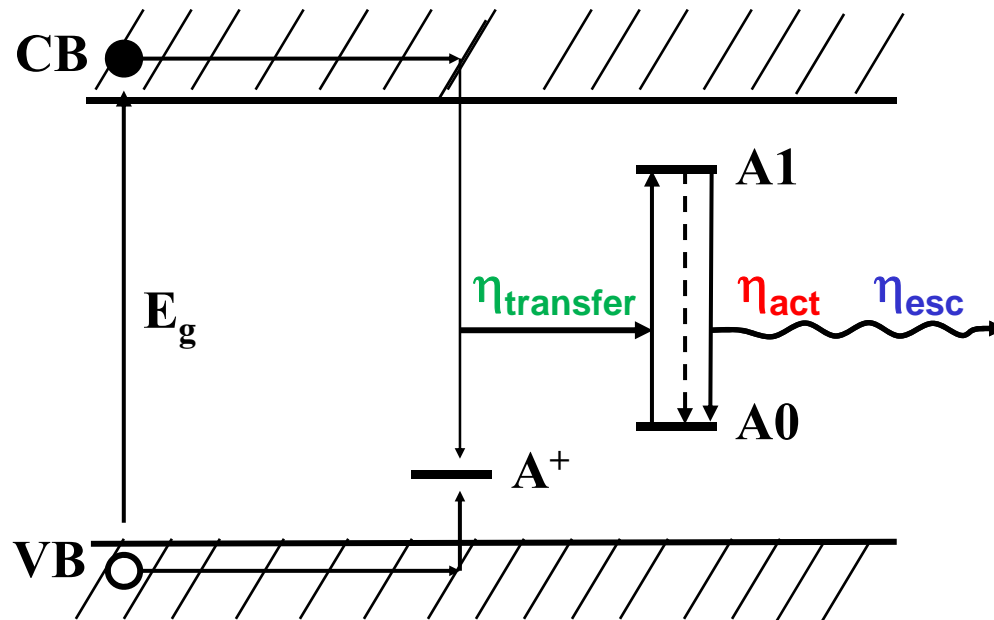
Efficiency surprisingly well understood, but with two different models:

1. Robbins
2. Bartram-Lempicki



8.3 Excitation Mechanisms

Photons with an energy $>$ band gap of the host lattice: PDPs and Xe excimer lamps



Host lattice	Band gap E_g [eV]
MgF ₂	12.2
Al ₂ O ₃	8.0
Y ₂ O ₃	5.6
ZnS	3.9
ZnSe	2.8
ZnTe	2.4
CdS	2.6
CdTe	1.6

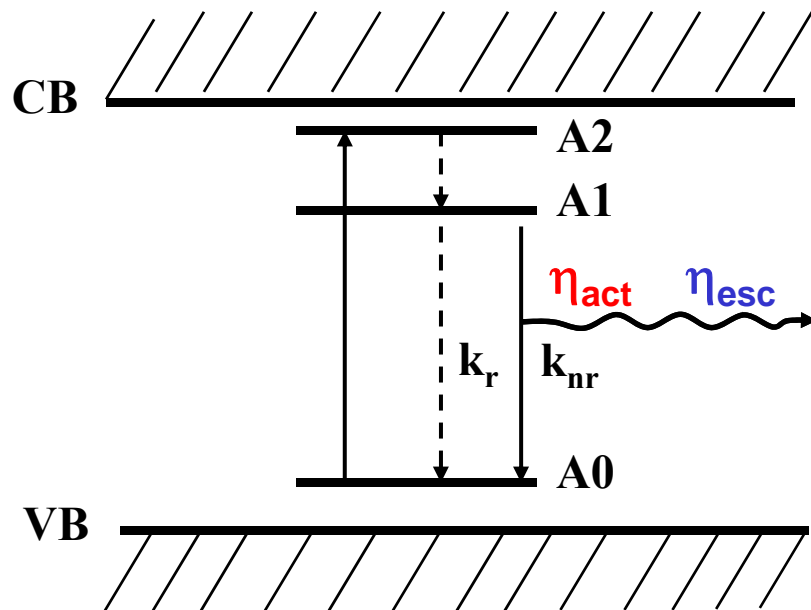
Internal quantum efficiency: $IQE = \eta_r / (\eta_r + \eta_{nr}) = \eta_{act}$

External quantum efficiency: $EQE = \eta_{act} * \eta_{transfer} * \eta_{esc}$

8.3 Excitation Mechanisms

Photons with an energy < band gap of the host lattice: Fluorescent lamps and LEDs

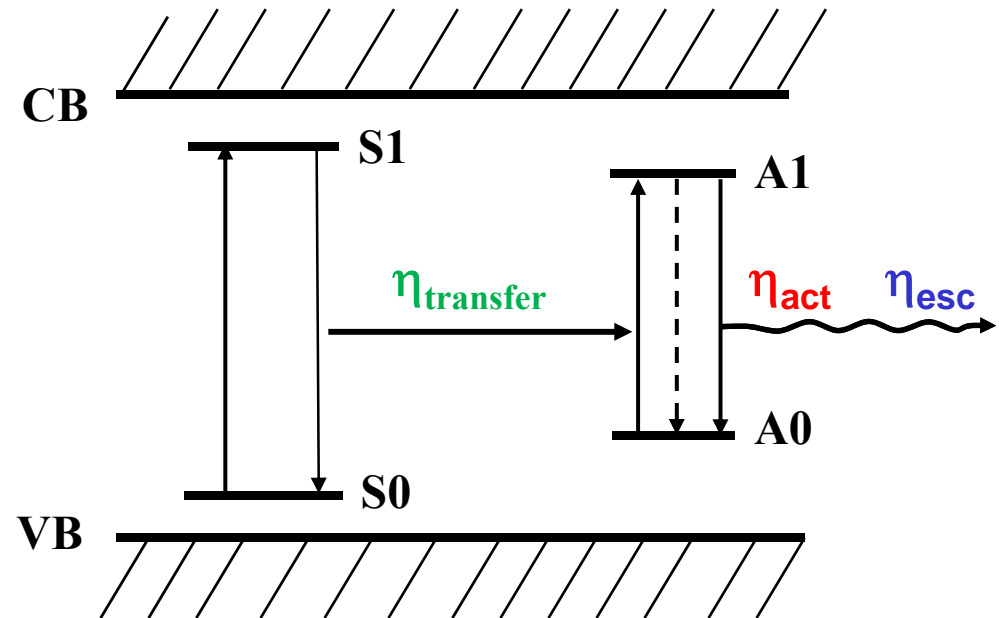
Activator excitation



$$\text{IQE} = \eta_{\text{act}} = k_r / (k_r + k_{\text{nr}}) = \tau / \tau_0$$

with $k_r + k_{\text{nr}} = 1/\tau$ and $k_r = 1/\tau_0$

Sensitizer excitation

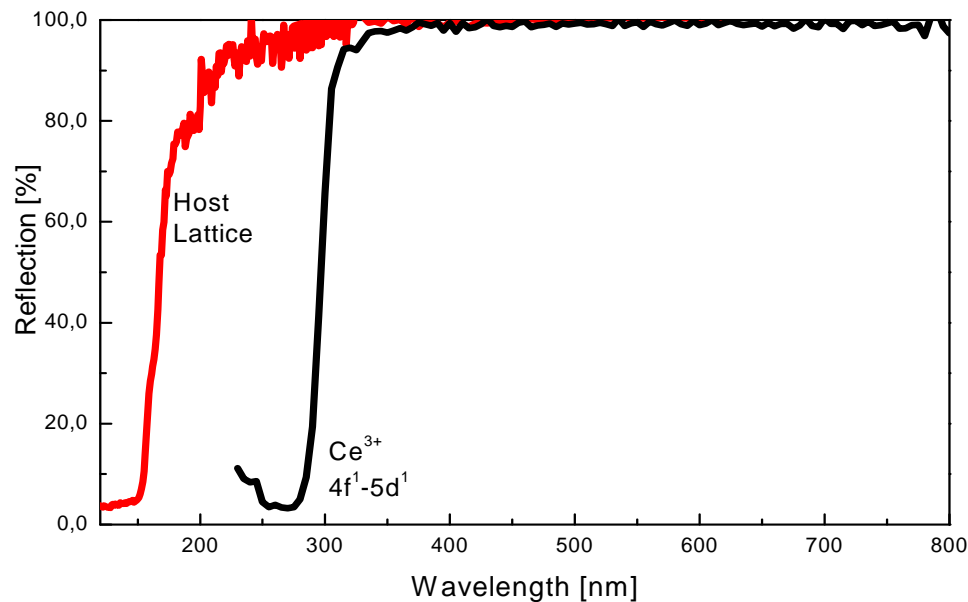


$$\text{EQE} = \eta_{\text{act}} * \eta_{\text{transfer}} * \eta_{\text{esc}}$$

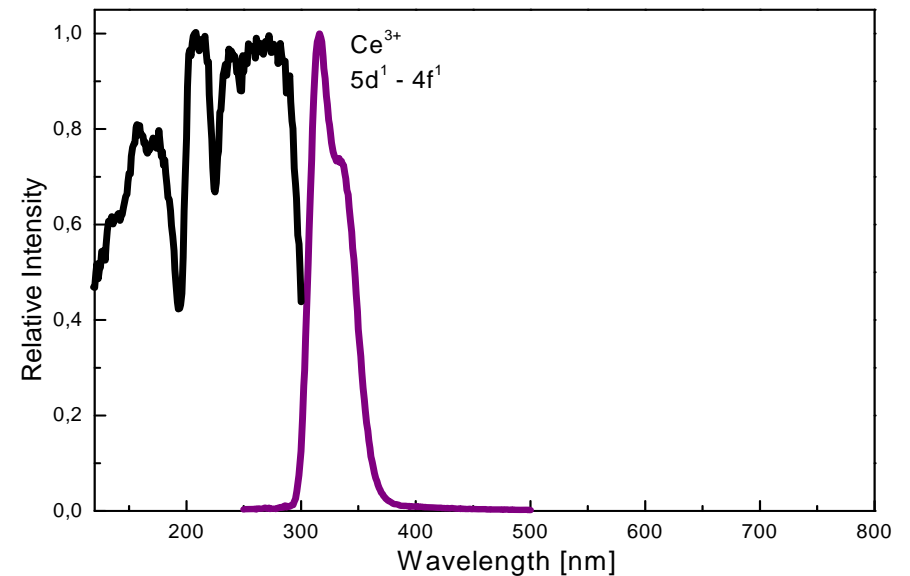
8.3 Excitation Mechanisms

Example: LaPO₄ doped by 20% Ce³⁺

Reflection spectra



Emission and excitation spectra

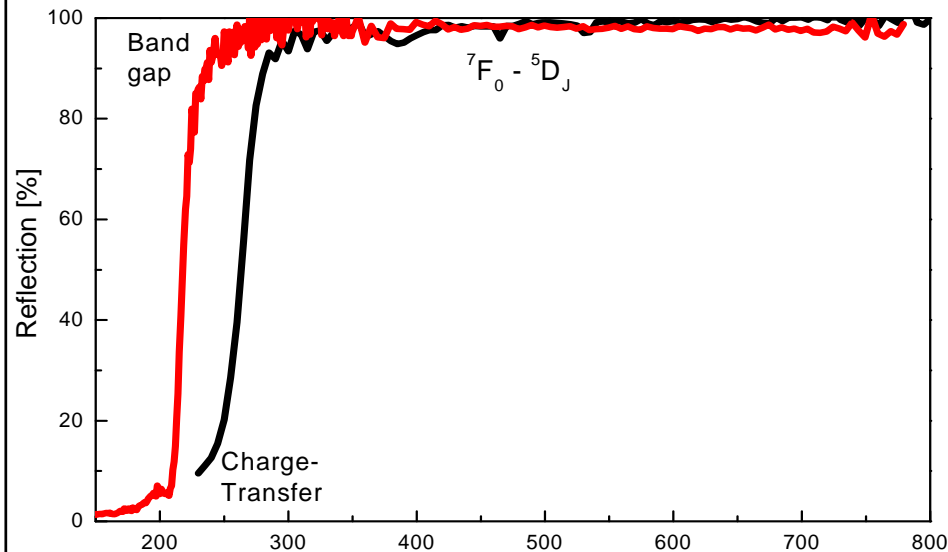


- Host material VB → CB 150 nm (8.2 eV)
- Ce³⁺ [Xe]4f¹ → [Xe]5d¹ 200 nm (6.2 eV) and 450 nm (2.8 eV)
- Allowed transition ⇒ Intense absorption bands and fast decay (~ 30 ns)

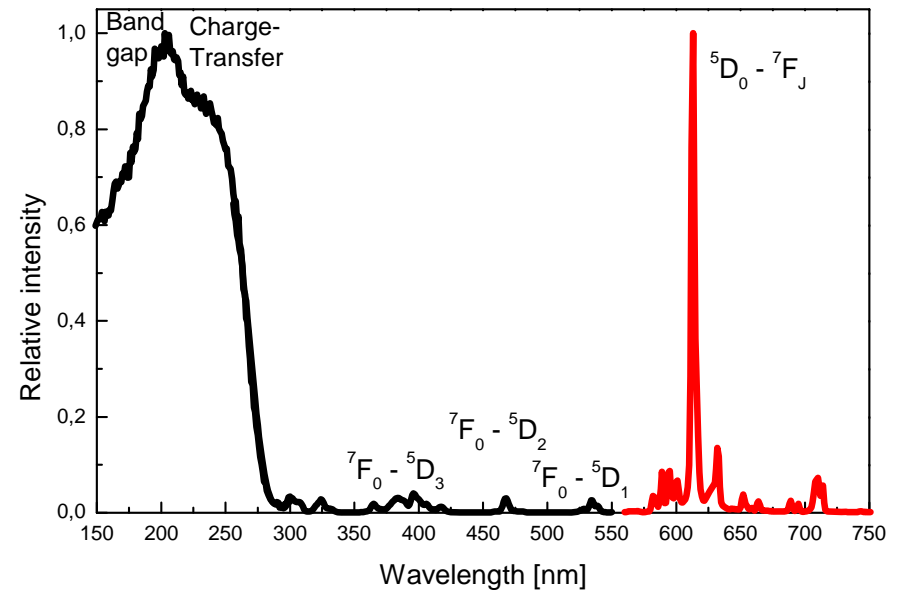
8.3 Excitation Mechanisms

Example: Y_2O_3 doped by 5% Eu^{3+}

Reflection spectra



Emission and excitation spectra



- **Host material** VB \rightarrow CB
 - **Eu^{3+}** Charge-Transfer
[Xe]4f⁶ \rightarrow [Xe]4f⁶
 - **Forbidden transitions** \Rightarrow Weak absorption bands and slow decay (~ 3 ms)
- 210 nm (5.9 eV)
230 nm (5.4 eV)
395 nm (3.1 eV) and 465 nm (2.2 eV)

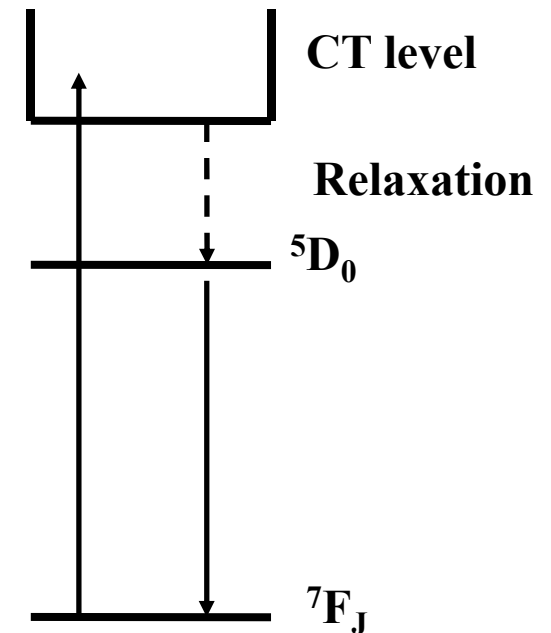
8.3 Excitation Mechanisms

Sensitisation to enhance absorption strength

→ $3d^n - 3d^n$ and $4f^n - 4f^n$ transitions are very weak

Ways to enhance absorption:

- Taking advantage of allowed transitions
 - Charge-Transfer (CT) states → Eu^{3+} , Yb^{3+}
 - Low-lying energy levels of the $[\text{Xe}]4f^{n-1}5d^1$ configuration → Tb^{3+} , Eu^{2+} , Ce^{3+} , Pr^{3+}
- Sensitisation (via energy transfer)
 - Ce^{3+} → Tb^{3+}
 - Pr^{3+} → Tb^{3+}
 - Nd^{3+} → Gd^{3+}
 - Pr^{3+} → Gd^{3+}
 - Bi^{3+} → Eu^{3+}
 - Sb^{3+} → Mn^{2+}



Simplified energy level scheme of Eu^{3+}

8.4 Energy Transfer

Requirements for ET ($S^* + A \rightarrow S + A^*$)

- Sensitizer S and activator A interact with each other by

- Coulomb interaction (multipolar interaction)

Dipole-Dipole: $P_{SA} = (1/\tau_S)(r_0/r_{SA})^6$ $Ce^{3+} - Eu^{2+}$

Dipole-Quadrupole: $P_{SA} = (1/\tau_S)(r_0/r_{SA})^8$ $Ce^{3+} - Tb^{3+}$

Quadrupole-Quadrupole: $P_{SA} = (1/\tau_S)(r_0/r_{SA})^{10}$ unknown

- Exchange interaction

$P_{SA} \sim J \cdot \exp(-2 r_{SA})$

for $r_{SA} < 5 \text{ \AA}$ with $J =$ coupling constant $Mn^{2+} - Mn^{2+}$

- Spectral overlap (\rightarrow Energy conservation law!)

8.4 Energy Transfer

Probability P_{ET}

The probability P_{ET} for an energy transfer is given by the following term:

$$P_{ET} = (2\pi/\hbar) \cdot (\rho) \langle \varphi_i | \mathbf{H} | \varphi_f \rangle^2$$

φ_i : Wave function of the initial state

φ_f : Wave function of the final state

\mathbf{H} : Operator coupling the states

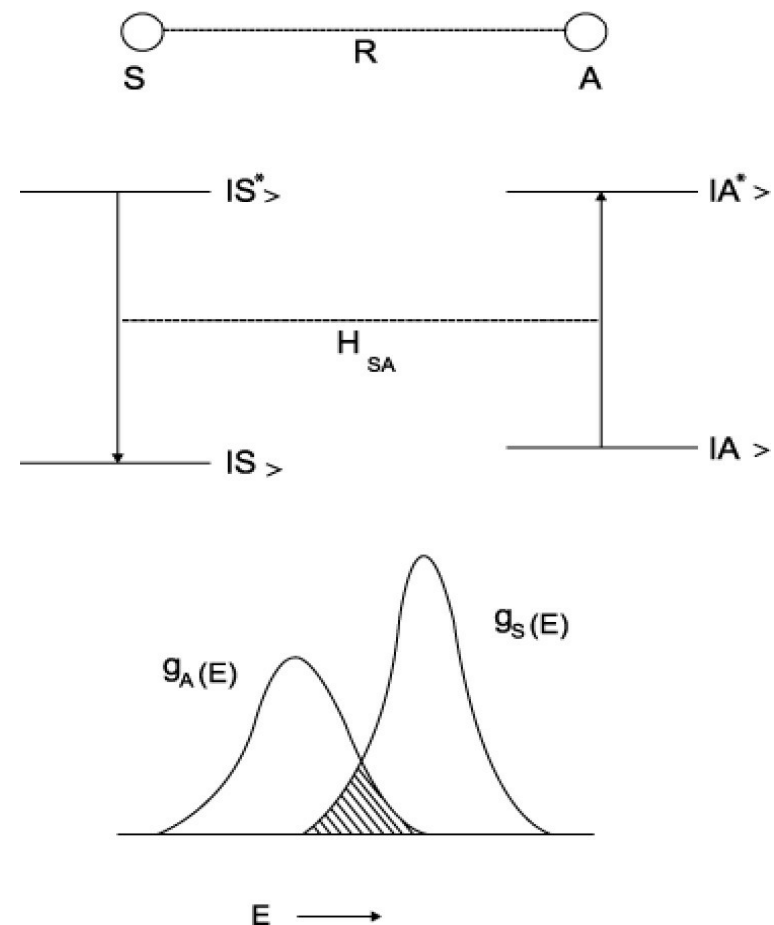
ρ : Spectral overlap (energy conservation)

Spectral overlap

$$\rho = g_S(E) \cdot g_A(E) \cdot dE$$

$g_S(E)$ and $g_A(E)$: Normalised optical line shape functions for sensitizer and activator ions

Energy Transfer



8.4 Energy Transfer

Consequences for luminescence processes

ET causes

- Energy migration
- Concentration quenching
- Thermal quenching
- Cross-relaxation
- Possibility of sensitization

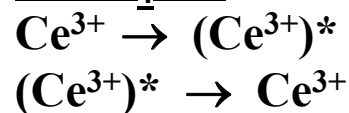
Some rules

- ET from a broad band emitter to a line emitter only possible for nearest neighbors in the host lattice (Ce^{3+} - Tb^{3+})
- ET from a line emitter to a band absorber proceeds over long distances (Gd^{3+} - Ce^{3+})
- ET strongly depends on average distance and thus concentration of luminescent centers

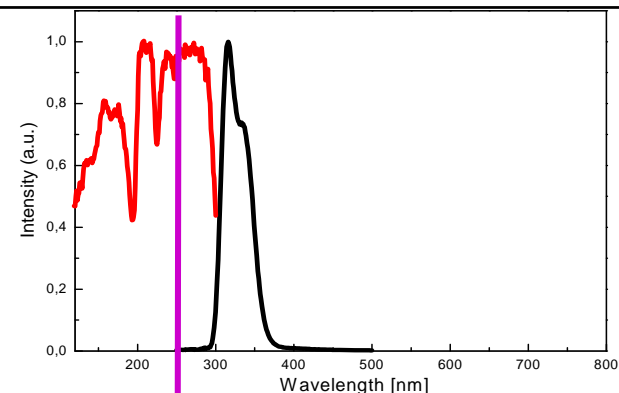
8.4 Energy Transfer

Example: ET in $\text{LaPO}_4:\text{Ce,Tb}$

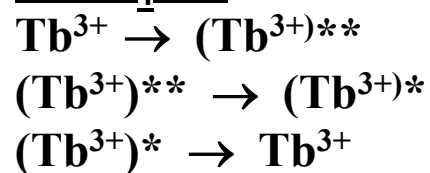
$\text{LaPO}_4:\text{Ce}$



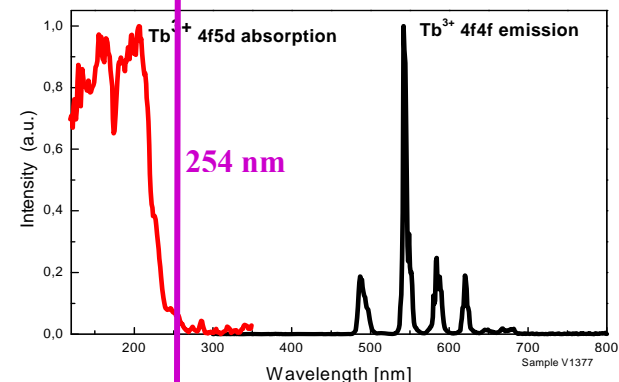
Excitation 4f - 5d
Emission 5d - 4f



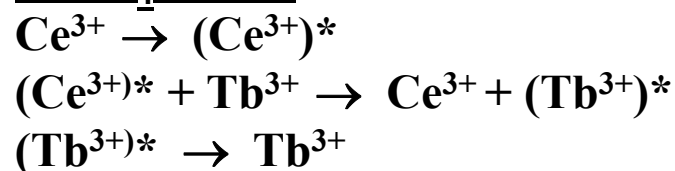
$\text{LaPO}_4:\text{Tb}$



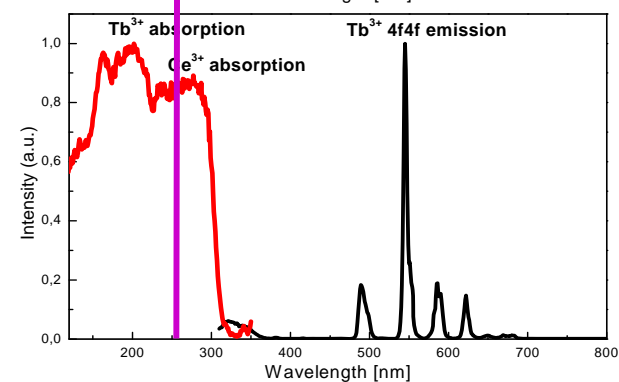
Excitation 4f - 5d
Relaxation
Emission 4f - 4f



$\text{LaPO}_4:\text{Ce,Tb}$



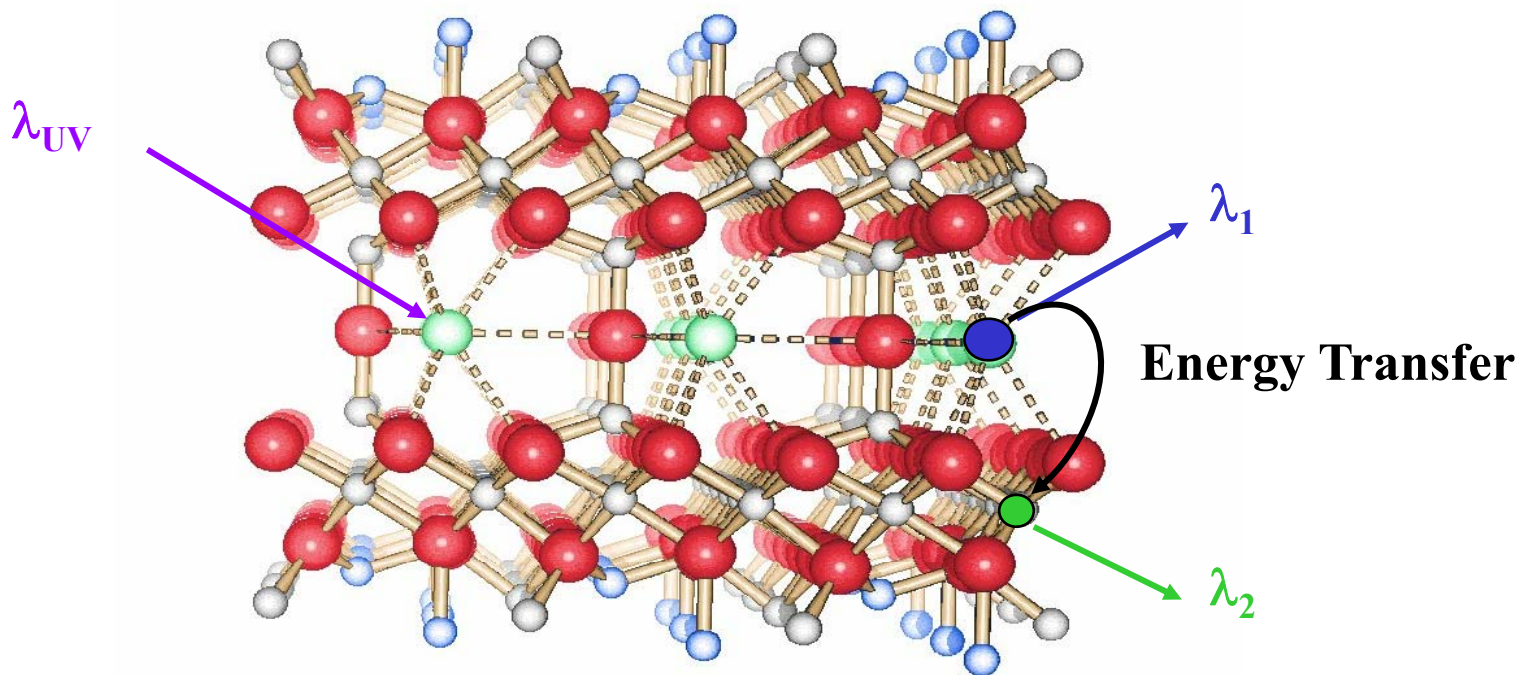
Excitation 4f - 5d
ET from Ce^{3+} to Tb^{3+}
Emission 4f - 4f



Fluorescent lamps \Rightarrow Excitation at 254 nm

8.4 Energy Transfer

Example: ET in $\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$ co-doped by transition metal ions



SCHAKAL

Divalent RE ions

Divalent TM ions

Trivalent TM ions

Ba^{2+} sites in the conduction layer

tetrahedral gaps in the spinel blocks

octahedral gaps in the spinel blocks

Eu^{2+} , Yb^{2+}

Mn^{2+} , Co^{2+}

Cr^{3+} , Ti^{3+}

8.4 Energy Transfer

Example: ET in BaMgAl₁₀O₁₇:Eu co-doped by transition metal ions

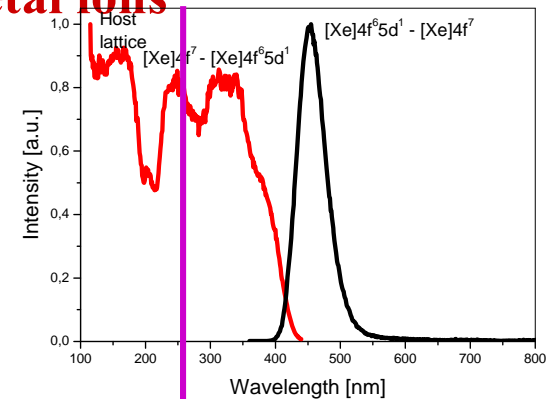
BaMgAl₁₀O₁₇:Eu

Eu²⁺ → (Eu²⁺)*

(Eu²⁺)* → Eu³⁺

Absorption 4f - 5d

Emission 5d - 4f



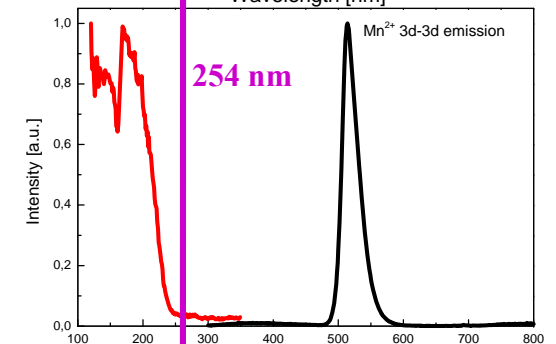
BaMgAl₁₀O₁₇:Mn

Mn²⁺ → (Mn²⁺)*

(Mn²⁺)* → Mn²⁺

Absorption 3d - 3d

Emission 3d - 3d



BaMgAl₁₀O₁₇:Eu,Mn

Eu²⁺ → (Eu²⁺)*

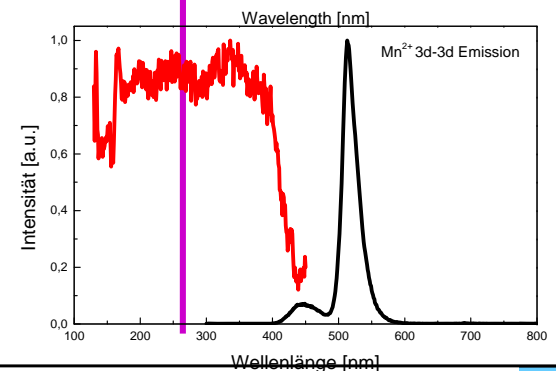
(Eu²⁺)* + Mn²⁺ → Eu²⁺ + (Mn²⁺)*

(Mn²⁺)* → Mn²⁺

Absorption 3d - 3d

ET from Eu to Mn

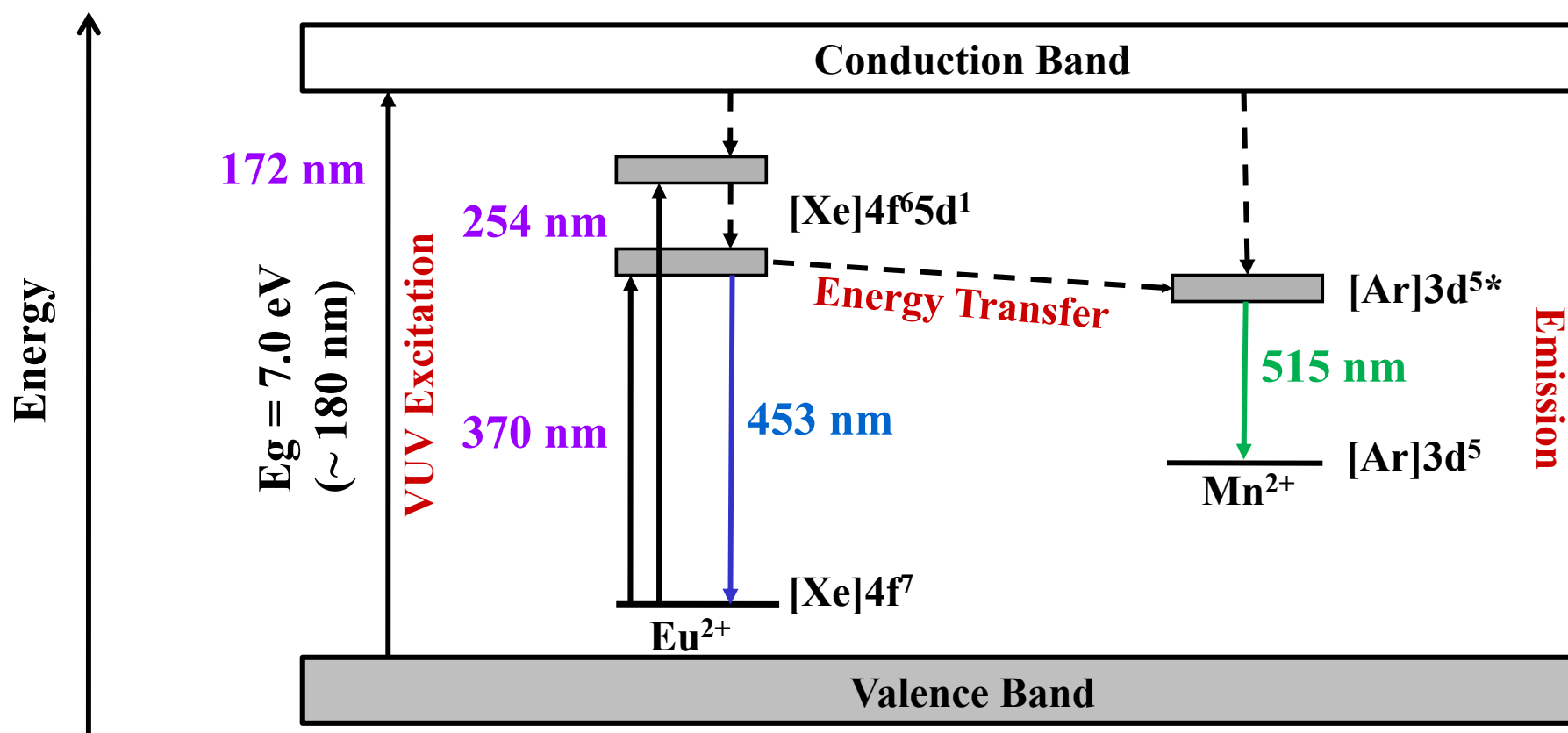
Emission 3d - 3d



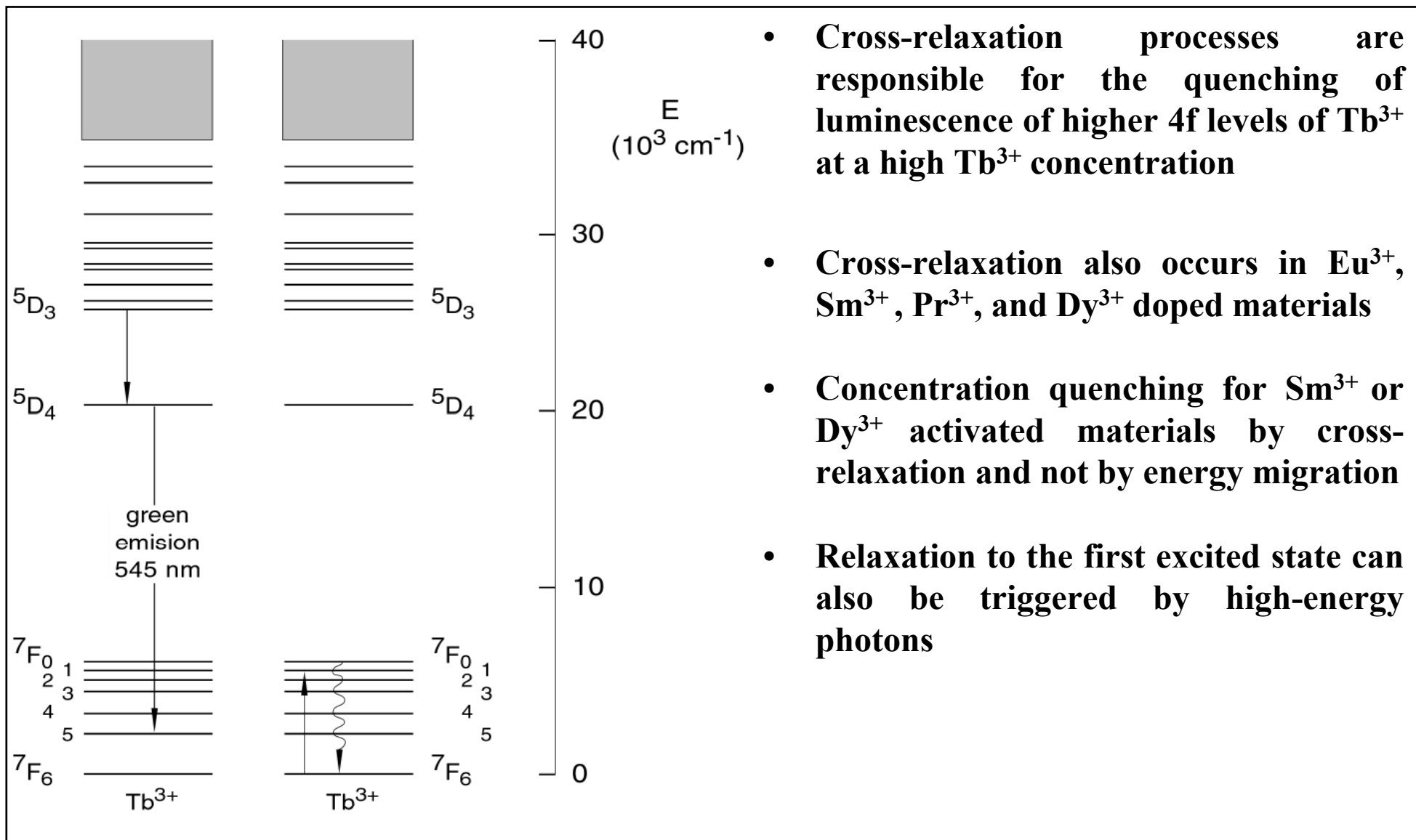
**BaMgAl₁₀O₁₇:Eu(Mn) can be excited at 172 nm, 254 and 370 nm
⇒ Application in PDPs, FLs (and near UV emitting LEDs)**

8.4 Energy Transfer

Energy pathways in $\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu},\text{Mn}$



8.5 Cross-Relaxation



- Cross-relaxation processes are responsible for the quenching of luminescence of higher 4f levels of Tb^{3+} at a high Tb^{3+} concentration
- Cross-relaxation also occurs in Eu^{3+} , Sm^{3+} , Pr^{3+} , and Dy^{3+} doped materials
- Concentration quenching for Sm^{3+} or Dy^{3+} activated materials by cross-relaxation and not by energy migration
- Relaxation to the first excited state can also be triggered by high-energy photons

8.6 Loss Processes

Overview of the most relevant processes leading to luminescence quenching

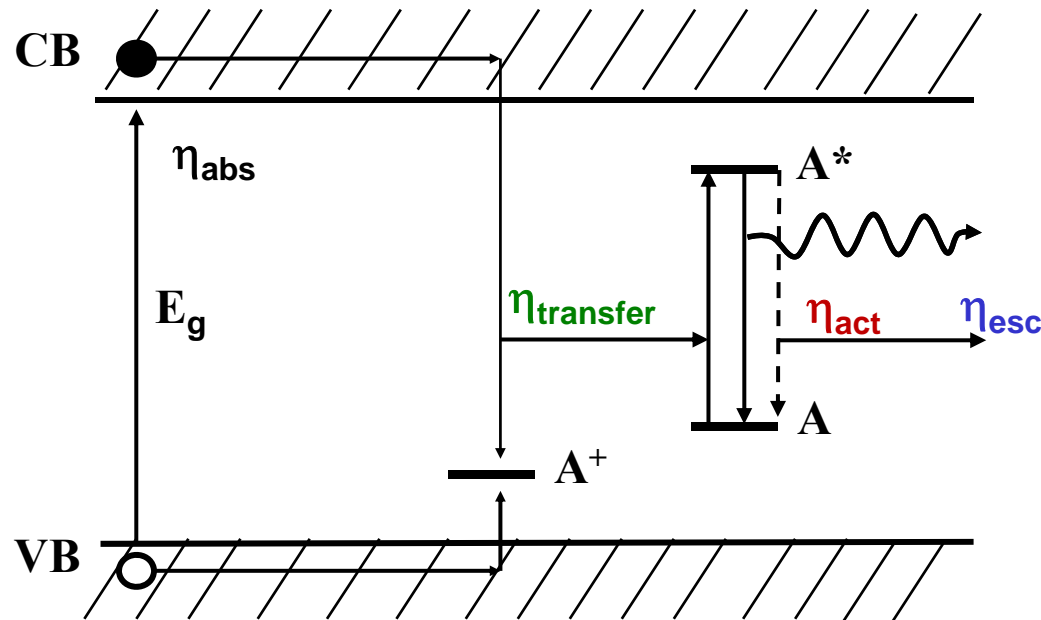
1. The absorbed energy does not reach the activator ion (η_{transfer})
 - a) Competitive absorption
 - b) ET to defects or non-luminescent impurity ions
 - c) Excited state absorption (ESA)
 - d) Auger processes

2. The absorbed energy reaches the activator ion, but non-radiative channels dominate the radiative return to the ground state (η_{act})
 - a) Crossing of excited and ground state parabola
 - b) Multi-phonon relaxation
 - c) Cross-relaxation
 - d) Photoionization
 - e) Energy transfer to quenching sites = $f(T)$

3. Emitted radiation is re-absorbed by the luminescent material (η_{esc})
 - a) Self-absorption due to spectral overlap between excitation and emission band
 - b) Additional absorption bands due to degradation of the material, e.g. by colour centre formation

8.6 Loss Processes

Related to the host lattice and host lattice activator interaction



Internal Quantum Efficiency

$$\begin{aligned} \text{IQE} &= \eta_{act} \\ &= \eta_r / (\eta_r + \eta_{nr}) \\ &= \tau / \tau_0 \end{aligned}$$

(Anti proportional to decay time)

External Quantum Efficiency

$$\begin{aligned} \text{EQE} &= N_{hv(\text{emitted})} / N_{hv(\text{absorbed})} \\ &= \eta_{transfer} * \eta_{act} * \eta_{esc} \end{aligned}$$

(No correlation to decay time!)

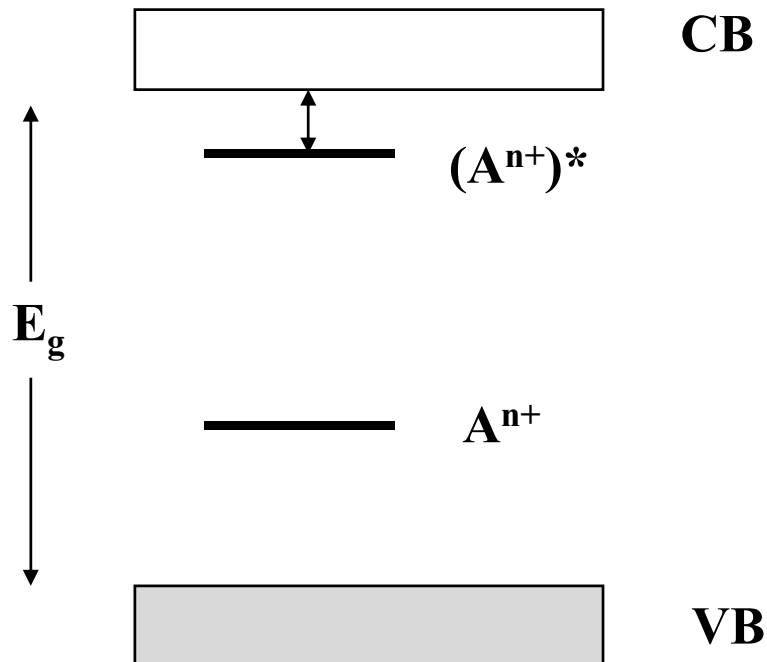
Light Yield

$$\text{LY} = \text{EQE} * \eta_{abs} = \text{EQE} * (1-R)$$

(No correlation to decay time!)

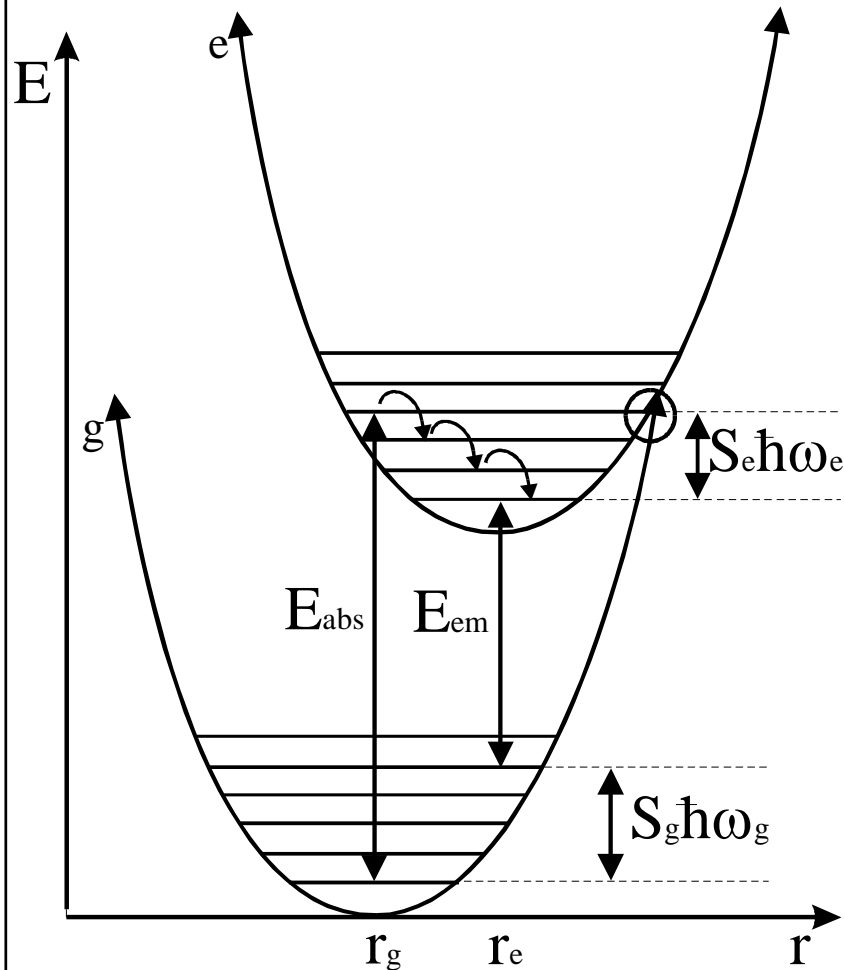
8.6 Loss Processes

Photoionization



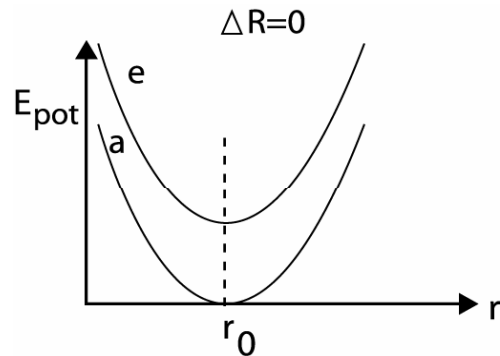
- Excited A^{n+} ion gets ionised
- Released electron is re-trapped, e.g. by anion vacancies
- Causes afterglow in
 - scintillators
 - persistent phosphors

8.7 Configuration Coordinate Diagram



- **Stokes shift**
Energy gap between absorption and emission band
 $S = S_e \hbar \omega_e + S_g \hbar \omega_g$
- **Full width at half maximum of the emission band**
 $FWHM \sim \sqrt{S}$
- **Thermal quenching decreases with increasing $\Delta R = r_e - r_g$**

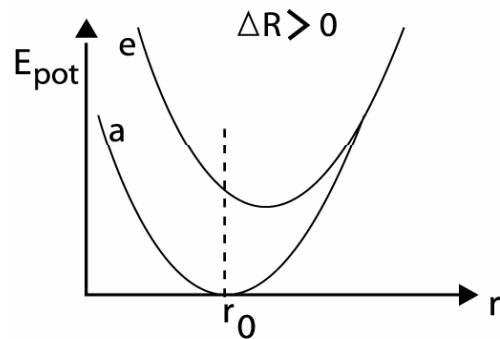
8.7 Configuration Coordinate Diagram



1. Weak to no electron-phonon-coupling

- High IQE, EQE determined by ET processes
- Thermal quenching mainly due to photoionization
- $4f \rightarrow 4f$ transitions (shielded 4f-shell: small crystal field splitting [CFS])

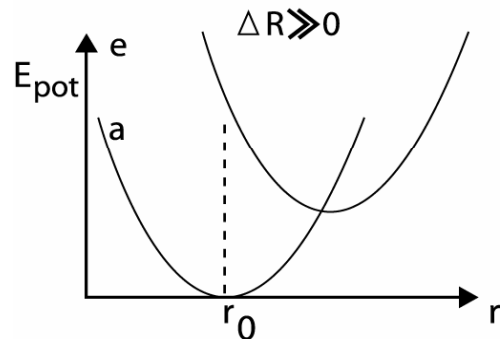
• **Lines** $\text{Eu}^{3+}, \text{Tb}^{3+}, \dots$



2. Moderate electron-phonon-coupling

- High to moderate IQE
- Thermal quenching due to tunnelling or photoioniz.
- $4f \rightarrow 5d$ transitions (large CFS)

• **Narrow bands** $\text{Eu}^{2+}, \text{Ce}^{3+}, \dots$



3. Strong electron-phonon-coupling

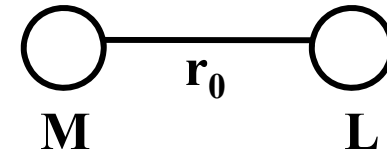
- High to low IQE at RT, strong thermal quenching
- Thermal quenching mainly due to tunnelling
- $ns^2 \rightarrow ns^1np^1$ or CT transitions

• **Broad bands** $\text{Pb}^{2+}, \text{Bi}^{3+}, \dots$

8.7 Configuration Coordinate Diagram

Width of the transitions can be explained by the model “harmonic oscillator”

$$F = -k*(r - r_0) \quad : \text{Integration}$$
$$\Rightarrow E = -1/2*k*(r - r_0)^2$$



Quantum mechanics provides: $E_v = (v + 1/2)*h\nu$

Franck-Condon principle: **Electrons motion is much faster than nuclear motion \rightarrow “vertical transitions”**

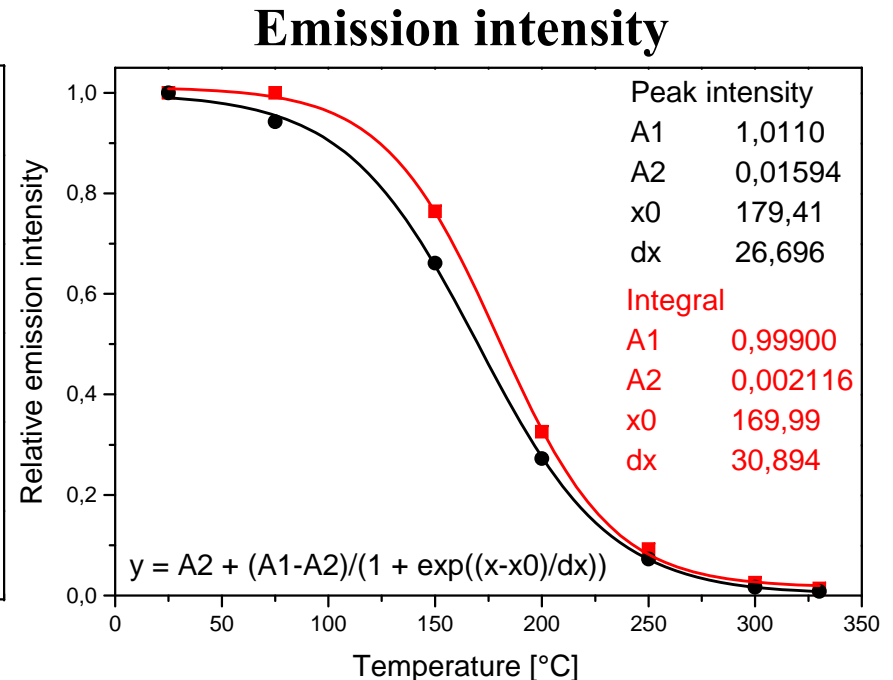
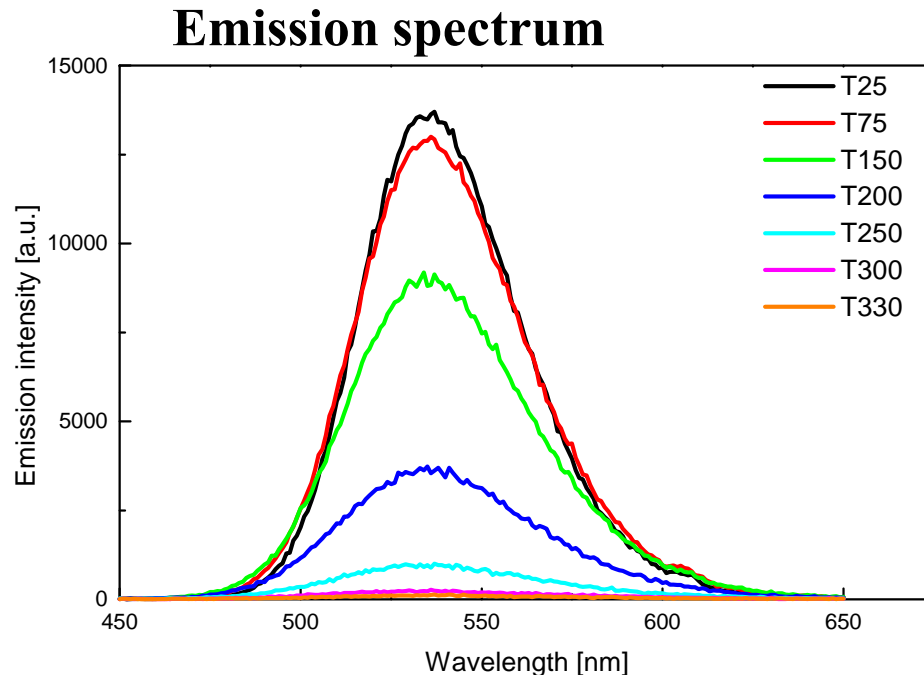
Transitions: $E_g(v_g = 0) \rightarrow E_e(v_e = x)$ for $v_e = 0$ “zero-phonon line”

$r_{0g} = r_{0e} \Rightarrow$ **narrow bands or lines ($4f \rightarrow 4f$ absorption lines)**

$r_{0g} < r_{0e} \Rightarrow$ **broad bands ($4f^n \rightarrow 4f^{n+1}L^{-1}$, $4f^n \rightarrow 4f^{n-1}5d$, $6s^2 \rightarrow 6s6p$)**

8.8 Thermal Quenching

Example: $\text{SrGa}_2\text{S}_4:\text{Eu}^{2+}$

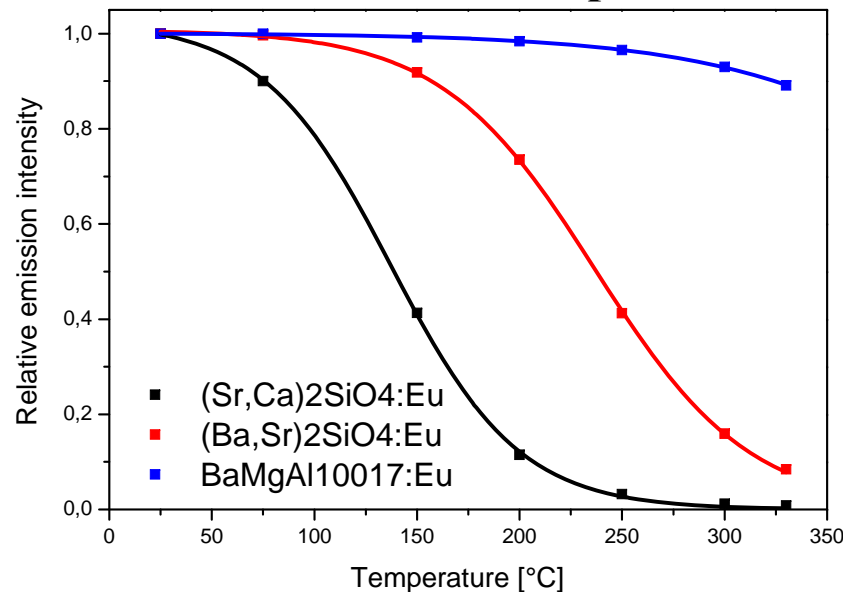


- $T_{1/2}$ = Temperature at which the phosphor loses 50% of its initial emission intensity (here $\sim 170^\circ\text{C}$)
- $T_{1/2}$ depends on the extent of the activator-host lattice interaction
- In many industrially important phosphors the quantum yield starts increasing distinctly between $100 - 150^\circ\text{C}$

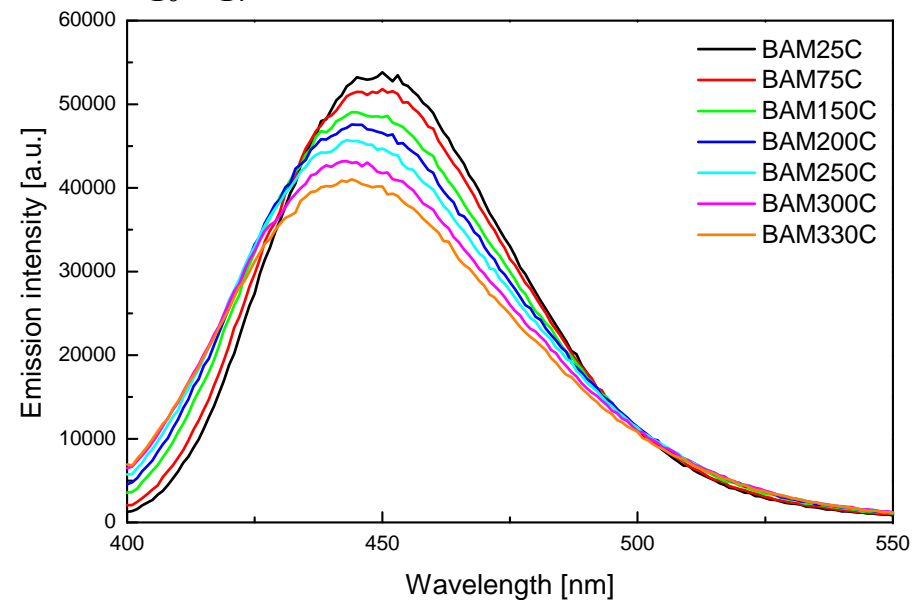
8.8 Thermal Quenching

Example: Other Eu^{2+} activated phosphors

Light yield
as a function of the temperature



Spectral width of the emission band of
 $\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}$ as a function of the temperature



Stokes shift

$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu} < (\text{Ba,Sr})_2\text{SiO}_4:\text{Eu} < (\text{Sr,Ca})_2\text{SiO}_4:\text{Eu}$

Thermal quenching

$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu} < (\text{Ba,Sr})_2\text{SiO}_4:\text{Eu} < (\text{Sr,Ca})_2\text{SiO}_4:\text{Eu}$

Blue shift due to thermal expansion of the host lattice and thus reduction in crystal field splitting

8.8 Thermal Quenching

Some Rules

- **Increases with increasing energy separation of the ground and excited state**
- **Increases with increasing phonon frequencies (thus most organic compounds exhibit luminescence only at low temperatures)**
- **Increases with $\Delta r = r_e - r_g$**
- **Thermal quenching due to photoionization concerns luminescent materials, where the excited state is located close to the conduction band**

8.9 Lifetime of the Excited State

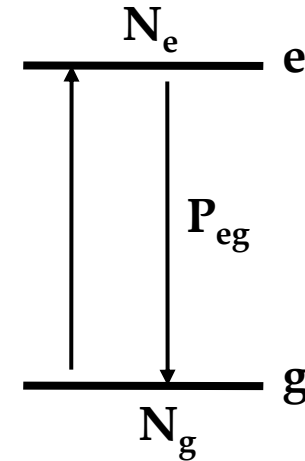
Description equal to 1st order kinetics (no energy transfer!)

$$dN_e/dt = -N_e * P_{eg}$$

$$\Rightarrow dN_e/N_e = -P_{eg} * dt : \text{Integration}$$

$$\Rightarrow \ln(dN_e(t)/N_e(0)) = -P_{eg} * t$$

$$\Rightarrow N_e(t) = N_e(0) * \exp(-P_{eg}/\tau) \text{ with } \tau = 1/P_{eg}$$

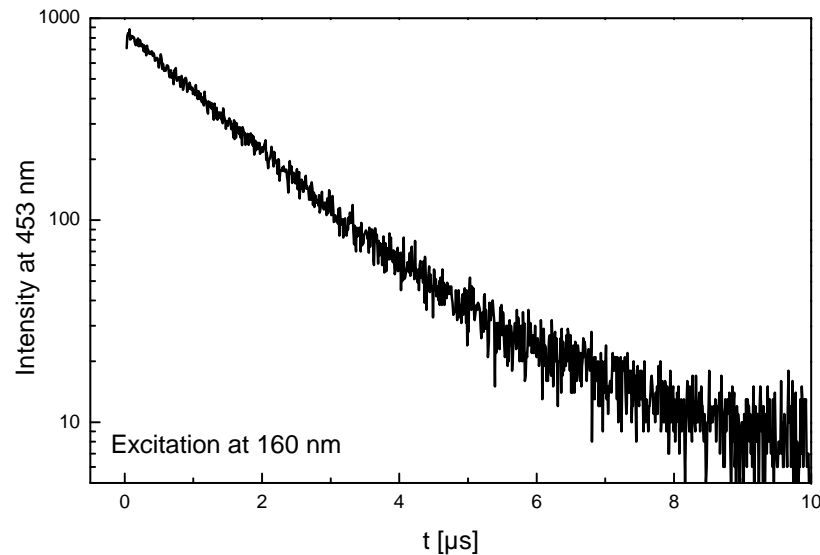


Transition	Time scale	Oscillator strength	Activators
“allowed”	$\sim 10^{-9}$ s	$f \sim 0.1$	$\text{Eu}^{2+}, \text{Ce}^{3+}$
“weak”	$\sim 10^{-6}$ s	$f \sim 0.001$	$\text{Pr}^{3+}, \text{Nd}^{3+}$
“forbidden”	$\sim 10^{-3}$ s	$f \sim 10^{-5}$	$\text{Eu}^{3+}, \text{Mn}^{2+}$

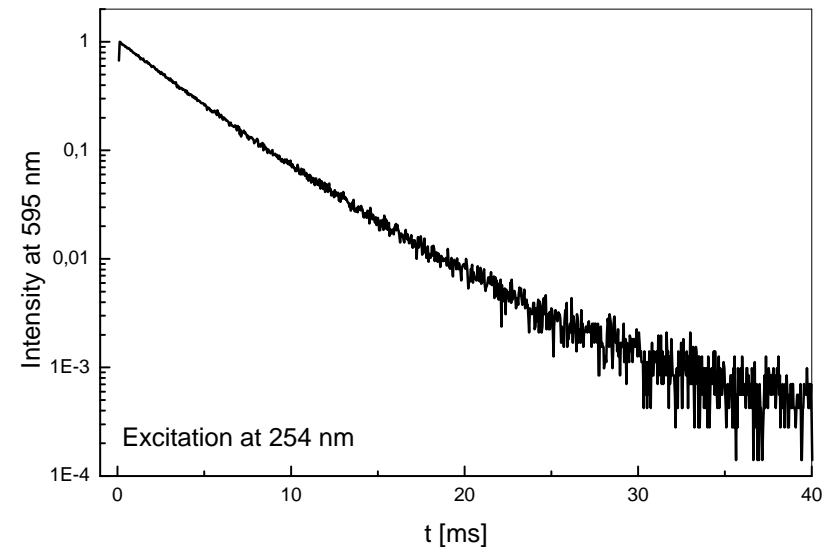
8.9 Lifetime of the Excited State

Typical decay curves

BaMgAl₁₀O₁₇:Eu²⁺ ($\tau = 1 \mu\text{s}$)



(Y,Gd)BO₃:Eu³⁺ ($\tau = 3.5 \text{ ms}$)



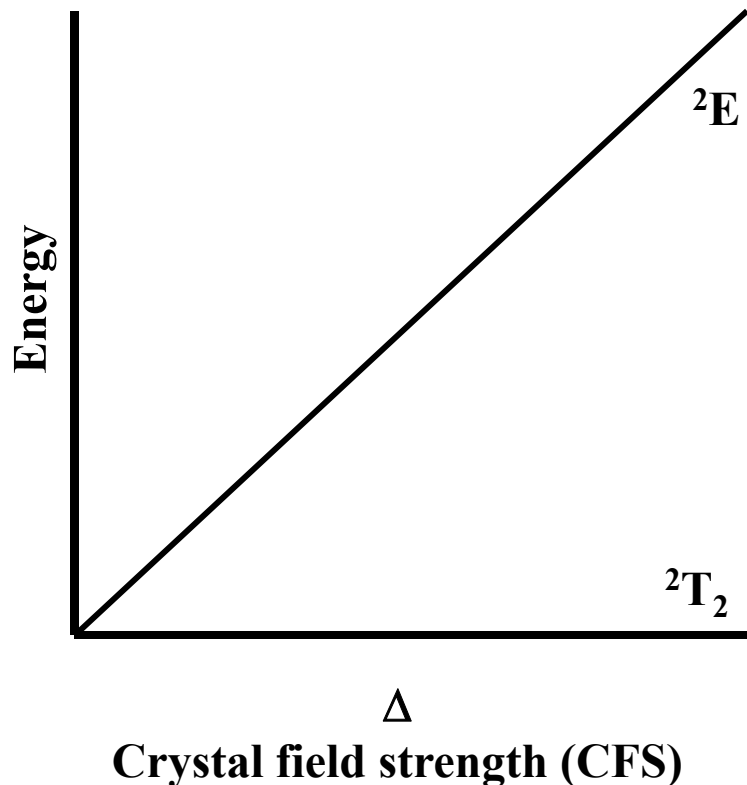
Mono-exponential decay \Rightarrow No energy transfer e.g. to impurities such as Fe³⁺ or Cr³⁺

Deviation from mono-exponential decay \Rightarrow quenching, energy transfer, afterglow,

8.10 Luminescence of Transition Metal Ions

Absorption processes of d^n -ions \rightarrow Tanabe-Sugano diagram

Energy level diagram of a d^1 -ion (Ti^{3+} , V^{4+} , Cr^{5+} , Mn^{6+}): $\text{CFS} \Rightarrow {}^2\text{D}_{3/2} \rightarrow {}^2\text{T}_2 + {}^2\text{E}$



Ion	Configuration	Example
Ti^{3+}	$[\text{Ar}]d^1$	$\text{Al}_2\text{O}_3:\text{Ti}$ (Sapphire)
Cr^{3+}	$[\text{Ar}]d^3$	$\text{Al}_2\text{O}_3:\text{Cr}$ (Ruby)
Mn^{4+}	$[\text{Ar}]d^3$	$\text{Mg}_4\text{GeO}_{5.5}\text{F}:\text{Mn}$
Mn^{2+}	$[\text{Ar}]d^5$	$\text{Zn}_2\text{SiO}_4:\text{Mn}$ (Willemite)
Fe^{3+}	$[\text{Ar}]d^5$	$\text{LiAlO}_2:\text{Fe}$

d - d transitions are parity-forbidden

\Rightarrow low absorption coefficient

\Rightarrow high concentration needed

8.10 Luminescence of Transition Metal Ions

Absorption in glasses, laser crystals and phosphors

Ion	Configuration	Colour	Pigment	Structure type
Ti ³⁺	d ¹	violet, brown		
V ³⁺	d ²	green		
V ⁴⁺	d ¹	green, blue	(Zr,V)SiO ₄	Zircon
Cr ³⁺	d ³	green, yellow	Cr ₂ O ₃	Corundum
Mn ²⁺	d ⁵	light pink	MnO	NaCl
Mn ³⁺	d ⁴	violet	Mn ₂ O ₃	Corundum
Mn ⁴⁺	d ³	red, brown	MnO ₂	Rutile
Fe ³⁺	d ⁵	yellow, brown	Fe ₂ O ₃	Corundum
Fe ²⁺	d ⁶	blue, green	Fe(C ₂ O ₄)·2H ₂ O	
Co ²⁺	d ⁷	blue, violet	CoAl ₂ O ₄	Spinel
Ni ²⁺	d ⁸	green	NiO	NaCl
Cu ²⁺	d ⁹	blue, green	CuO	

8.10 Luminescence of Transition Metal Ions

Absorption processes of transition metal ions with d^0 -configuration

Examples: VO_4^{3-} , NbO_4^{3-} , TaO_4^{3-} , CrO_4^{2-} , MoO_4^{2-} , WO_4^{2-} , MnO_4^-

Absorption due to ligand to metal charge-transfer (LMCT)

$\text{O}^{2-} \rightarrow \text{Me}^{n+}$ or $p(\text{non-bonding}) \rightarrow d(e_g: \text{anti-bonding})$

Bond is weakened $\Rightarrow \Delta R \gg 0 \Rightarrow$ broad absorption band

<u>Phosphor</u>	<u>Absorption [cm^{-1}]</u>	<u>CN</u>	<u>Polyhedron</u>
CaWO_4	40000	4	Tetrahedron
Ca_3WO_6	35000	6	Octahedron

\Rightarrow Position of the CT state decreases with increasing CN and effective charge of the metal center

8.11 Luminescence of Ions with s²-Configuration

Examples: Ga⁺, In⁺, Tl⁺, Ge²⁺, Sn²⁺, Pb²⁺, As³⁺, Sb³⁺, Bi³⁺

Electron configuration of s²-ions

Ga⁺, Ge²⁺ and As³⁺:

[Ar]3d¹⁰4s²

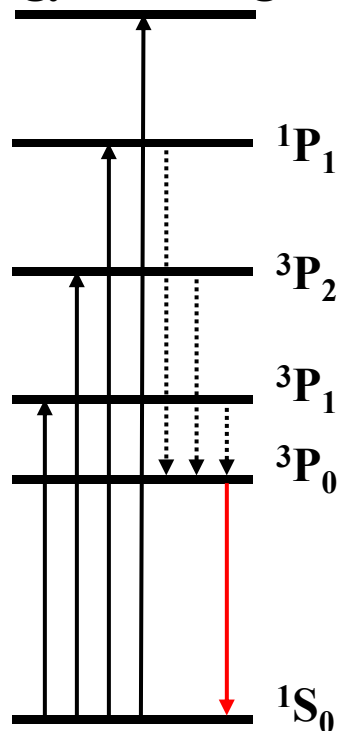
In⁺, Sn²⁺ and Sb³⁺:

[Kr]4d¹⁰5s²

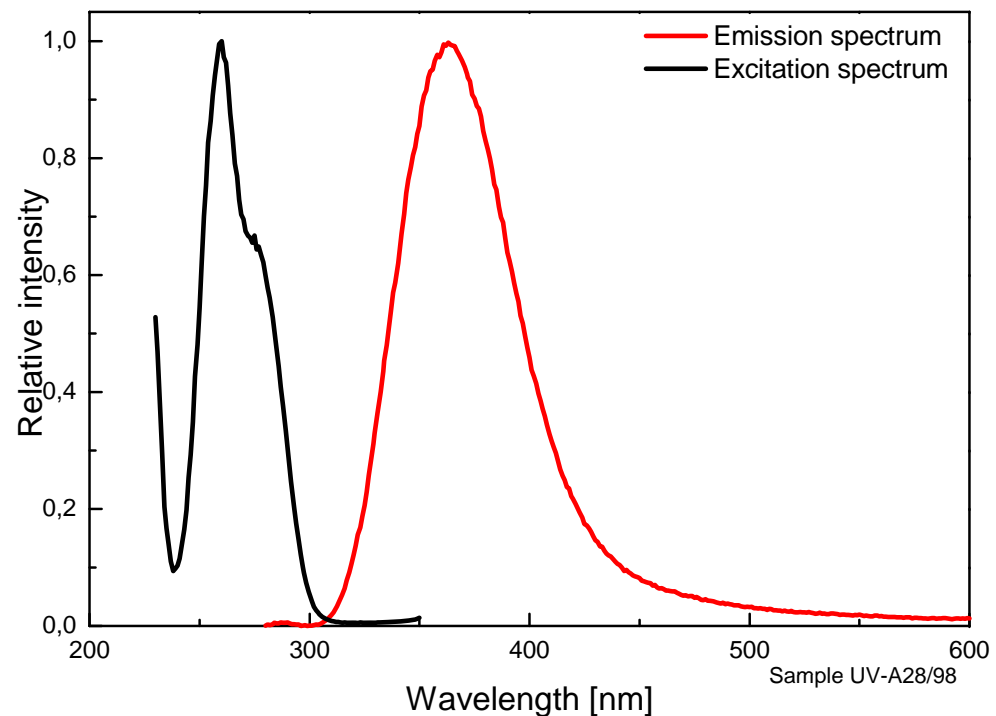
Tl⁺, Pb²⁺ and Bi³⁺:

[Xe]4f¹⁴5d¹⁰6s²

Energy level diagram of s²-ions

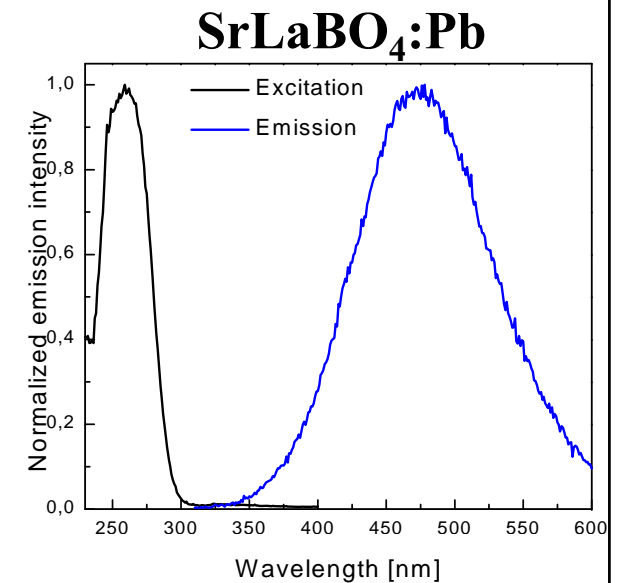
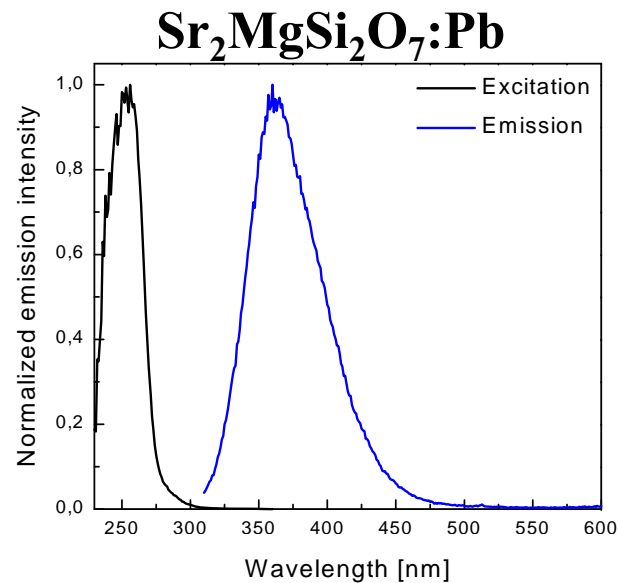
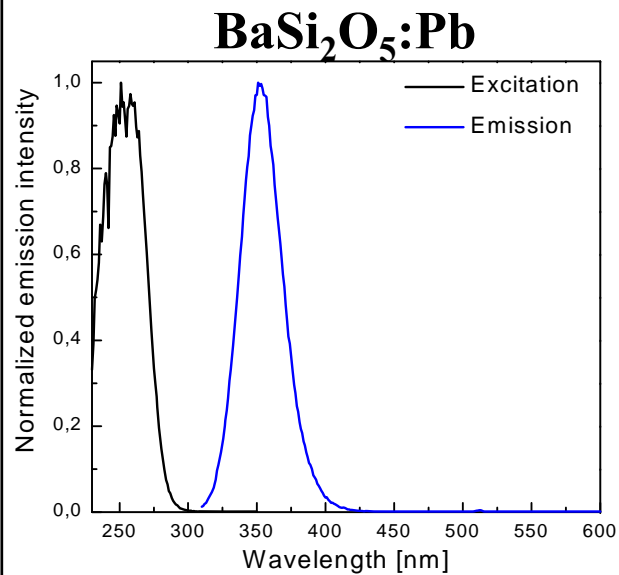


Excitation and emission spectra of BaYB₉O₁₆:Sb³⁺



8.11 Luminescence of Ions with s²-Configuration

Example: Pb²⁺ Luminescence process: $[\text{Xe}]4f^{14}5d^{10}6s^2 \rightarrow [\text{Xe}] 4f^{14}5d^{10}6s^1 6p^1$

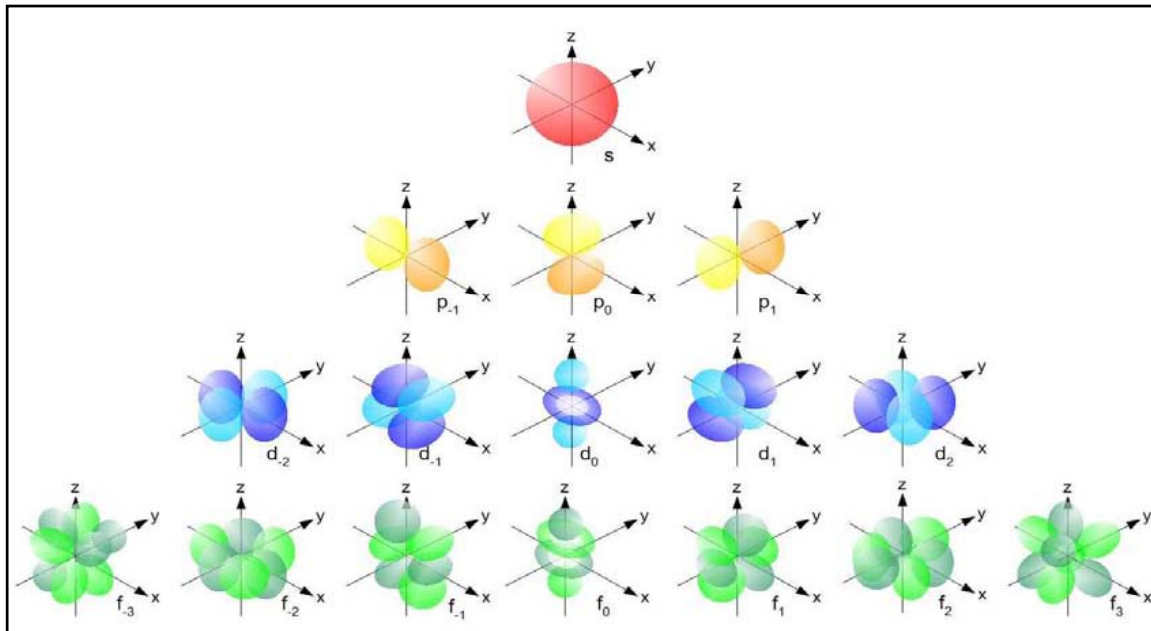


Phosphor	Structure type	Stokes shift [cm ⁻¹]	Half width [cm ⁻¹]	QA [%]
BaSi ₂ O ₅ :Pb	Sanbornite	10600	2700	90
Sr ₂ MgSi ₂ O ₇ :Pb	Akermanite	12000	4300	75
SrLaBO ₄ :Pb		17700	5300	65

8.12 Luminescence of Rare Earth Ions

Properties of electronic orbitals

Shape and orientation



Orbital	Parity	l	m_l
s	g	0	0
p	u	1	-1, 0, 1
d	g	2	-2, ..., 2
f	u	3	-3, ..., 3

8.12 Luminescence of Rare Earth Ions

Electron configuration of rare earth metals and ions

Metals

[Xe]	La	Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
6s	2	2	2	2	2	2	2	2	2	2	2	2	2	2	2
5d	1	0	0	0	0	0	0	1	0	0	0	0	0	0	1
4f	0	2	3	4	5	6	7	7	9	10	11	12	13	14	14

Ions

[Xe]	La ³⁺	Ce ³⁺	Pr ³⁺	Nd ³⁺	Pm ³⁺	Sm ³⁺	Eu ³⁺	Gd ³⁺	Tb ³⁺	Dy ³⁺	Ho ³⁺	Er ³⁺	Tm ³⁺	Yb ³⁺	Lu ³⁺
	Ce ⁴⁺	Pr ⁴⁺	Nd ⁴⁺				Sm ²⁺	Eu ²⁺						Tm ²⁺	Yb ²⁺
4f	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14

Example

m_l	-3	-2	-1	0	1	2	3	-2	-1	0	1	2	0	-1	0	1
Gd ³⁺ /Eu ²⁺	↑	↑	↑	↑	↑	↑	↑						↑			
	4f							5d					6s	6p		

$$S = \sum s = 7/2$$

$$\rightarrow 2S+1 = 8$$

→ strongly paramagnetic ions

$$L = |\sum l| = 0$$

$$\rightarrow \text{„S“}$$

→ LS-Term symbol ⁸S

Spectroscopic
Terms

$$2S+1LJ$$

8.12 Luminescence of Rare Earth Ions

History of distangling the energy level structure

1908 Becquerel

Sharp lines in optical spectra of lanthanide ions

1937 Van Vleck

The Puzzle of Rare-Earth Spectra in Solids

1960s Judd, Wybourne, Dieke, Carnall

Theory for energy level structure and transition probabilities of 4f-4f transitions

8.12 Luminescence of Rare Earth Ions

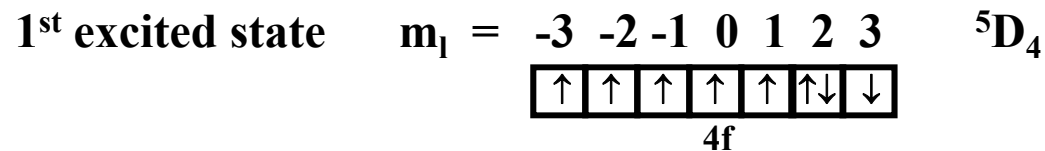
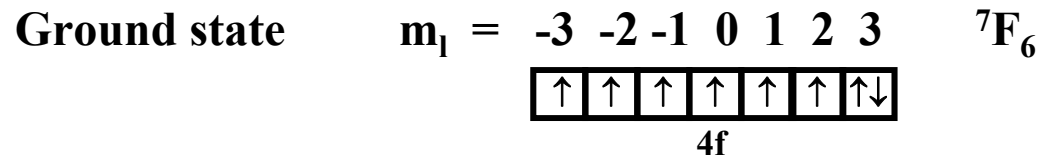
Energy level structure of $[\text{Xe}]4f^n$ ions

Partly filled 4f-shell results in multiple electron configurations

Example: $\text{Tb}^{3+} [\text{Xe}]4f^8 \rightarrow 8$ electrons in 7 f-orbitals: **3003** different arrangements!

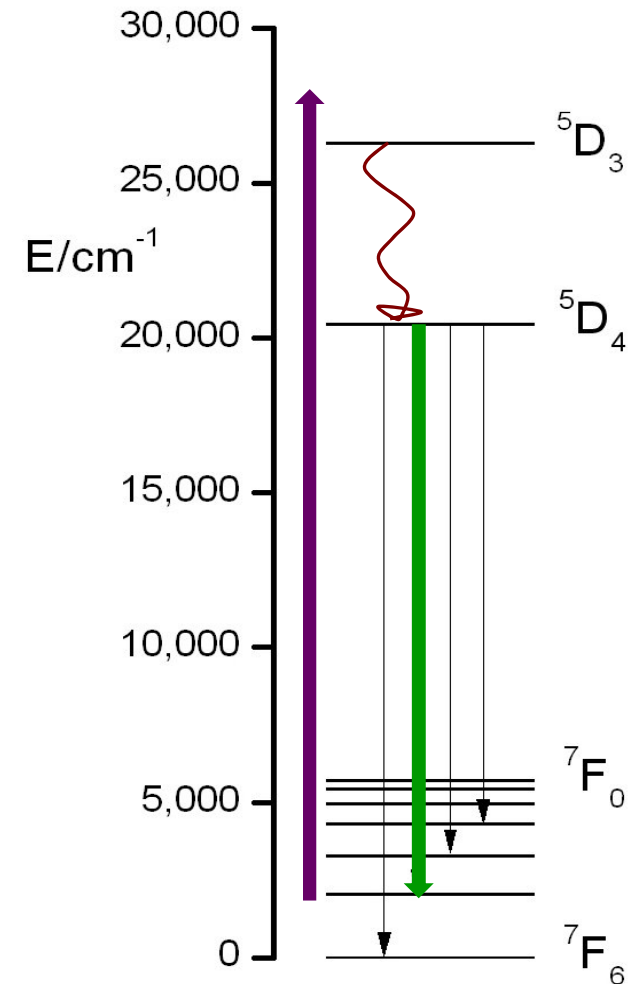
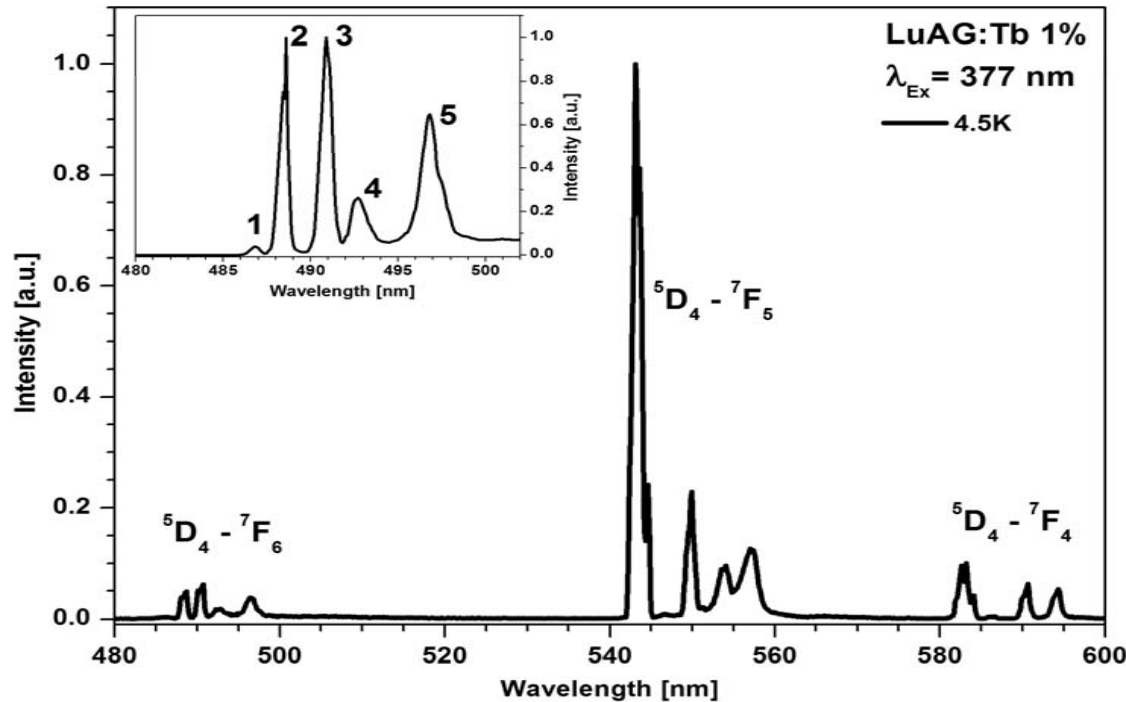
Free ion energy levels due to:

1. Electrostatic interactions (comparable to $3d^n$ ions)
2. Spin-orbit coupling (larger than for $3d^n$ ions)
3. Crystal field splitting (smaller than for $3d^n$ ions)



8.12 Luminescence of Rare Earth Ions

Typical emission spectrum of Tb^{3+} (Example: $Lu_3Al_5O_{12}:Tb$)

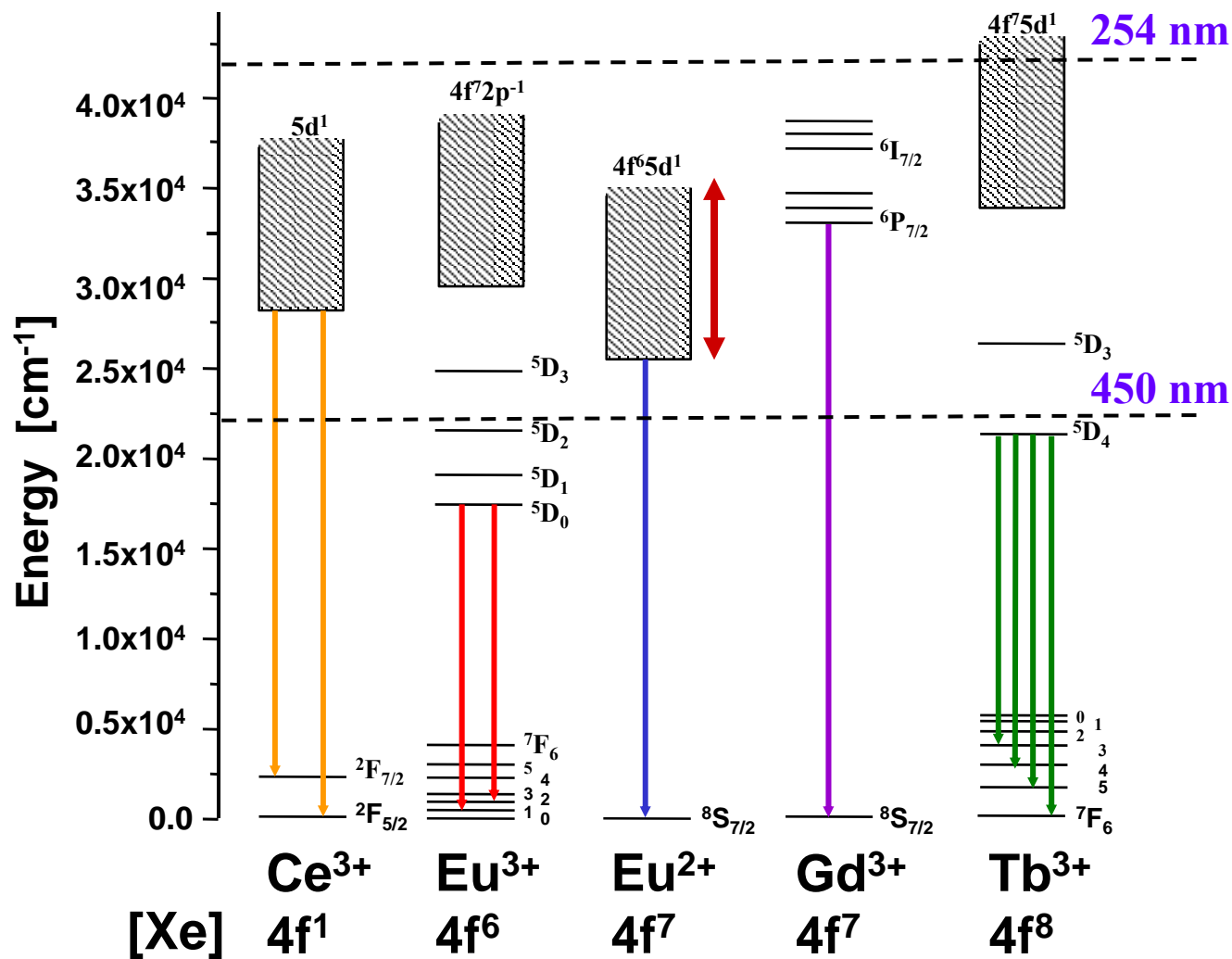


Characteristic luminescence of lanthanides

- Sharp emission lines
- Almost independent of chemical environment, e. g. green-yellow emission of Tb^{3+} phosphors
- High quantum yield (> 90%), due to small Stokes shift

8.12 Luminescence of Rare Earth Ions

Simplified energy level diagram of selected Ln³⁺ ions



Line emitting ions

- Pr³⁺
- Nd³⁺
- Sm^{2+/3+}
- Eu³⁺ (Eu²⁺)
- Gd³⁺
- Tb³⁺
- Dy³⁺
- Ho³⁺
- Er³⁺
- Tm³⁺
- Yb³⁺

Band emitting ions

- Ce³⁺
- Pr³⁺
- Nd³⁺
- Eu²⁺
- Yb²⁺

8.12 Luminescence of Rare Earth Ions

1. Electrostatic interactions

Shielding due to inner electrons described by the so-called Slater parameters
(comparable to Racah parameters)

$$F^{(k)} = \frac{e^2}{4\pi\epsilon_0} \int_0^\infty \int_0^\infty \frac{r_{<}^k}{r_{>}^{k+1}} [R'_{4f}(r_i)R'_{4f}(r_j)]^2 r_i^2 r_j^2 dr_i dr_j$$

Electrostatic interaction increases with effective charge on
the activator ion (ion charge density)

Therefore splitting between different terms depends on

- Oxidation state
- Nucleus charge
- Charge flow back from ligands (polarizability of surrounding anions)

8.12 Luminescence of Rare Earth Ions

2. Spin-orbit coupling

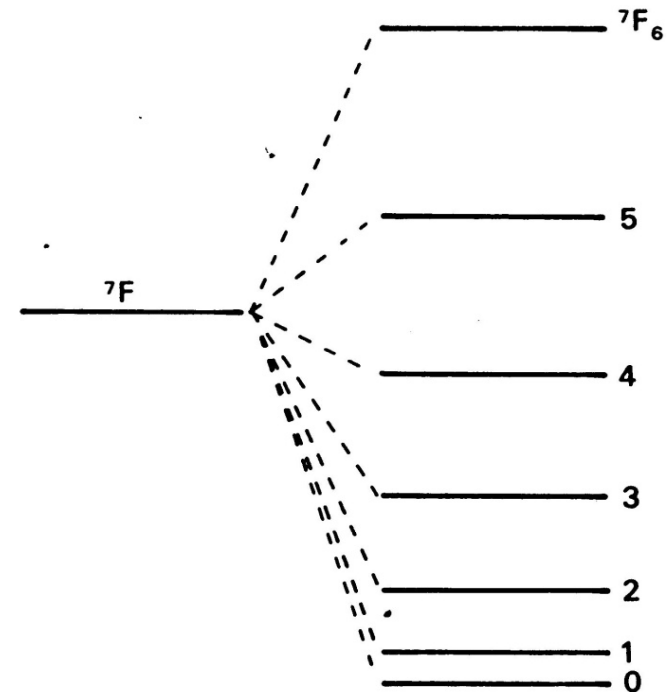
Spin-orbit coupling constant ζ increases throughout the lanthanide series, i.e. from $\zeta(\text{Ce}) = 650 \text{ cm}^{-1}$ to $\zeta(\text{Yb}) = 2930 \text{ cm}^{-1}$

Further splitting of LS terms into J -levels by energy, assuming weak spin-orbit coupling:

→ Complete term symbol:

$$2S+1L_J \quad \text{with } |L-S| < J < L+S$$

For Tb^{3+} Ground state: ${}^7F_{6,5,4,3,2,1,0}$
Excited state: ${}^5D_{4,3,2,1,0}$

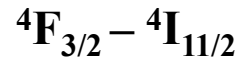
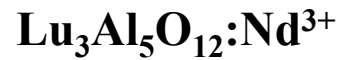


8.12 Luminescence of Rare Earth Ions

3. Crystal field splitting

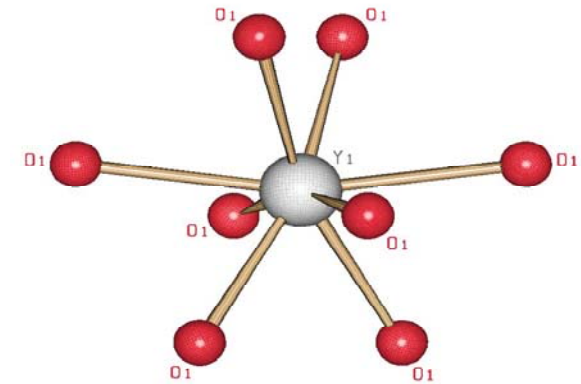
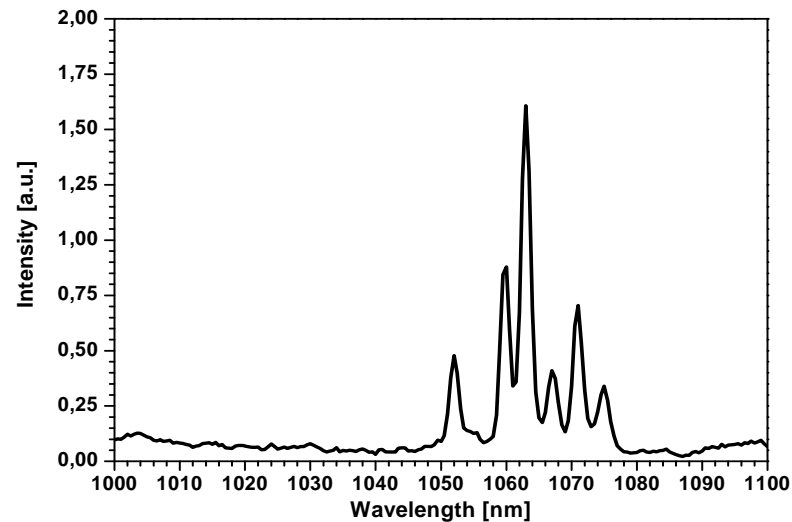
Further splitting of J multiplets into a maximum of $2J+1$ levels

Crystal field splitting $\sim 100 \text{ cm}^{-1}$ + sensitive function of site symmetry



$\Delta E = 203 \text{ cm}^{-1}$

six levels without
external magnetic
field



Dodecahedral coordination

Extra fitting parameters B_kq to graphically fit experimentally observed levels:

$$\mathcal{H}_c^{O_h} = B_0^4 \left[C_0^{(4)} + \sqrt{\frac{5}{14}} (C_{-4}^{(4)} + C_4^{(4)}) \right] + B_0^6 \left[C_0^{(6)} - \sqrt{\frac{7}{2}} (C_{-4}^{(6)} + C_4^{(6)}) \right]$$

8.12 Luminescence of Rare Earth Ions

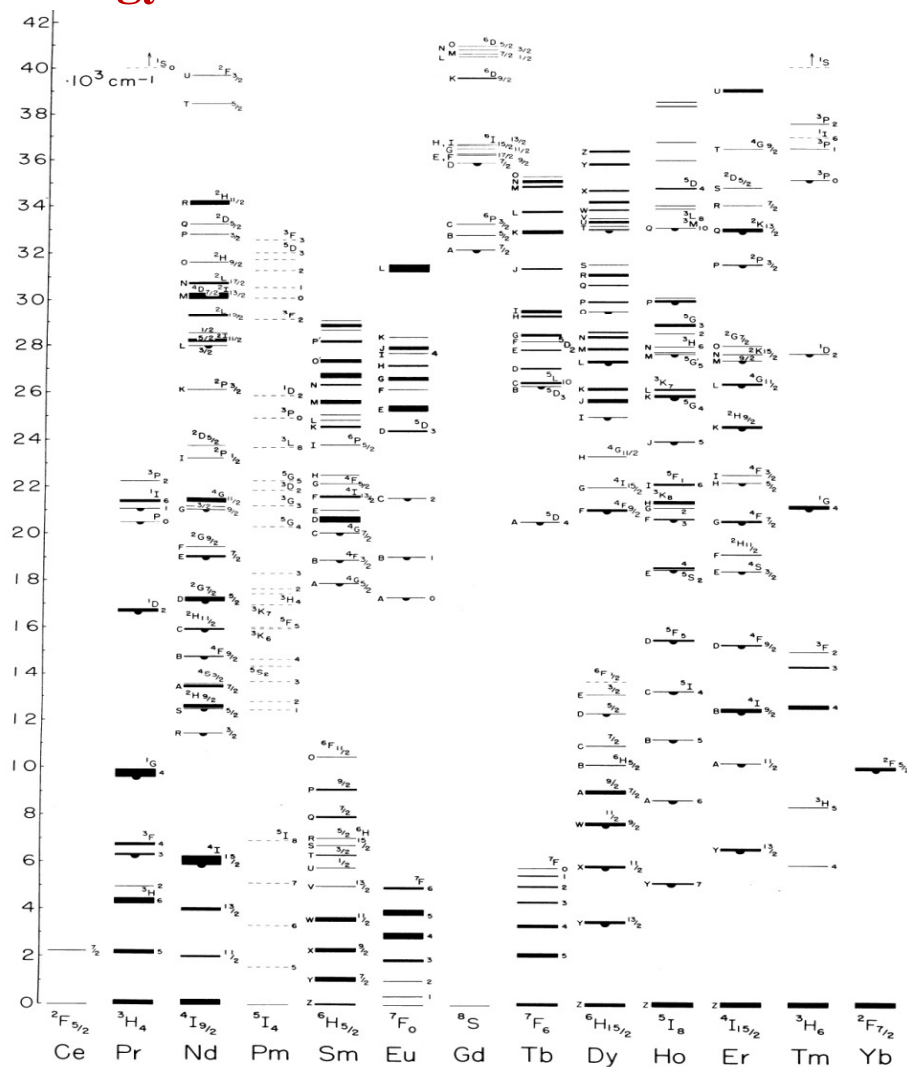
In summary: RE ions exhibit a great number of energy levels $2S+1L_J$

	Ce (Yb)	Pr (Tm)	Nd (Er)	Pm (Ho)	Sm (Dy)	Eu (Tb)	Gd
n	1	2	3	4	5	6	7
SL	1	7	17	47	73	119	119
SLJ	2	13	41	107	198	295	327
SLJM	4	91	364	1001	2002	3003	3432

**Early experimental and theoretical work on $\text{LaCl}_3:\text{Ln}^{3+}$ and $\text{LaF}_3:\text{Ln}^{3+}$ by Dieke and Carnall (experiment) and Judd, Crosswhite and Wybourne (theory):
“Dieke diagram” and the “Blue book”**

8.12 Luminescence of Rare Earth Ions

Dieke diagram (1968): Energy levels of trivalent RE ions

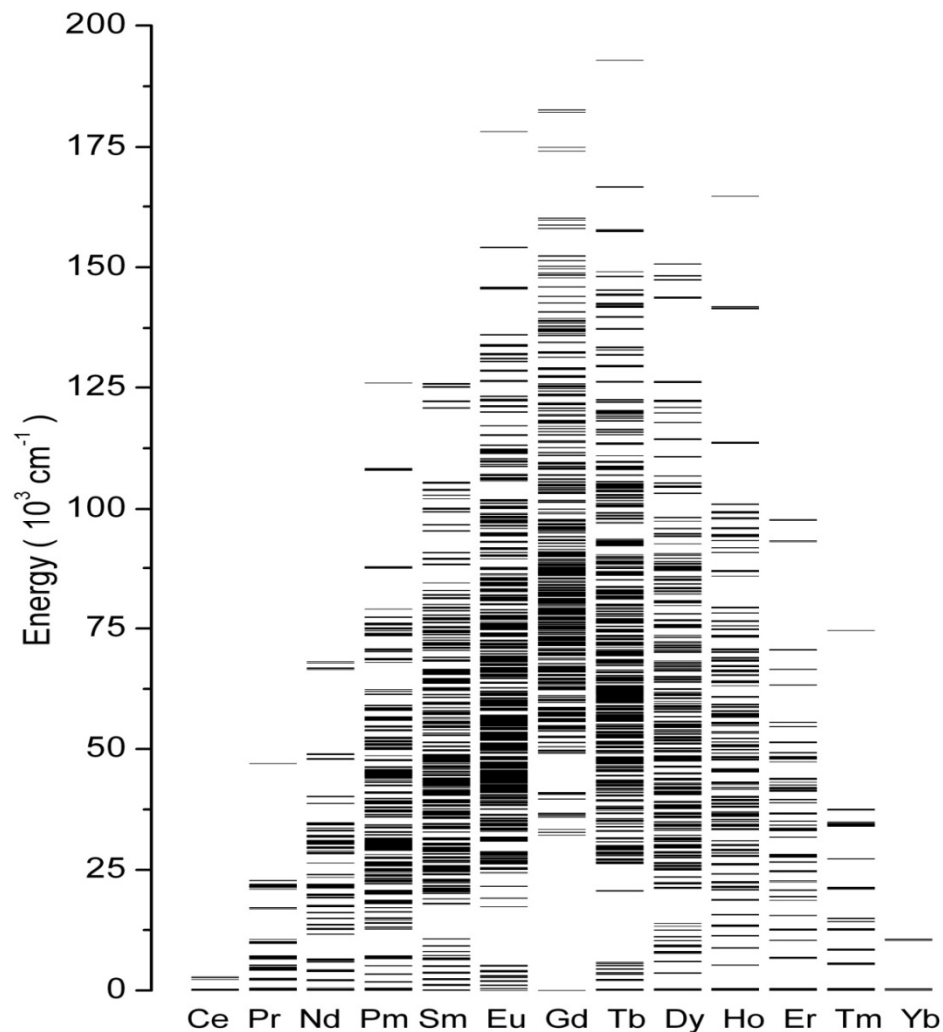


8.12 Luminescence of Rare Earth Ions

Complete energy level diagram

Ce³⁺	~	Yb³⁺
Pr³⁺	~	Tm³⁺
Nd³⁺	~	Er³⁺
Pm³⁺	~	Ho³⁺
Sm³⁺	~	Dy³⁺
Eu³⁺	~	Tb³⁺
Gd³⁺		

Energy level splitting increases from Ce³⁺ to Yb³⁺ due to increasing nucleus charge

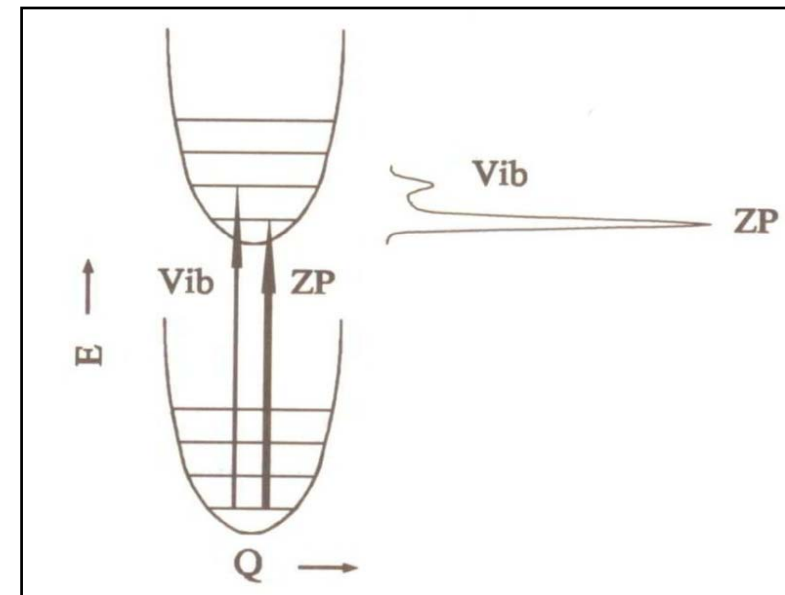


8.12 Luminescence of Rare Earth Ions

Characteristic optical properties

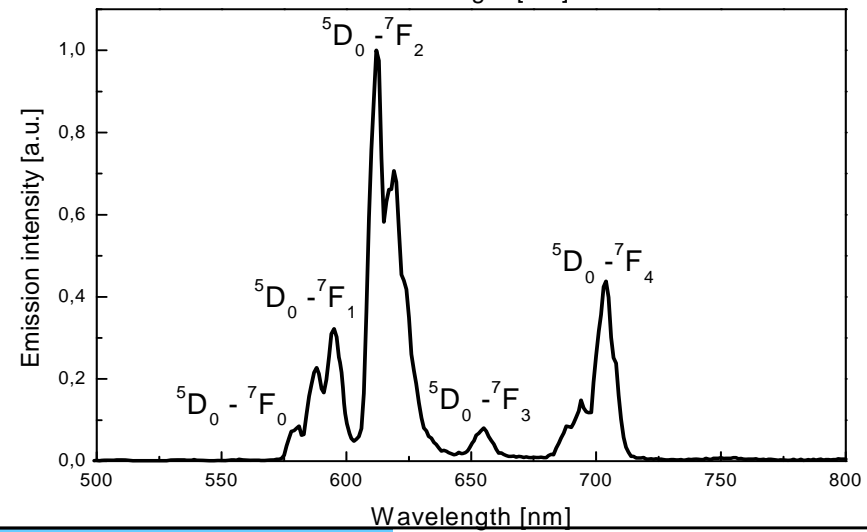
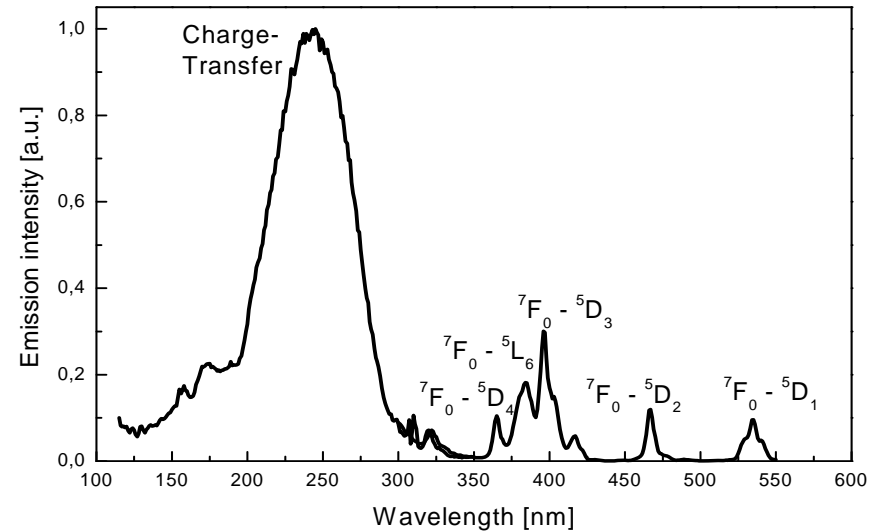
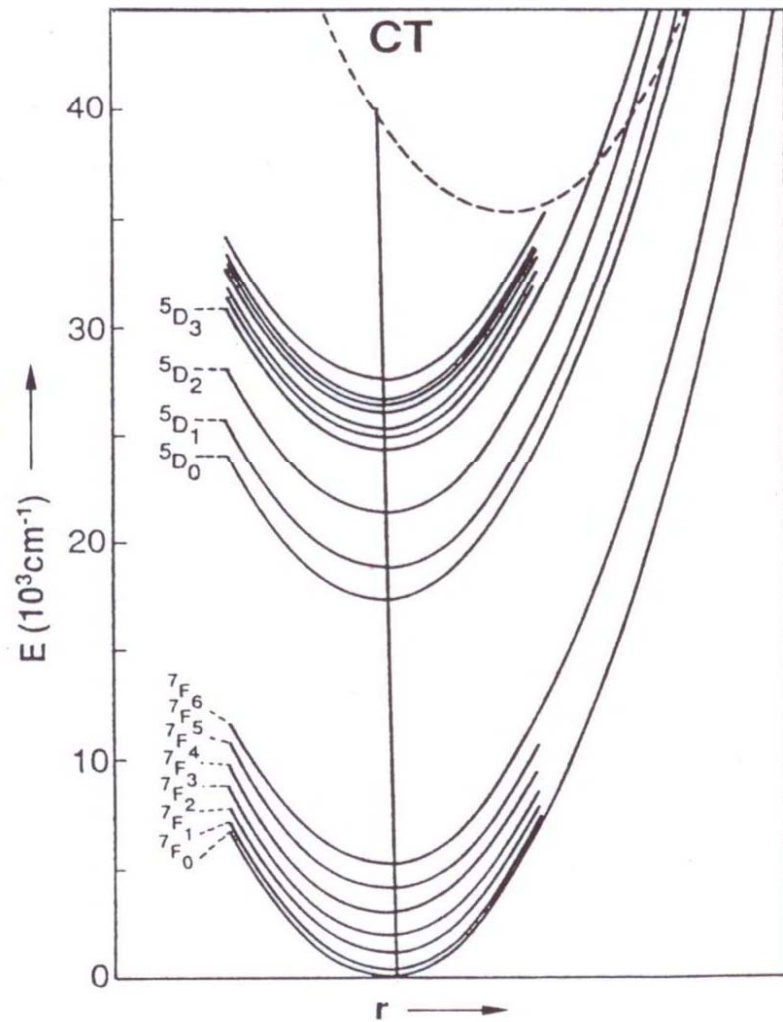
- 1) Sharp lines (atomic like), Stokes shift $\sim 0 \text{ cm}^{-1}$
- 2) Little influence of environment on energy level scheme
- 3) Parity forbidden transitions ($\sim \text{ms}$ life time, $f \sim 10^{-5}$)

Origin: Shielding of $4f^n$ electrons
by outer filled $5s$ and $5p$ shells
→ no shift of excited state parabola
and strong zero-phonon lines (ZPL)



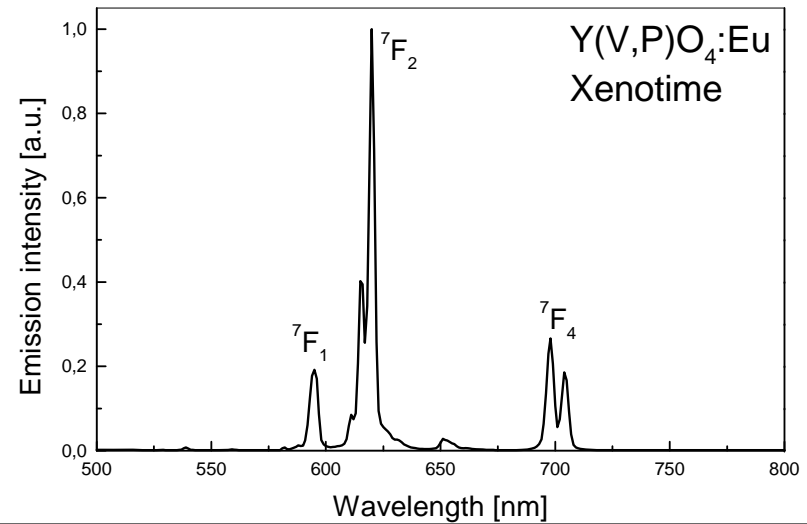
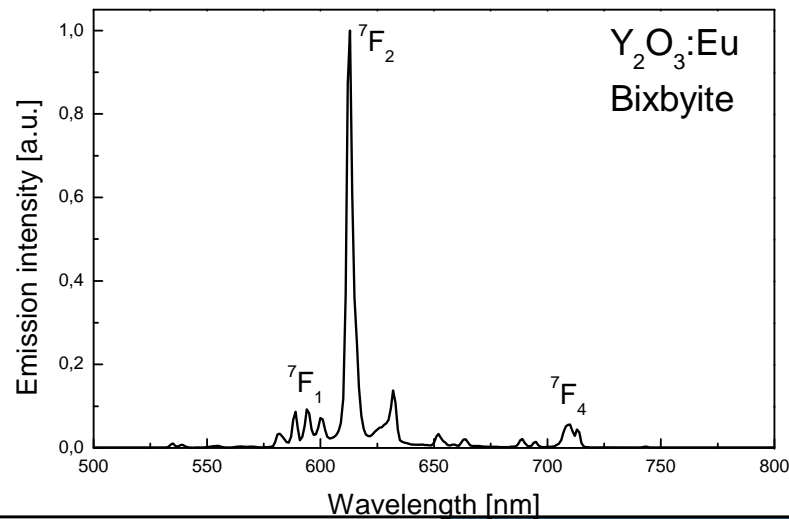
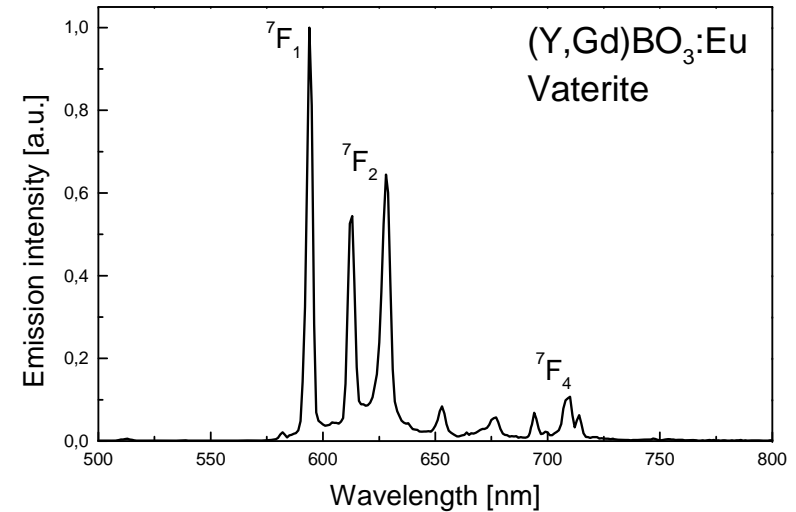
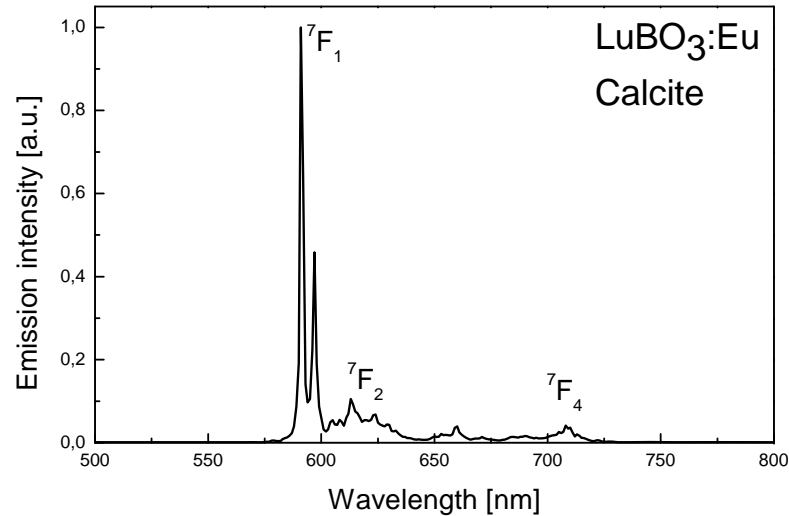
8.12 Luminescence of Rare Earth Ions

Example: Eu^{3+} - Typical excitation and emission spectra ($\text{Y}_2\text{SiO}_5:\text{Eu}$)



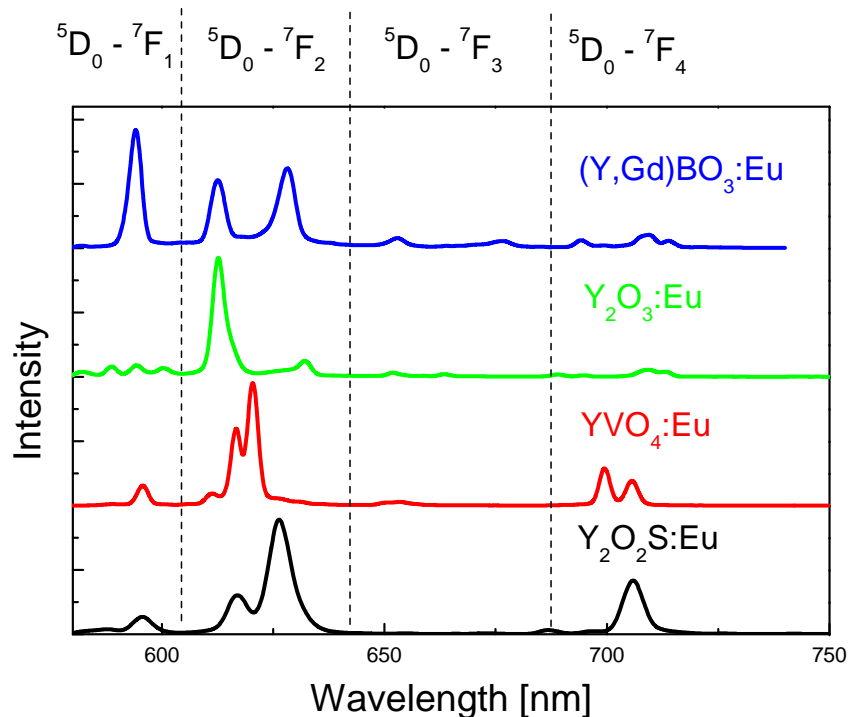
8.12 Luminescence of Rare Earth Ions

Emission spectra and colour points of Eu^{3+} activated phosphors



8.12 Luminescence of Rare Earth Ions

Emission spectra and colour points of Eu^{3+} activated phosphors

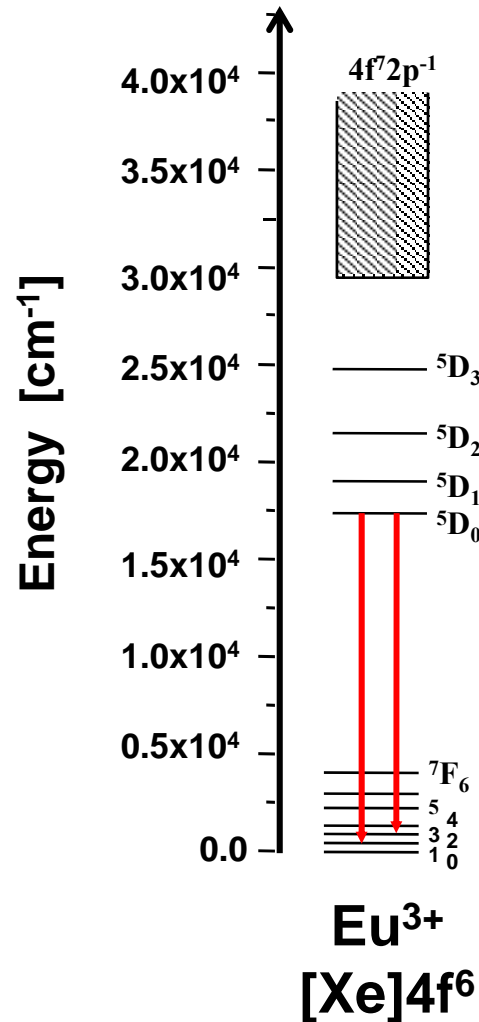


Phosphor	CIE(1931) colour point	
	x	y
(Y,Gd) BO_3 :Eu	0.640	0.360
Y_2O_3 :Eu	0.641	0.344
YVO_4 :Eu	0.645	0.343
$\text{Y}_2\text{O}_2\text{S}$:Eu	0.650	0.342

Colour saturation: $\text{Y}_2\text{O}_2\text{S}:\text{Eu} > \text{YVO}_4:\text{Eu} > \text{Y}_2\text{O}_3:\text{Eu} > (\text{Y,Gd})\text{BO}_3:\text{Eu}$

8.12 Luminescence of Rare Earth Ions

Emission spectra and colour points of Eu^{3+} activated phosphors



Observed emission spectrum due to ${}^5\text{D}_0 \rightarrow {}^7\text{F}_J$ transitions (lines)

a) Inversion symmetry (S_6 , D_{3d})

Magnetic dipole transitions, e.g. ${}^5\text{D}_0 - {}^7\text{F}_1$

$\Delta J = 0, \pm 1$ ($J = 0 \rightarrow J = 0$ forbidden)

$\text{MeBO}_3:\text{Eu}$ (Calcite, Vaterite)

$\tau \sim 8 - 16$ ms

b) No inversion symmetry

Electric dipole transitions ${}^5\text{D}_0 - {}^7\text{F}_{2,4}$

$\Delta J \leq 6$ ($J_i = 0 \rightarrow J_f = 2, 4, 6$)

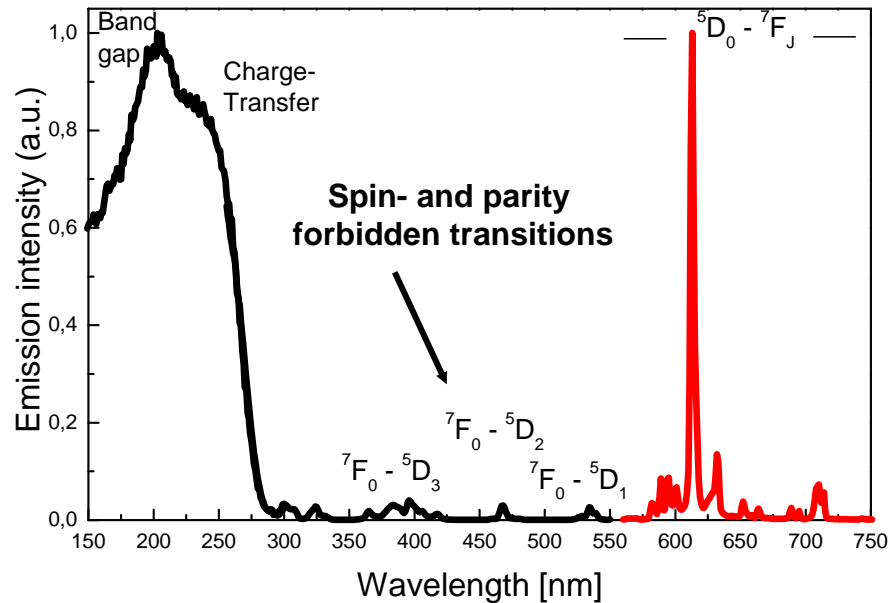
$\text{Y}_2\text{O}_3:\text{Eu}$ (Bixbyite), $\text{Y(V,P)O}_4:\text{Eu}$ (Xenotime)

$\tau \sim 2 - 5$ ms

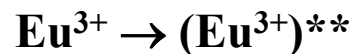
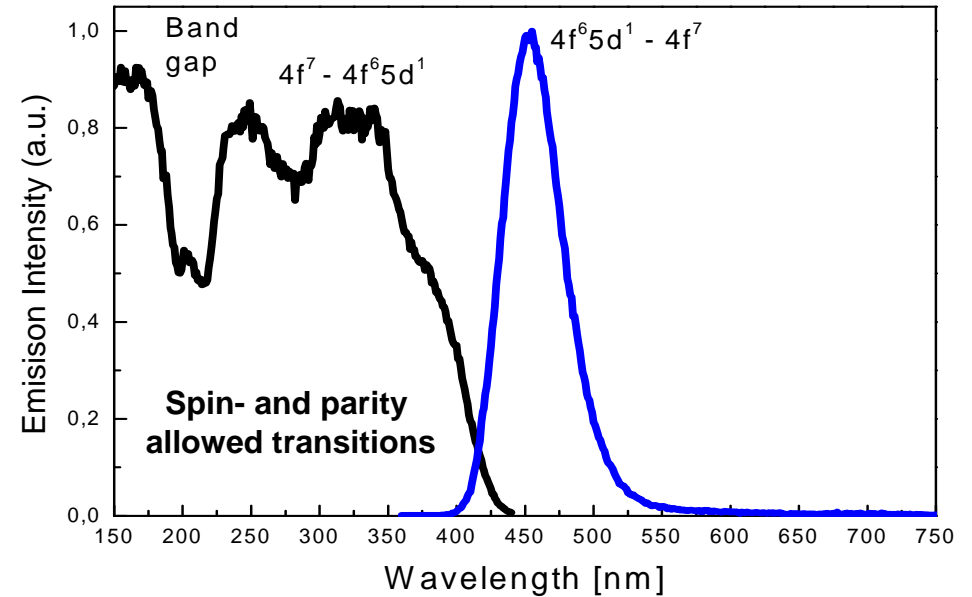
8.12 Luminescence of Rare Earth Ions

Excitation and emission spectra of Eu^{3+} and Eu^{2+} activated phosphors

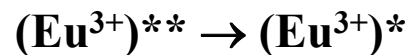
$\text{Y}_2\text{O}_3:\text{Eu}^{3+}$



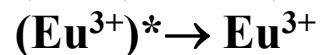
$\text{BaMgAl}_{10}\text{O}_{17}:\text{Eu}^{2+}$



CT



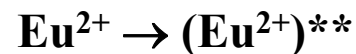
Relaxation



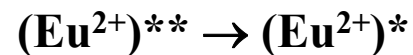
4f-4f

Strong CT absorption band (broad)

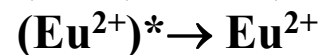
Weak 4f-4f absorption lines (narrow)



4f-5d



Relaxation

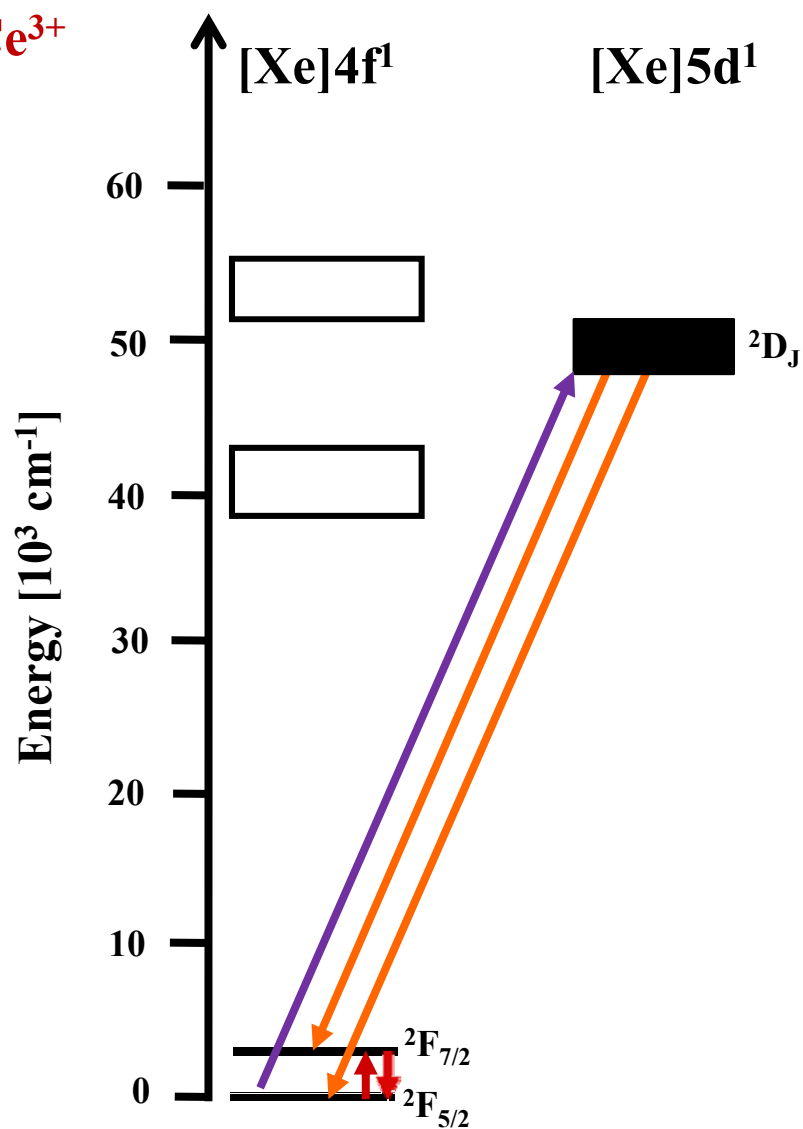


5d-4f

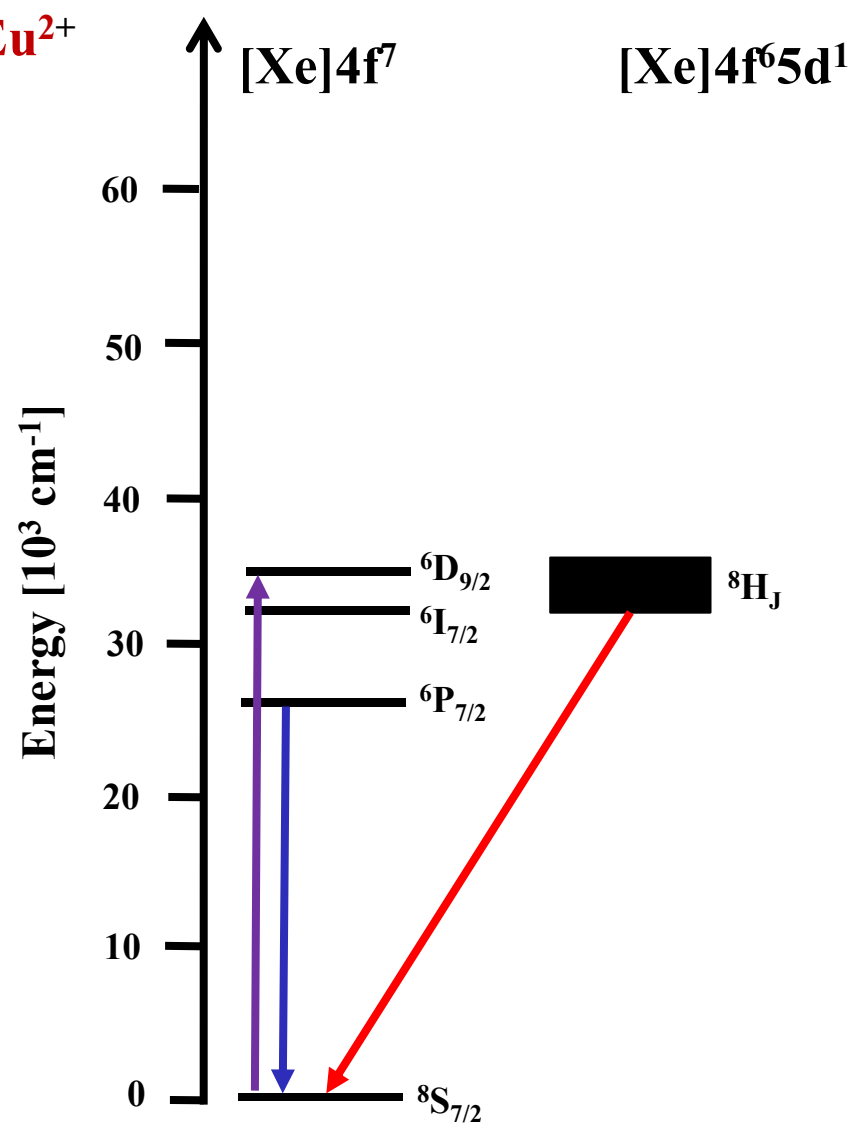
Strong 4f-5d absorption bands (broad)

8.12 Luminescence of Rare Earth Ions

Ce³⁺

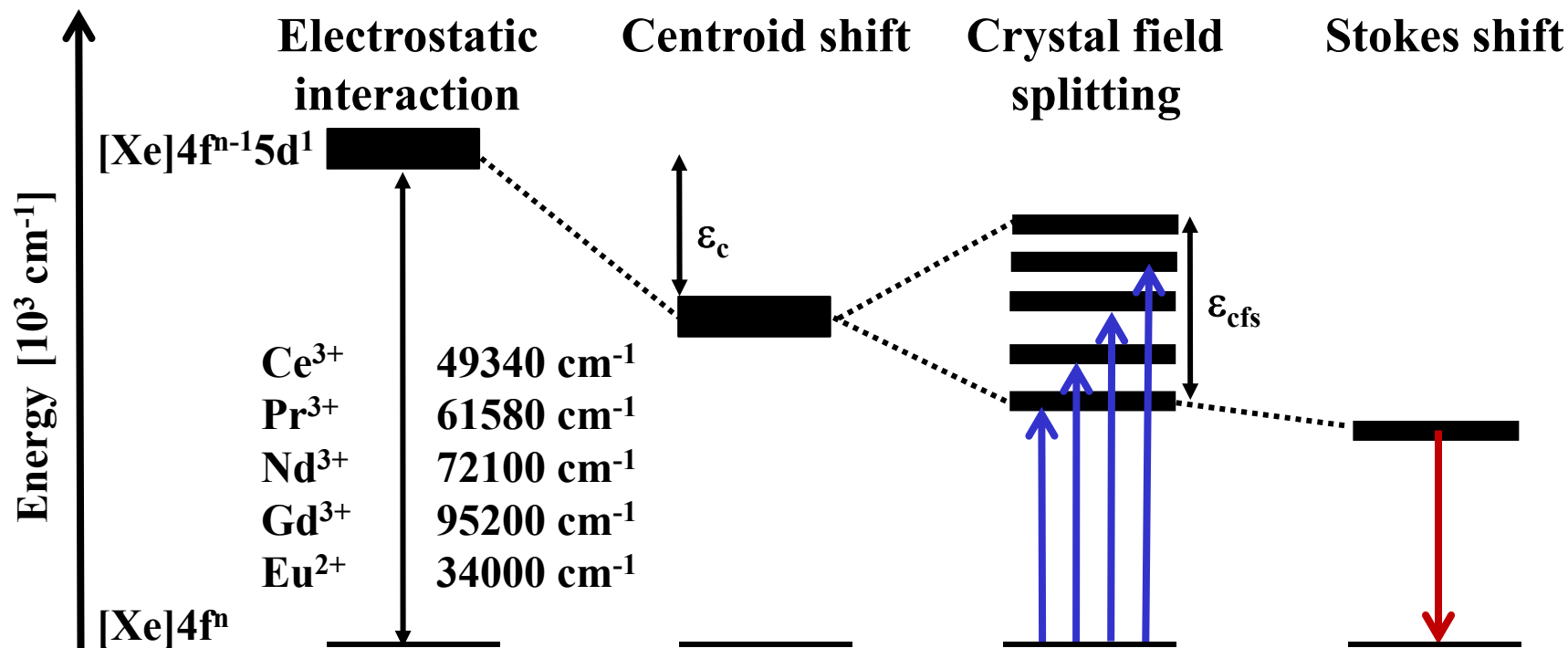


Eu²⁺



8.12 Luminescence of Rare Earth Ions

Energy gap between the $[\text{Xe}]4f^n$ and $[\text{Xe}]4f^{n-1}5d^1$ states



ϵ_c : Centroid energy proportional to the spectroscopic polarizability α_{sp} ($3000 - 20000 \text{ cm}^{-1}$)

ϵ_{cfs} : Crystal field splitting ($< 23000 \text{ cm}^{-1}$)

8.12 Luminescence of Rare Earth Ions

Centroid shift ~ electron density between activator and ligands

Polarizability of the anions

- selenides > sulfides > nitrides > oxides > fluorides

Charge density of the surrounding anions

- Type of network former:

oxides	aluminates	silicates	borates	phosphates	sulfates
O^{2-}	AlO_4^{5-}	SiO_4^{4-}	BO_3^{3-}	PO_4^{3-}	SO_4^{2-}

- Degree of networking

neso-silicate	soro-silicate	cyclo-silicate	phyllo-silicate
$[SiO_4]^{4-}$	$[Si_2O_7]^{6-}$	$[Si_3O_9]^{6-}$	$[Si_4O_{10}]^{4-}$

garnet

zircon

olivine

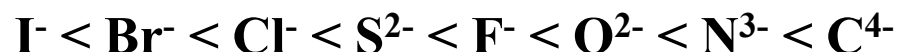
8.12 Luminescence of Rare Earth Ions

Crystal field splitting

Crystal field theory \Rightarrow ionic interaction between metal center and point charges

Energy splitting of the d-orbitals depends on:

- **Anionic charge / anionic radius (spectrochemical series)**



- **Symmetry (coordination number and symmetry)**

octahedral > cubic, dodecahedral, square-antiprismatic > tetrahedral

- **Metal-ligand distance (strong distance dependence)**

$$D = 35Ze/4R^5$$

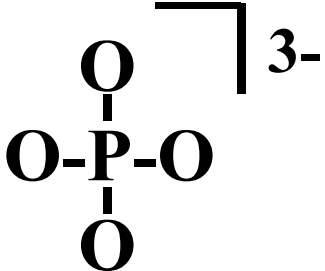
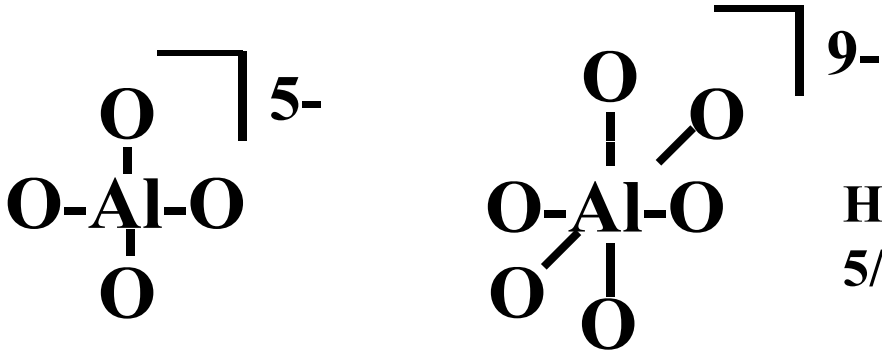
R = Cation-anion distance

Z = Valence of the anion

e = Electron charge

8.12 Luminescence of Rare Earth Ions

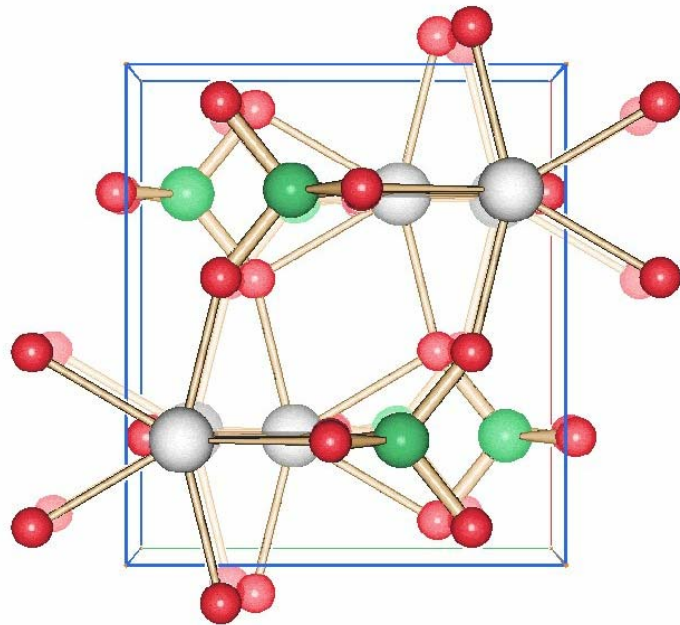
Covalent character of ionic bonds

Host lattice	Cation	Type of network former	
YPO_4	Y^{3+}	 <p>tetrahedral PO_4^{3-}</p>	Low charge density $3/4^-$ per oxygen
$\text{Y}_3\text{Al}_5\text{O}_{12}$	Y^{3+}	 <p>tetrahedral AlO_4^{5-} + octahedral AlO_6^{9-}</p>	High charge density $5/4^-$ or $9/4^-$ per oxygen

P^{5+} attracts more charge density of the O^{2-} anions than Al^{3+}

8.12 Luminescence of Rare Earth Ions

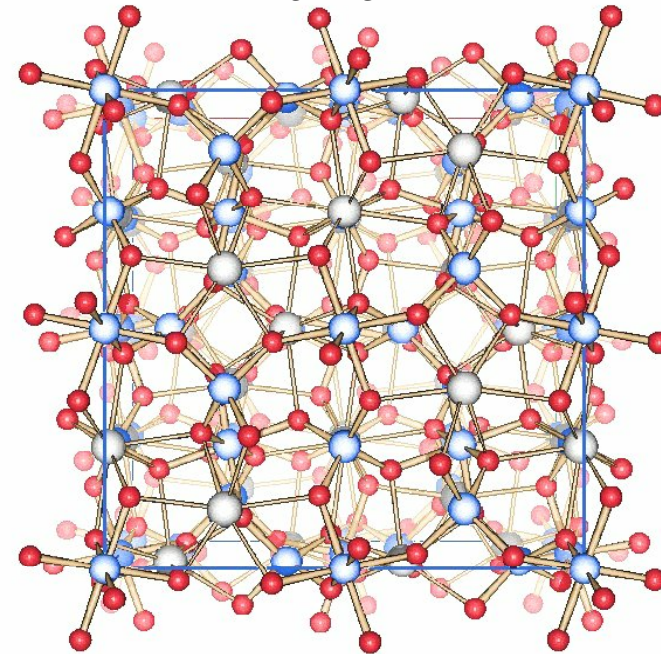
Electron density on the anions



4 x O(1) 7.248

4 x O(2) 7.193

Low charge density on oxygen



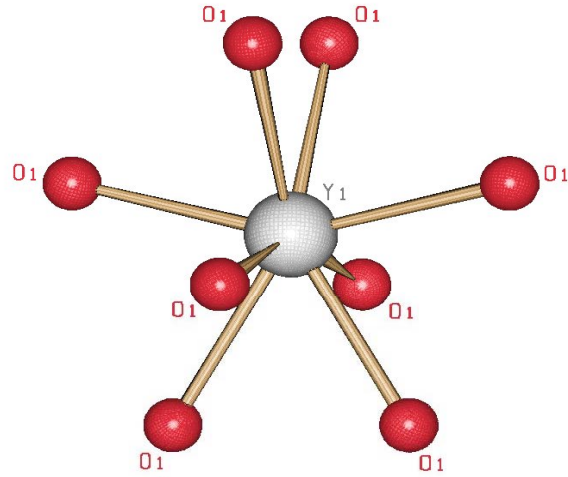
4 x O(1) 7.528

4 x O(2) 7.504

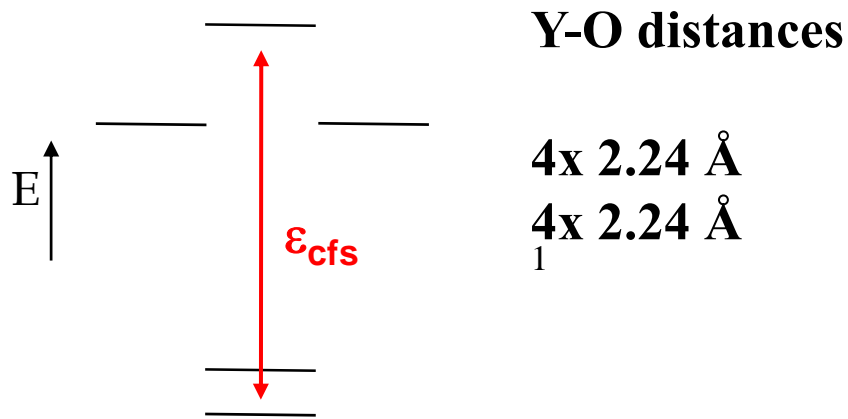
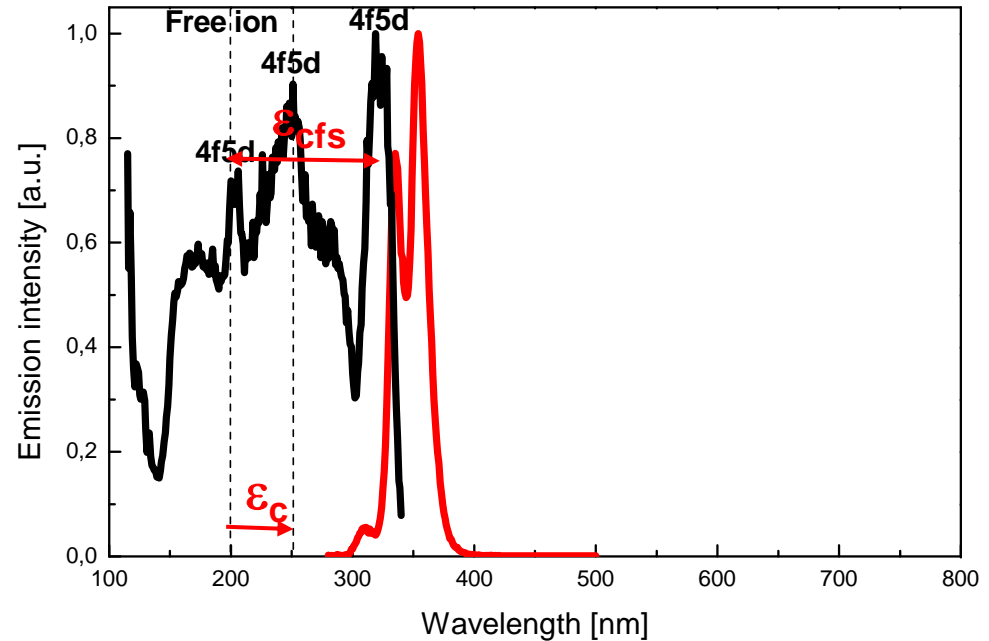
High charge density on oxygen

8.12 Luminescence of Rare Earth Ions

Luminescence of $\text{YPO}_4:\text{Ce}$



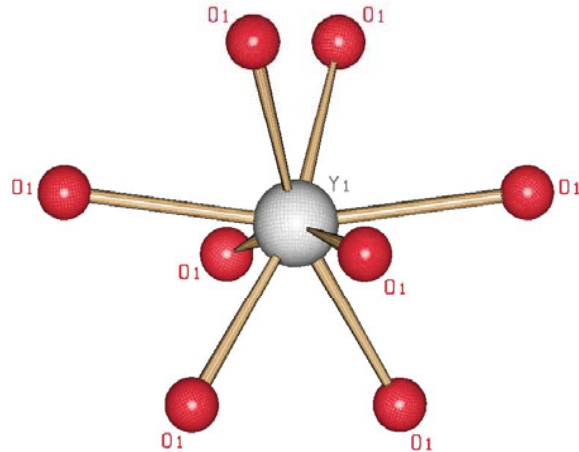
Distorted dodecahedral



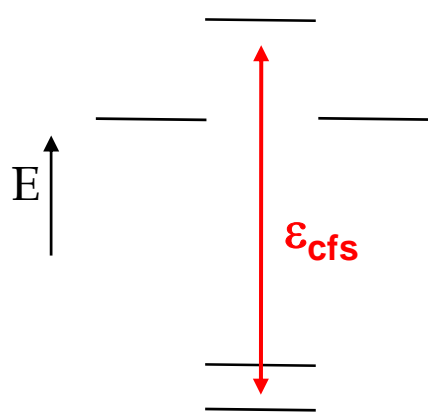
Crystal field splitting $\sim 18000 \text{ cm}^{-1}$
 Centroid shift $\sim 9600 \text{ cm}^{-1}$
 (P. Dorenbos, *Phys. Rev. B*, 64, 2001, 1251)
 \Rightarrow Large 4f-5d energy gap
 \Rightarrow Emission bands at 335 and 355 nm

8.12 Luminescence of Rare Earth Ions

Luminescence of $\text{Y}_3\text{Al}_5\text{O}_{12}:\text{Ce}$



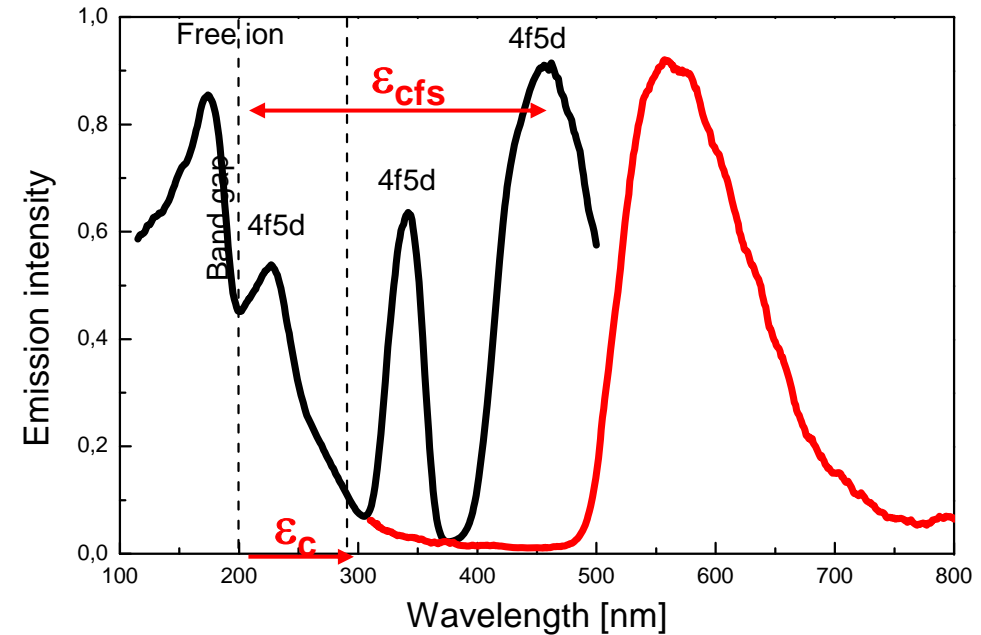
Distorted dodecahedral



Y-O distances

4x 2.30 Å

4x 2.44 Å



Crystal field splitting $\sim 27000 \text{ cm}^{-1}$

Centroid shift $\sim 14700 \text{ cm}^{-1}$

(P. Dorenbos, Phys. Rev. B, 65, 2002, 2351)

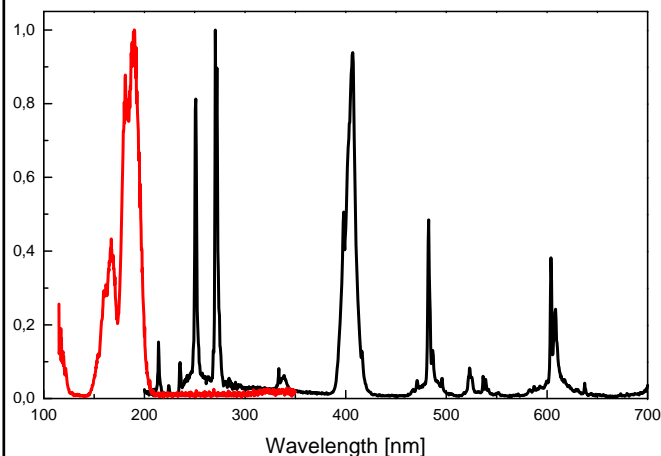
\Rightarrow Small 4f-5d energy gap

\Rightarrow Emission bands at 560 nm

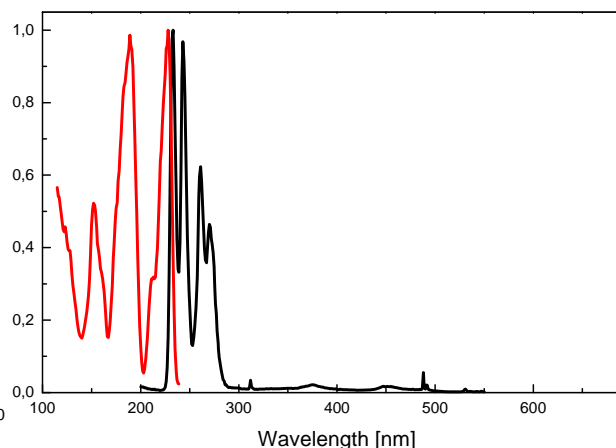
8.12 Luminescence of Rare Earth Ions

Excitation and emission spectra of Pr^{3+} activated phosphors

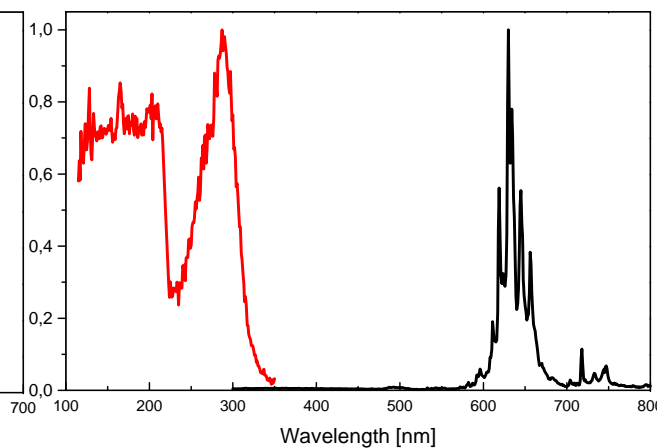
$\text{YF}_3:\text{Pr}$



$\text{YPO}_4:\text{Pr}$



$\text{Y}_2\text{O}_3:\text{Pr}$



$4f^15d^1-4f^2$ band emission

$4f^2-4f^2$ line emission

$4f^2-4f^2$ line emission

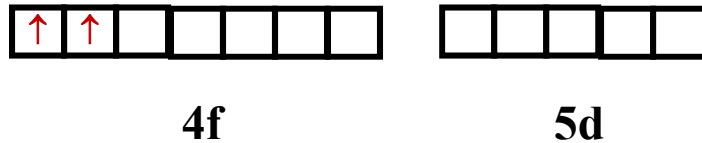
The nature of the luminescence spectrum of Pr^{3+}
is strongly determined by the host lattice!

8.12 Luminescence of Rare Earth Ions

Fundamentals of Pr³⁺ luminescence

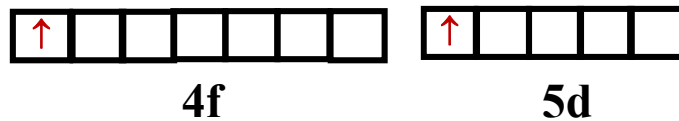
Pr³⁺ ground state configuration

[Xe]4f² → 13 SLJ-States



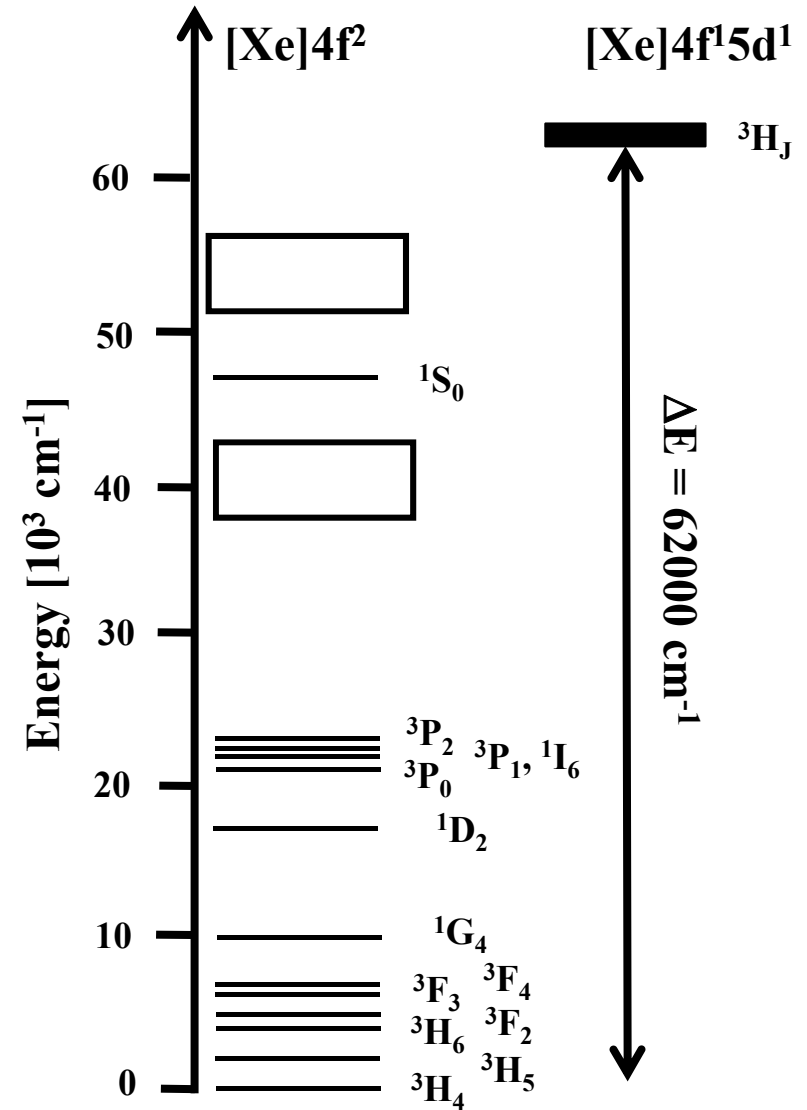
Pr³⁺ excited state configuration

[Xe]4f¹5d¹ → 2 SLJ-States



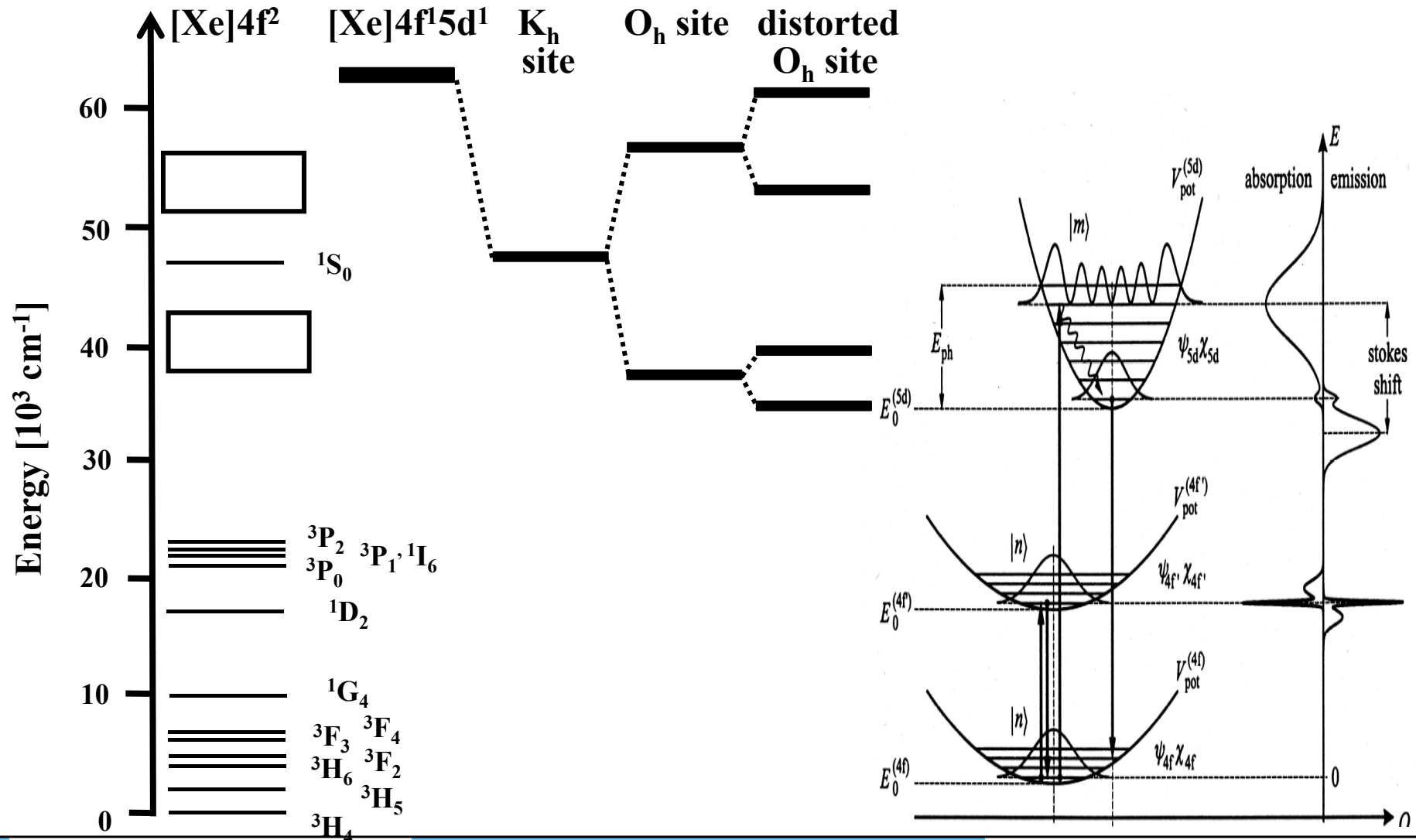
⇒ [Xe]4f² – [Xe]4f² transitions

⇒ [Xe]4f² – [Xe]4f¹5d¹ transitions



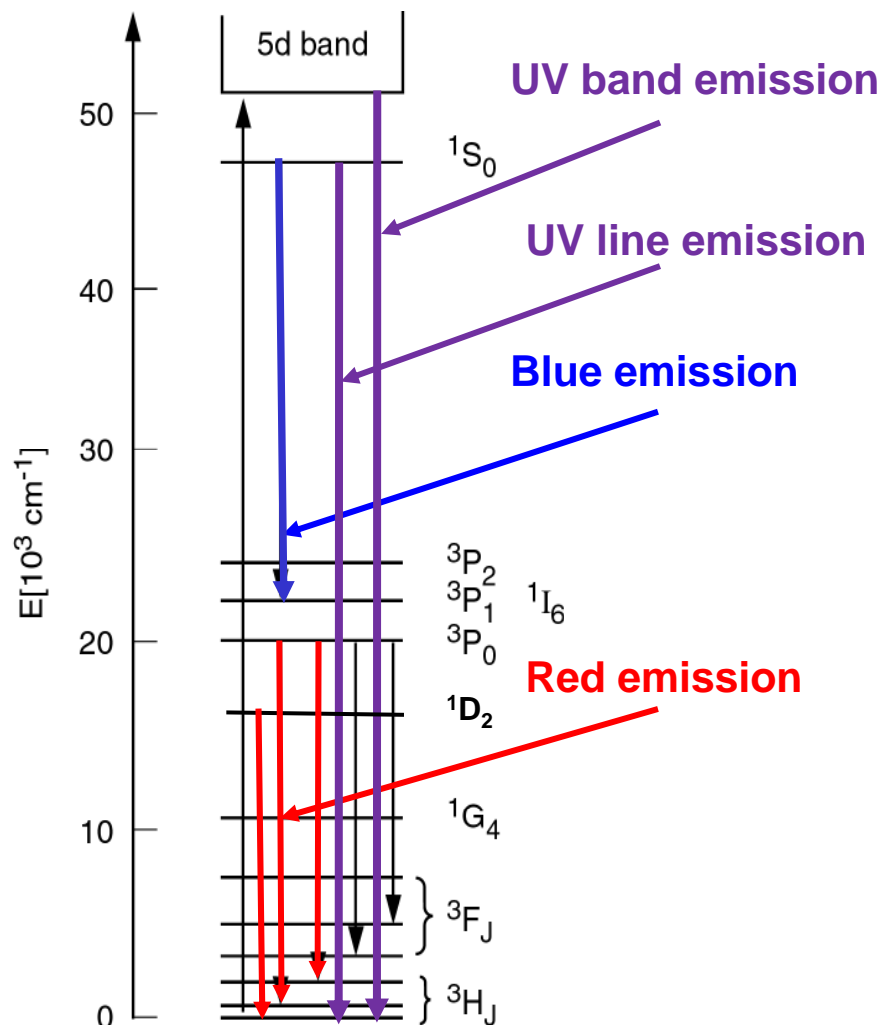
8.12 Luminescence of Rare Earth Ions

Fundamentals of Pr³⁺ luminescence



8.12 Luminescence of Rare Earth Ions

Emission spectra of Pr³⁺ phosphors



¹S₀ – ²S+¹L_J line emission

YF₃:Pr

NaYF₄:Pr

SrAl₁₂O₁₉:Pr

LaMgB₅O₁₀:Pr

LaB₃O₆:Pr

213, 236

252, 271

407 nm

¹S₀ – ²S+¹L_J lines and 4f¹5d¹ – 4f² band emission

KY₃F₁₀:Pr

240, 250, 271 nm

4f¹5d¹ – 4f² band emission

LiYF₄:Pr

218 nm

YPO₄:Pr

232 nm

KYF₄:Pr

235 nm

YAIO₃:Pr

245 nm

YBO₃:Pr

263 nm

Lu₂Si₂O₇:Pr

273 nm

Lu₃Al₅O₁₂:Pr

310 nm

Y₃Al₅O₁₂:Pr

320 nm + line emission

¹D₂ – ³H_J line emission

Y₂O₃:Pr

615 nm

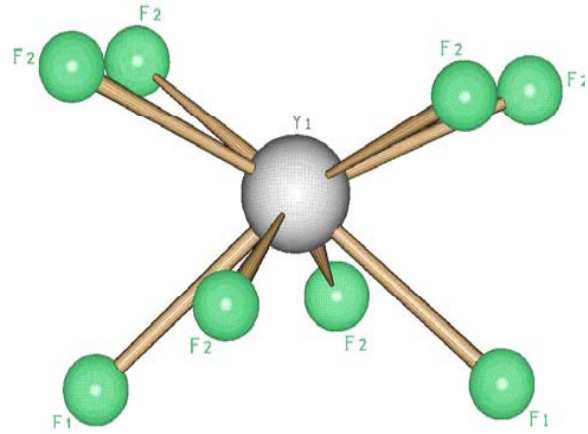
CaTiO₃:Pr,Na

615 nm

Energy of the lowest crystal field component of [Xe]4f¹5d¹ config.

8.12 Luminescence of Rare Earth Ions

Luminescence of $\text{YF}_3:\text{Pr}$



Distorted square-antiprismatic

Energy ↑



Y-F distances

4x 2.28 Å

2x 2.30 Å

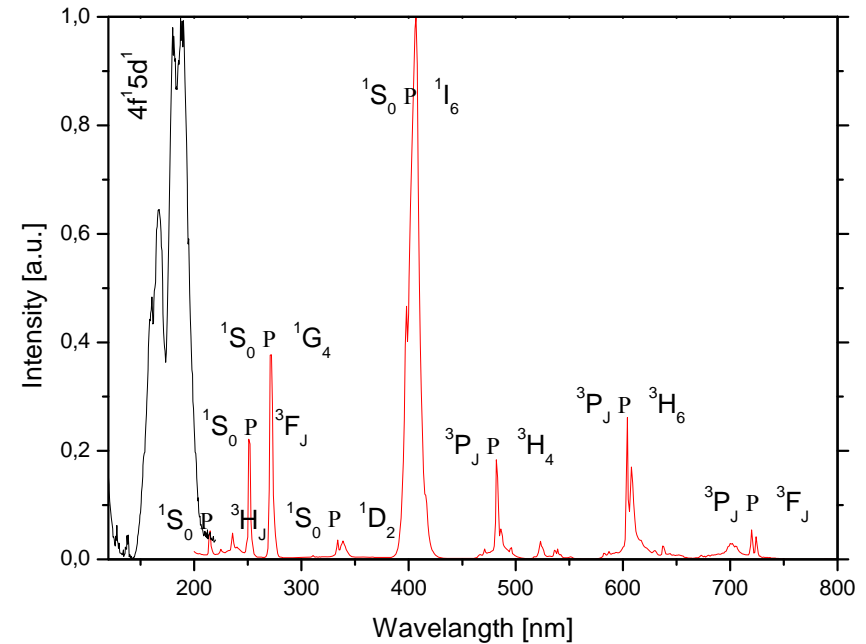
2x 2.31 Å

CF splitting

~ 8000 cm^{-1}

Centroid shift

~ 5600 cm^{-1}



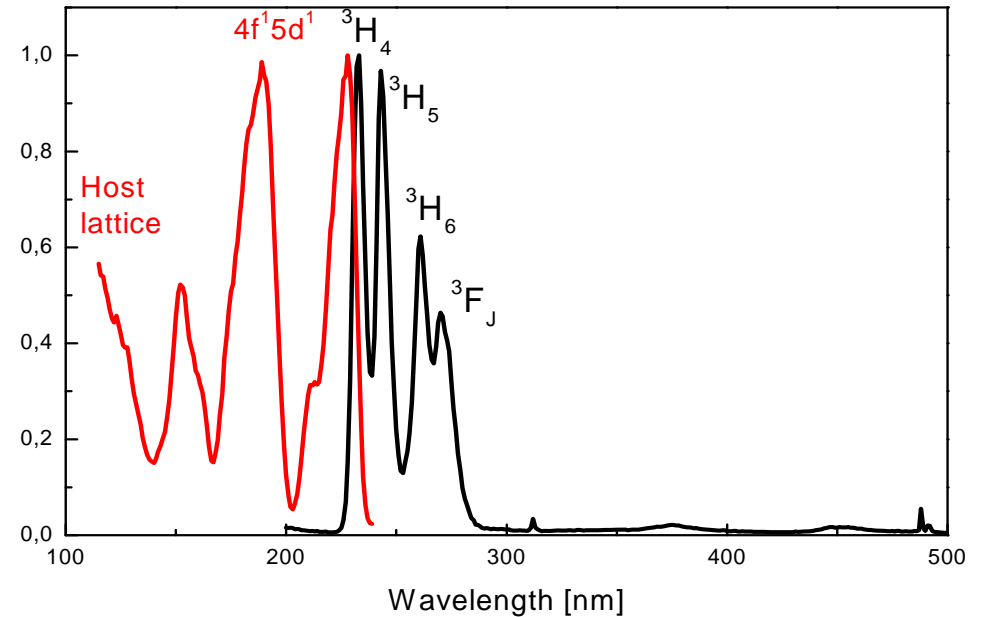
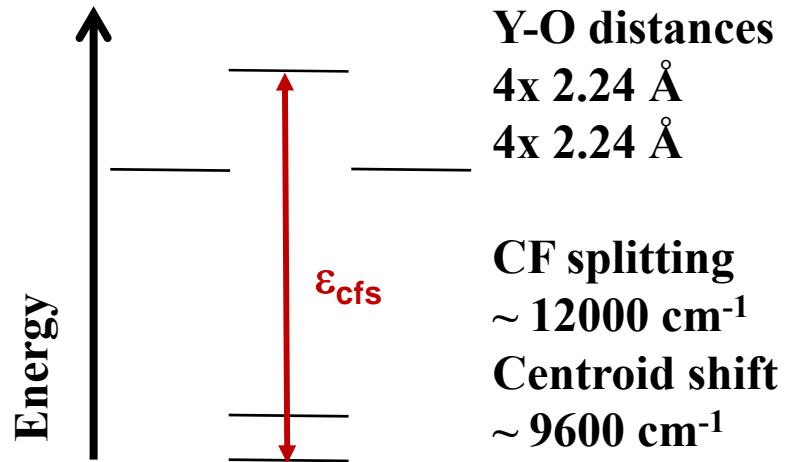
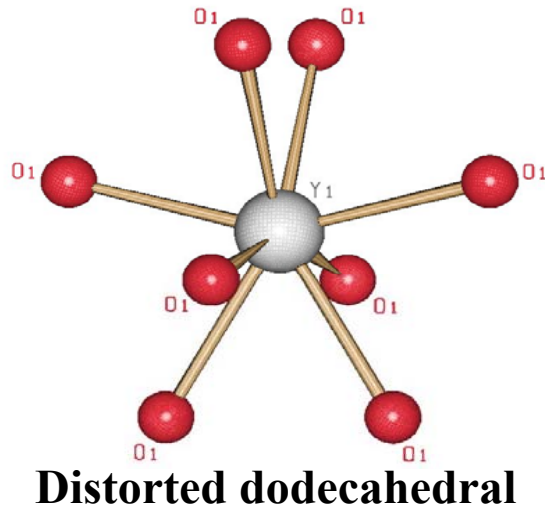
CFS + centroid shift reduces energy of lowest crystal field component of the $[\text{Xe}]4f^{15}d^1$ configuration by $\sim 10000 \text{ cm}^{-1}$

$\Rightarrow E(4f^{15}d^1) > E(1S_0)$

$\Rightarrow 1S_0 - 2S+1L_J$ line emission

8.12 Luminescence of Rare Earth Ions

Luminescence of $\text{YPO}_4:\text{Pr}$



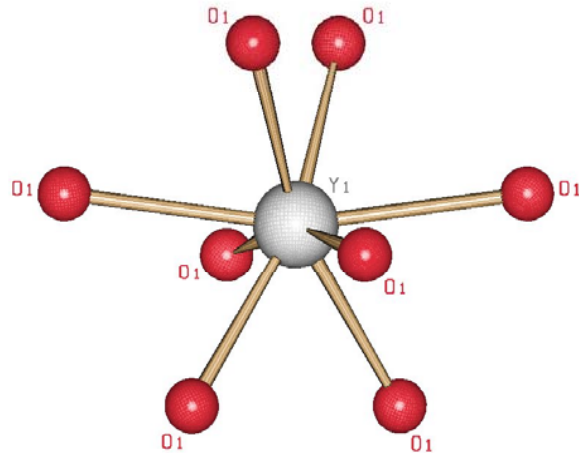
CFS + centroid shift reduces energy of lowest crystal field component of the $[\text{Xe}]4f^1 5d^1$ configuration by $\sim 16000 \text{ cm}^{-1}$

$$\Rightarrow E(4f^1 5d^1) < E(^1\text{S}_0)$$

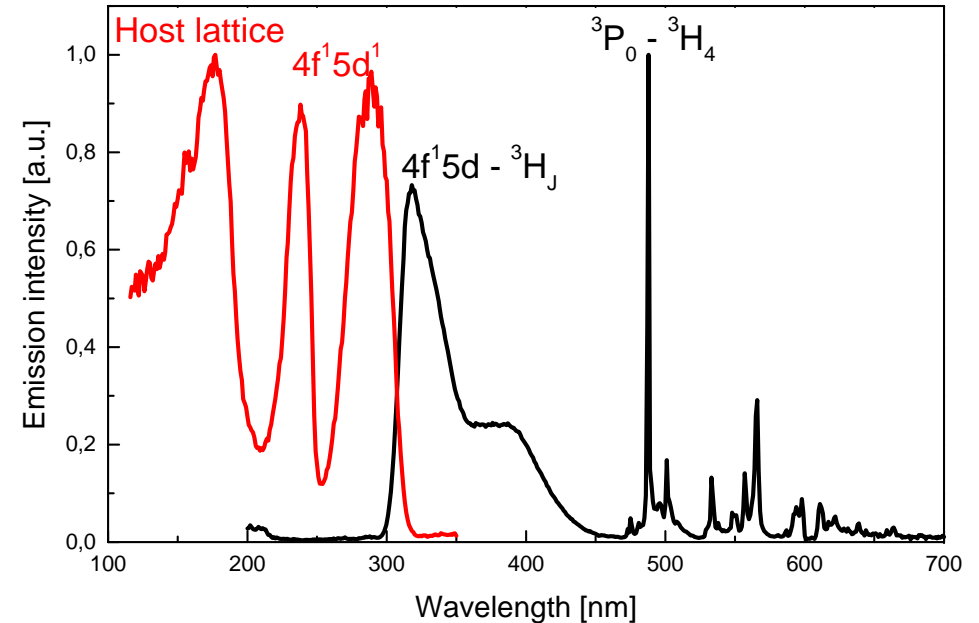
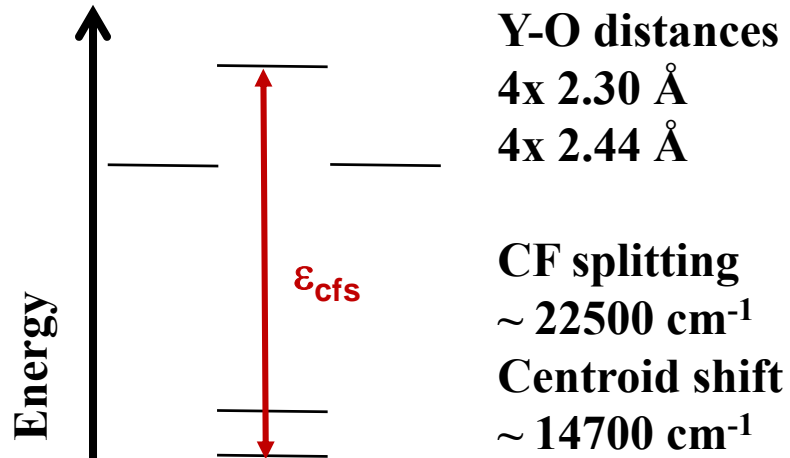
$\Rightarrow [\text{Xe}]4f^1 5d^1 - [\text{Xe}]4f^2$ band emission

8.12 Luminescence of Rare Earth Ions

Luminescence of $\text{Y}_3\text{Al}_5\text{O}_{12}:\text{Pr}$



Distorted dodecahedral



CFS + centroid shift reduces energy of lowest crystal field component of the $[\text{Xe}]4f^15d^1$ configuration by $\sim 26000 \text{ cm}^{-1}$

$\Rightarrow E(4f^15d^1) \ll E(1S_0)$

\Rightarrow UV band emission (320 nm) and visible line emission ($> 450 \text{ nm}$)

8.13 Down-Conversion

First examples (1974)

Sommerdijk et al., J. Lumin. 8 (1974) 288 (Philips)

Sommerdijk et al., J. Lumin. 8 (1974) 341 (Philips)

Piper et al., J. Lumin. 8 (1974) 344 (GE)

$\text{YF}_3:\text{Pr}(0.1\%)$ and $\text{NaYF}_4:\text{Pr}(0.1\%)$

$^1\text{S}_0 - ^3\text{P}_1, ^1\text{I}_6$ transition @ 407 nm

$^3\text{P}_0 - ^3\text{H}_J, ^3\text{F}_2$ transitions in the red

Internal QY = 166% (total) @ 214 nm exc.

Derived from line ratio UV to blue to green/red

Oxidic luminescent materials showing PCE

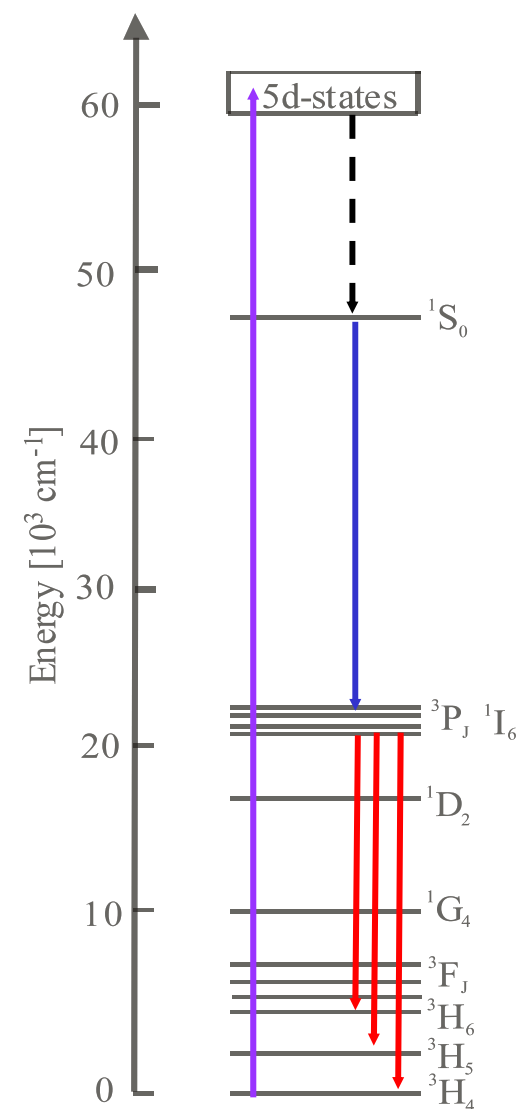
A.M. Srivastava, D.A. Doughty, W.W. Beers (GE)

Pr^{3+} on host lattice sites with high CN (> 8)

$\text{SrAl}_{12}\text{O}_{19}:\text{Pr},\text{Mg}$

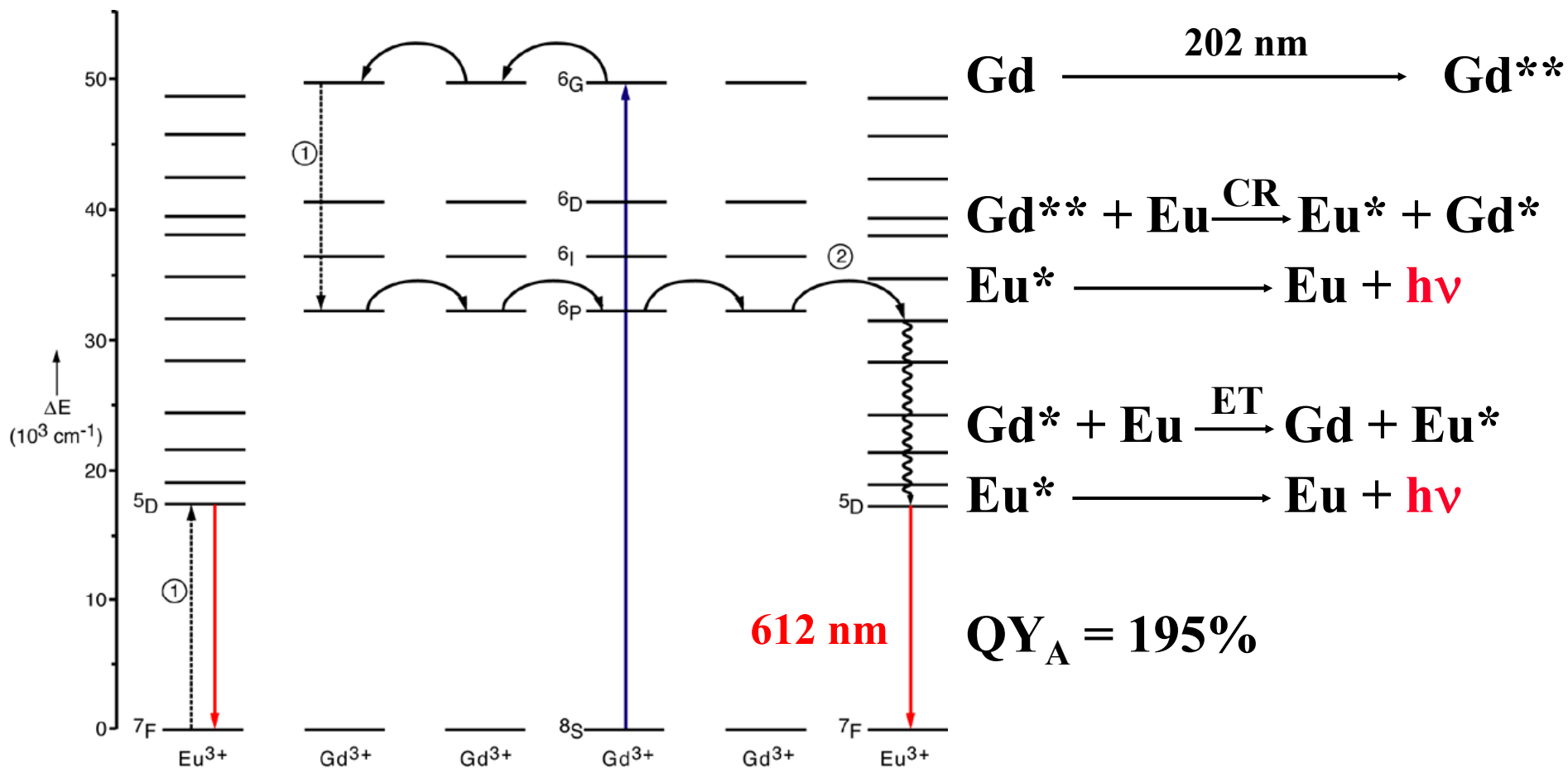
$\text{LaMgB}_5\text{O}_{10}:\text{Pr}$

$\text{LaB}_3\text{O}_6:\text{Pr}$



8.13 Down-Conversion

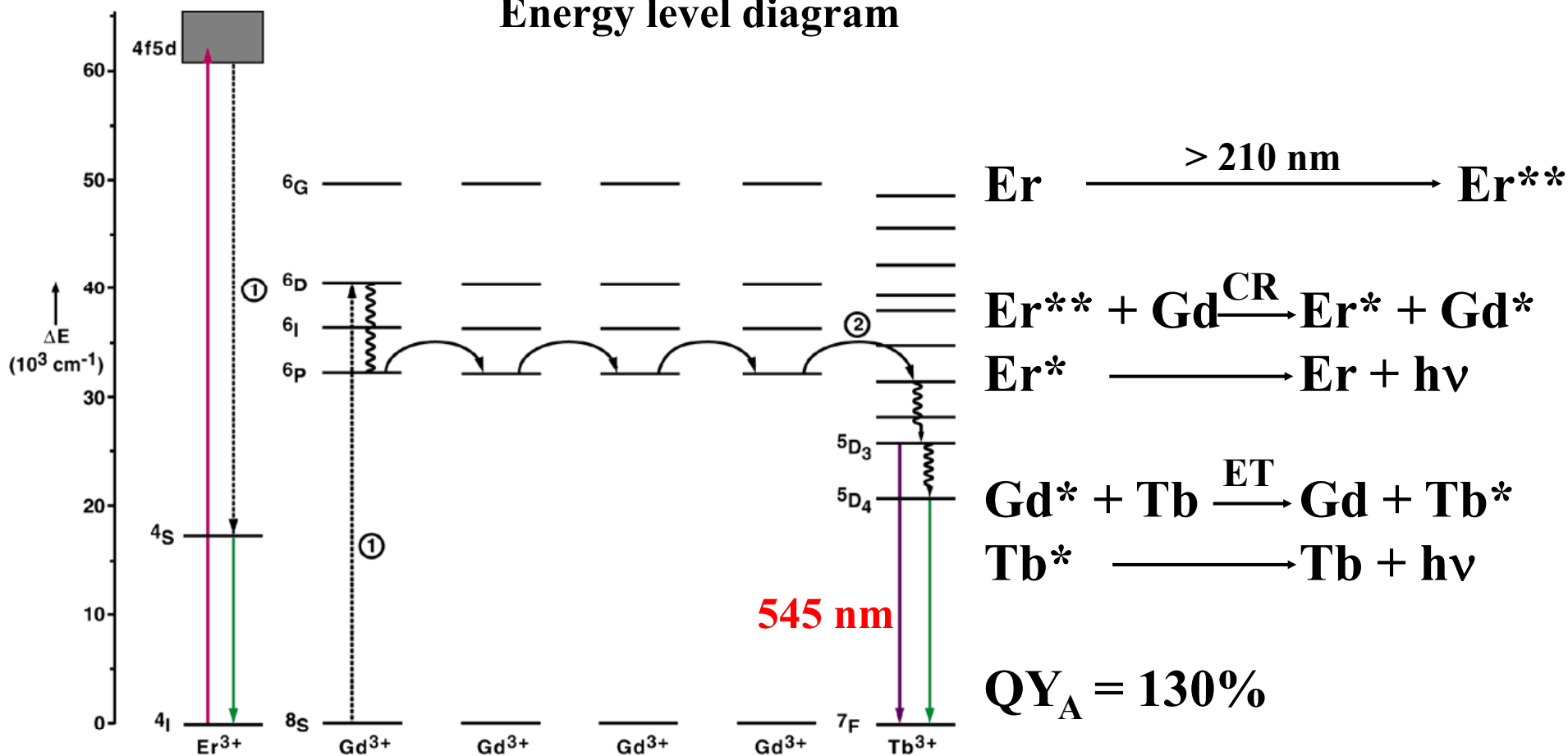
Example: LiGdF₄:Eu



8.13 Down-Conversion

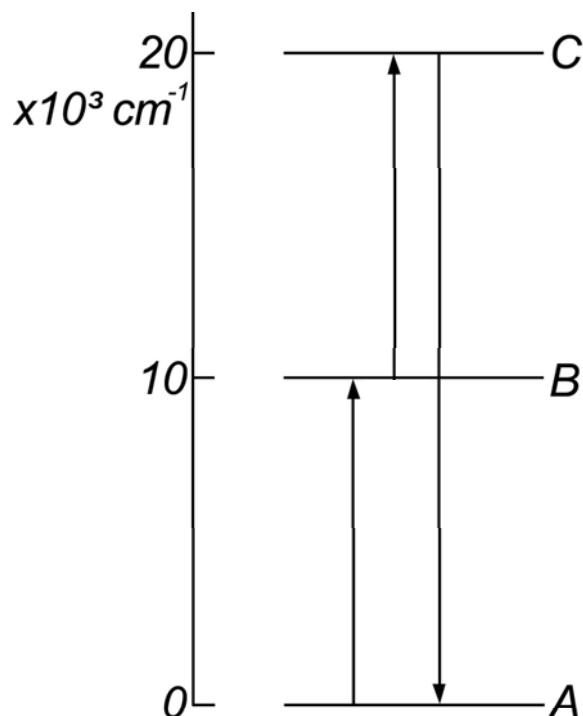
Example: $\text{LiGdF}_4:\text{Er,Tb}$

Energy level diagram



8.14 Up-Conversion

Principle

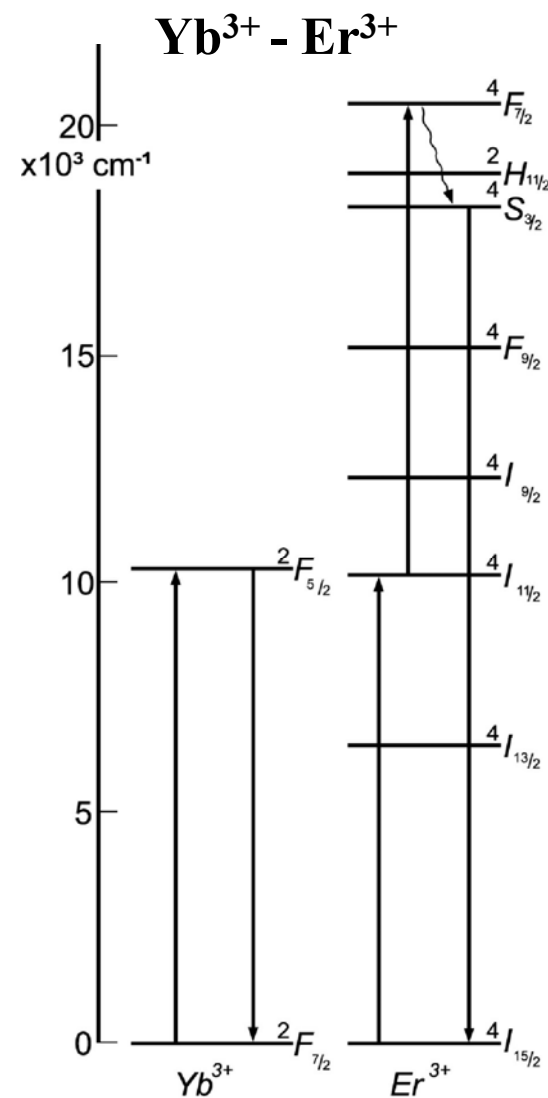


Examples

YF₃:Yb,Tm
YF₃:Yb,Er
NaYF₄:Yb,Er
BaY₂F₈:Yb,Er
YOCl:Yb,Er

20-35% Yb³⁺
1-5% Er³⁺ or Tm³⁺

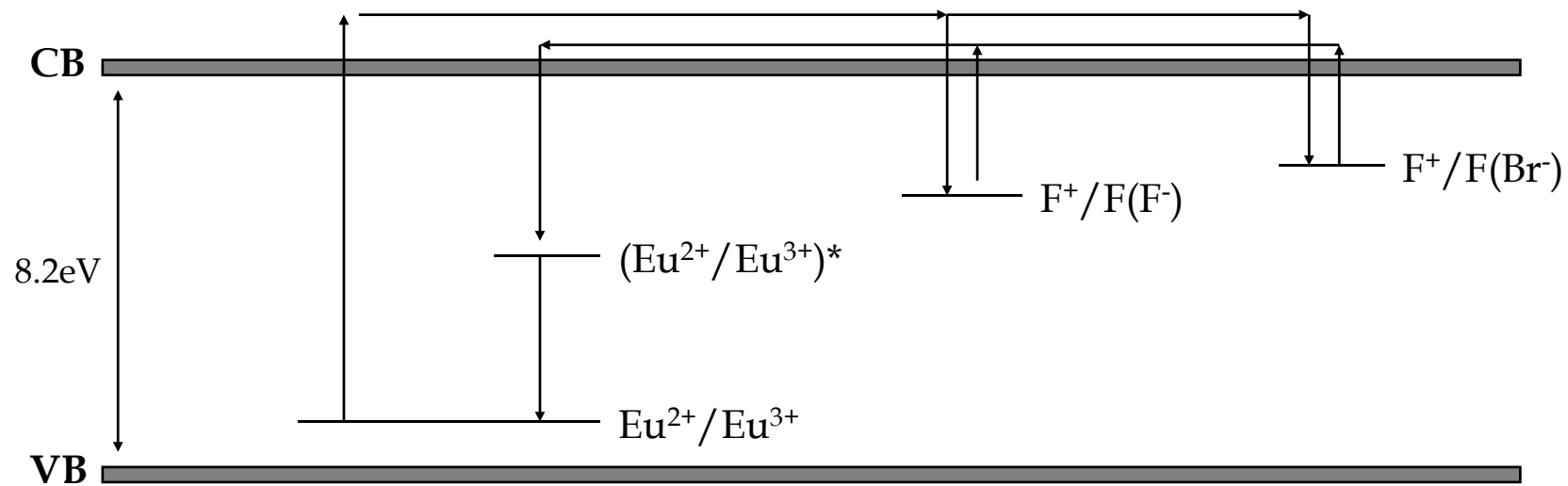
Implementation of IR radiation into visible
(in frequency multipliers, laser diodes, night vision goggles)



8.15 Afterglow

Cause: Storage of electrons / holes in certain sites in the lattice (vacancies, impurities)

Deep traps: Emptying of the traps is done by activation (LASER)

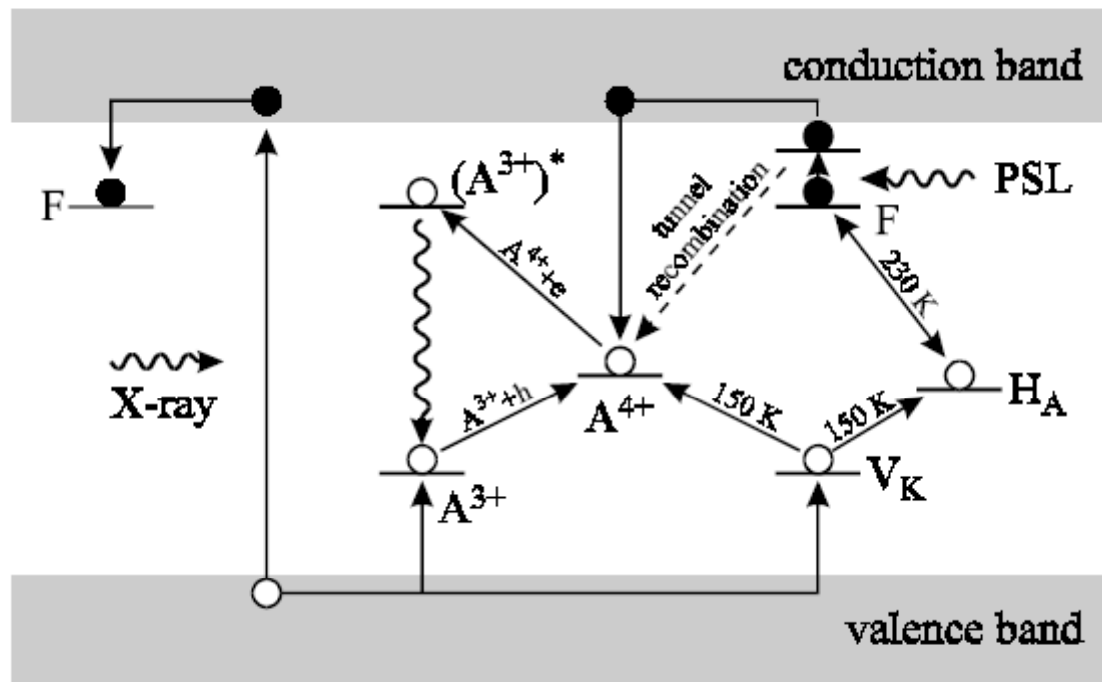


Example: BaFBr:Eu

Storage phosphor for imaging plates (detection of x-rays)
(*Y. Iwabuchi et al., J. Appl. Phys. 33 (1994) 178*)

8.15 Afterglow

Example: $\text{Cs}_2\text{NaYF}_6:\text{Ce}$ and $\text{Cs}_2\text{NaYF}_6:\text{Pr}$ (elpasolite)

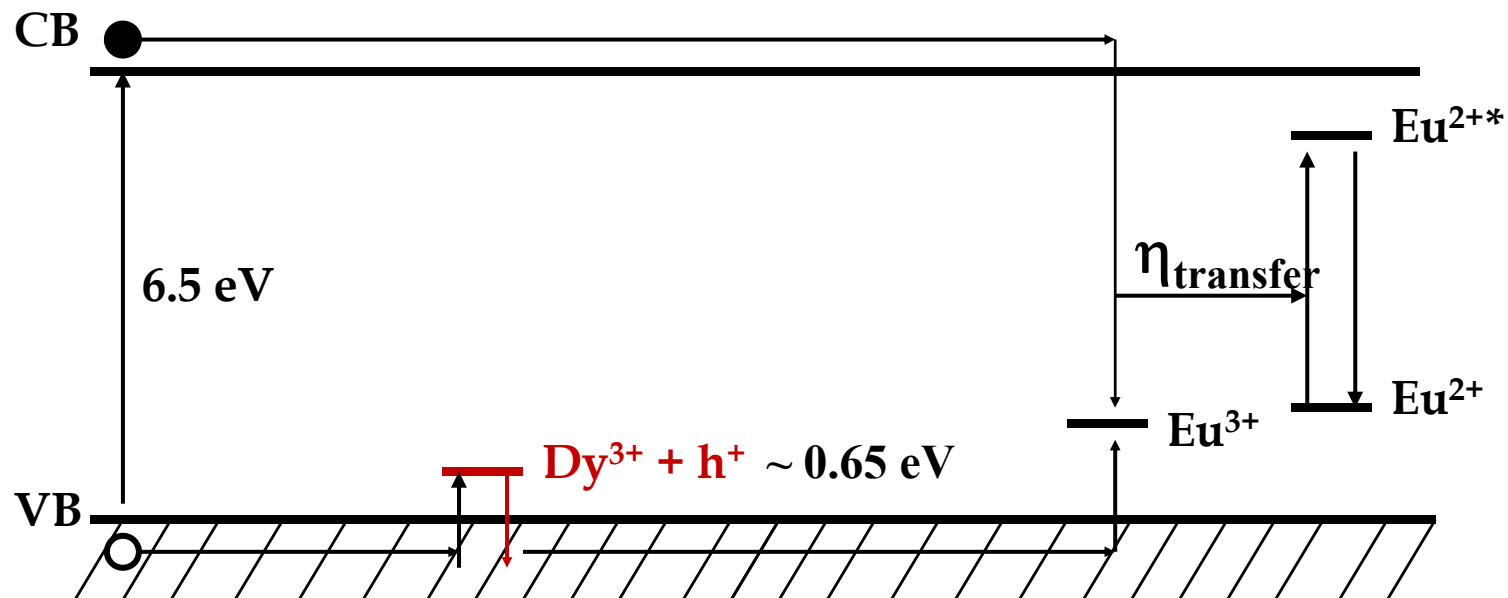


A = Ce, Pr

According to: Th. Pawlik and J.-M. Spaeth, *J. Appl. Phys.* 82 (9), 4236 (1997)

8.15 Afterglow

Shallow traps: Thermal emptying of the traps at room temperature



Example

$SrAl_2O_4:Eu,Dy$

(Nemoto Ltd., JECS 143 (1996) 2670)

8.15 Afterglow

Afterglow phosphors

Composition	colour	λ_{\max} [nm]
• $\text{CaAl}_2\text{O}_4:\text{Eu,Nd}$	blue	440 nm
• $\text{Sr}_2\text{MgSi}_2\text{O}_7:\text{Eu,Dy}$	blue	469 nm
• $\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu,Dy}$	cyan	490 nm
• $\text{Mg}_2\text{SnO}_4:\text{Mn}^{2+}$	cyan	499 nm
• $\text{SrAl}_2\text{O}_4:\text{Eu,Dy}$	green	520 nm
• $\text{ZnS}:\text{Cu,Co}$	green	530 nm
• $\text{Sr}_2\text{SiO}_4:\text{Eu,Dy}$	yellow	570 nm
• $\text{Y}_2\text{O}_2\text{S}:\text{Eu,Ti,Mg}$	red	620 nm
• $\text{CaZnGe}_2\text{O}_6:\text{Mn}$	red	648 nm
• $\text{CaS}:\text{Eu,Tm}$	red	655 nm
• $\text{MgSiO}_3:\text{Eu,Dy,Mn}$	red	660 nm

$\text{Sr}_4\text{Al}_{14}\text{O}_{25}:\text{Eu}^{2+},\text{Ln}^{3+}$

